

The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

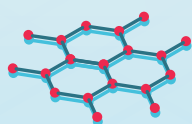


ICMOVPE XXII



July 12(Sun.)-17(Fri.), 2026
ICC JEJU, Jeju Island, Korea

Program Book



Organized by **KOES** 한국광전자공학회
Korea Optoelectronics Society

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Program at a Glance

July 12 (Sun.), 2026	
Time	Room A
	Baekrok Hall A, 1F
14:00–17:00	Tutorial Session
18:00–19:30	Welcome Reception (Ocean View, 5F)

July 13 (Mon.), 2026		
Time	Room A	Room B
	Baekrok Hall A, 1F	Baekrok Hall B, 1F
09:00–09:15	Opening Ceremony & Harold M. Manasevit Young Investigator Award Ceremony (Yeongju Hall A, 1F)	
09:15–10:05	Plenary Talk 1 (Yeongju Hall A, 1F) Prof. Hiroshi Amano (Nagoya University, Japan) "Refreshing the Social Infrastructure with MOVPE"	
10:05–10:55	Plenary Talk 2 (Yeongju Hall A, 1F) Prof. Joan Redwing (The Pennsylvania State University, USA) "Advances in MOCVD for Epitaxial Growth of Wafer-Scale 2D Transition Metal Dichalcogenides"	
10:55–11:15	Break	
11:15–12:30	[MoA1] 2D Materials – I	[MoB1] Nitrides for Electronics – I
12:30–14:00	Lunch (Event Hall A, 1F)	
14:00–15:45	[MoA2] Advanced Growth Techniques – I	[MoB2] Micro-LEDs
15:45–16:05	Break	
16:05–18:05	[MoA3] Arsenides	[MoB3] Optical Characterization

July 14 (Tue.), 2026		
Time	Room A	Room B
	Baekrok Hall A, 1F	Baekrok Hall B, 1F
08:30–10:15	[TuA1] Phosphides	[TuB1] Lasers
10:15–10:35	Break	
10:35–12:20	[TuA2] Low-Dimensional Materials	[TuB2] Nitrides for Electronics – II
12:20–14:00	Lunch (Event Hall A, 1F)	
14:00–16:00	[TuA3] 2D Materials – II	[TuB3] Optical Devices
16:00–17:40	Poster Session 1 (Event Hall A, 1F)	

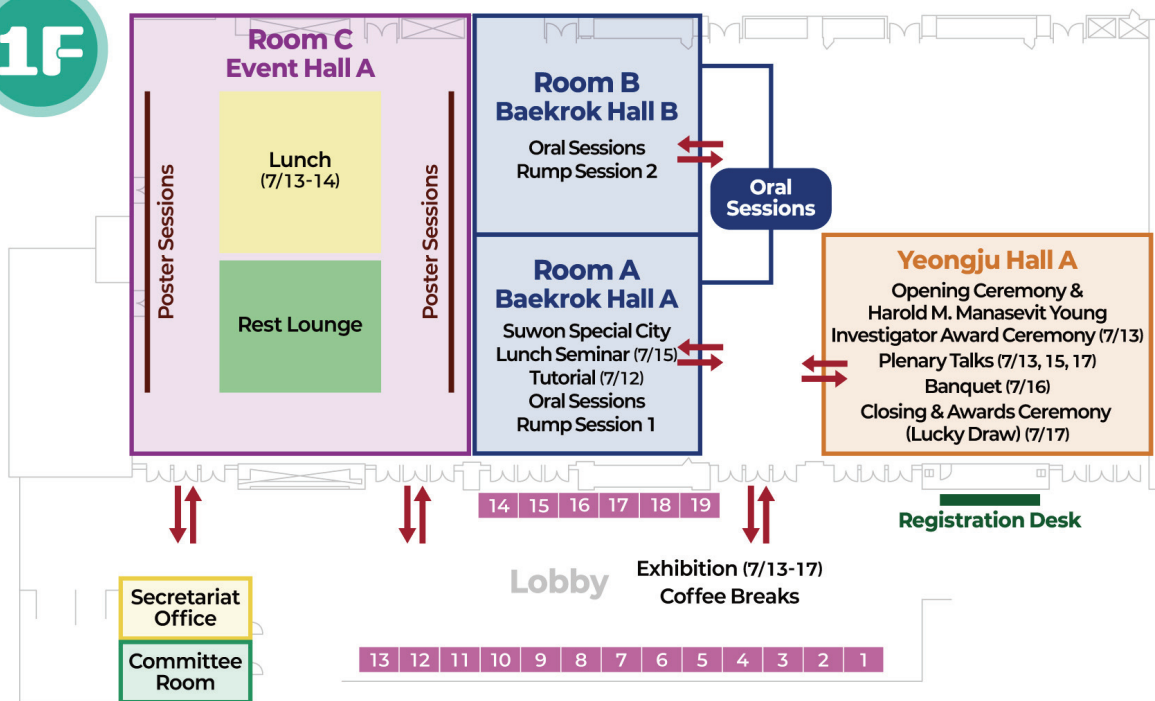
July 15 (Wed.), 2026			
Time	Room A	Room B	Room 202, 2F
	Baekrok Hall A, 1F	Baekrok Hall B, 1F	
08:30–09:20	Plenary Talk 3 (Yeongju Hall A, 1F) Prof. Michael Heuken (ADXTRON & RWTH Aachen University, Germany) “Status and Future Trends of Metalorganic Chemical Vapor Phase Deposition”		[Special Session] Compound Semiconductor Networking Reception (15:00–19:00)
09:20–10:10	Plenary Talk 4 (Yeongju Hall A, 1F) Prof. Nicolas Grandjean (EPFL, Switzerland) “Near-Perfect Quantum Efficiency InGaN LEDs through Growth Engineering”		
10:15–10:25	Break		
10:25–12:10	[WeA1] Gallium Oxides	[WeB1] UV Devices	
12:10–13:30	Suwon Special City Lunch Seminar (Baekrok Hall A , 1F)		
13:30–15:15	[WeA2] Polarity-Engineered Epitaxy	[WeB2] Visible LEDs	
15:15–15:35	Break		
15:35–17:05	[WeA3] Advanced Growth Techniques – II	[WeB3] Nitrides for Electronics – III	
17:10–18:50	Poster Session 2 (Event Hall A, 1F)		
19:00–20:30	Rump Session 1 Materials and Epitaxy Challenges in III–V Nitride Semiconductors for LEDs and Power Devices/HEMTs	Rump Session 2 Next big thing in MOCVD – 2D, ML/AI and MOCVD itself	

July 16 (Thu.), 2026		
Time	Room A	Room B
	Baekrok Hall A, 1F	Baekrok Hall B, 1F
08:30–10:15	[ThA1] Al-rich AlGaIn	[ThB1] Structural Analysis
10:15–12:00	Free Excursion	
12:00–18:30	Free Discussion Time (Optional Excursion)	
18:30–20:30	Banquet (Yeongju Hall A, 1F)	

July 17 (Fri.), 2026		
Time	Room A	Room B
	Baekrok Hall A, 1F	Baekrok Hall B, 1F
09:00–09:50	Plenary Talk 5 (Yeongju Hall A, 1F) Prof. Okhyun Nam (Tech University of Korea, Republic of Korea) "Heteroepitaxial Strategies for Wide- and Ultrawide-Bandgap Semiconductors: From III–Nitrides to Diamond"	
09:50–10:20	Break	
10:20–12:05	[FrA1] Nanowires	[FrB1] Emerging Nitrides
12:05–12:35	Closing & Awards Ceremony (Lucky Draw) (Yeongju Hall A, 1F)	

Floor Plan

1F





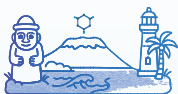
ICMOVPE XXII

The 22nd International Conference on Metal Organic Vapor Phase Epitaxy

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ICMOVPE XXII
July 12(Sun.)-17(Fri.), 2026
ICC JEJU, Jeju Island, Korea

I . Welcome Message





I. Welcome Message



On behalf of the ICMOVPE XXII Organizing Committee, I am pleased to welcome you to the 22nd International Conference on Metal Organic Vapor Phase Epitaxy (ICMOVPE XXII). The conference will be held July 12–17, 2026, at the International Convention Center Jeju (ICC JEJU) on Jeju Island, Korea.

Since the conference was first initiated in 1981 in Ajaccio, France, it has matured into a premier global forum where researchers and experts share insights, present cutting-edge research, and explore innovative concepts in both the fundamental and applied aspects of MOVPE. Held on a biennial rotation among the USA, Asia, and Europe, ICMOVPE continues to play a pivotal role in advancing the science and technology of epitaxy.

Having successfully hosted ICMOVPE–XVI in 2012 in Busan, we are honored to welcome the conference back, this time on the scenic island of Jeju in 2026. We hope to create an inspiring atmosphere for scientific exchange, collaboration, and the pursuit of new discoveries.

We are pleased to present a comprehensive program that covers a broad spectrum of topics, including Growth Studies, III–V Materials, Oxides and Dielectrics, Atomic Layer Deposition, Etching, and related fields. ICMOVPE XXII will feature the traditional plenary and invited talks, oral and poster sessions, rump sessions, and industrial exhibitions, complemented by social events infused with Korean culture and hospitality.

We believe that ICMOVPE XXII will serve as a dynamic platform that brings together researchers, engineers, and professionals from industry, academia, and national laboratories around the world. The conference will offer a vibrant environment to showcase the latest achievements, exchange ideas, and foster collaborations in MOVPE and related epitaxial growth technologies.

We sincerely welcome you to ICMOVPE XXII and hope that your time in Jeju will be both productive and memorable.

Sincerely,
Prof. Yong-Hoon Cho

Conference Chair of ICMOVPE XXII



A stylized illustration of a tropical island with various landmarks like a volcano, temples, and a waterfall, surrounded by a blue grid pattern. The island is green with a central volcano, two stone temples, a waterfall, and a small boat. The background is a light blue grid.



II. Committee

Organizing Committee

Conference Chair	Yong-Hoon Cho (KAIST, Korea)
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Joan Redwing	The Pennsylvania State University, USA
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Simon Watkins	Simon Fraser University, Canada
Markus Weyers	Ferdinand-Braun-Institute, Germany
Xiangang Xu	Shandong University, China
C.C. Yang	National Taiwan University, Taiwan



III.

Plenary Talks



III. Plenary Talks

Plenary Talk 1

Yeongju Hall A, 1F

July 13 (Mon.) 09:15–10:05

Session Chair Prof. Jong Kyu Kim (POSTECH, Korea)



Refreshing the Social Infrastructure with MOVPE

Prof. Hiroshi Amano
Nagoya University, Japan

Abstract

Metalorganic vapor phase epitaxy (MOVPE) plays a central role in the growth of compound semiconductor wafers—arsenides, phosphides, nitrides, and their heterostructures and quantum structures—used in highfrequency electronics, photonics, lighting, and display devices. These devices support modern society by enabling wireless and optical communication networks, linking Si LSI chips, providing highquality fullcolor displays, and realizing sustainable solidstate lighting. In this sense, MOVPE has become a foundational technology that underpins our social infrastructure. In contrast to these well-established application fields, power electronics has historically been dominated by Si and SiC-based devices. Recently, however, MOVPE-grown GaN high-electron-mobility transistors (HEMTs) on Si substrates have begun to transform this landscape. GaN-on-Si HEMTs offer MHz-order and higher switching speeds, enabling the marked miniaturization of power converters. This technology has led to compact AC adapters for PCs and smartphones, and is opening new markets for highfrequency power conversion. Nevertheless, the controllable power of lateral GaN-on-Si HEMTs remains limited to the 60–600 W range because the current-carrying area is restricted to the interface between the barrier and channel layers. Achieving higher breakdown voltages requires increasing the chip size, which constrains scalability. To extend the impact of MOVPE-grown nitride semiconductors to highpower electrical equipment and even power-grid-level systems, the development of vertical GaN power devices with thick, high-purity drift layers and fine-pitch device structures is essential.



Natural GaN substrates and Qromis Substrate Technology offer promising platforms for realizing such vertical GaN devices. However, growing thick, highpurity drift layers by MOVPE remains a major challenge due to carbon incorporation from metal-organic precursors. Overcoming this limitation is critical for realizing nextgeneration, highpower GaN/GaN devices. In this presentation, I will discuss recent progress and remaining challenges in MOVPE growth for vertical GaN power electronics, and explore pathways toward their future implementation in societal infrastructure.

I would like to thank all my colleagues, especially Professors Yoshio Honda, Jun Suda, Manabu Arai, Atsushi Tanaka, Manato Deki, and Maki Kushimoto for fruitful discussions. This work was partly supported by the MEXT program for the Creation of Innovative Core Technology for Power Electronics, (grant no. JPJ009777), the JST ASPIRE program (grant no. JPMJAP2311), and the Japan Society for Promotion of Science KAKENHI (grant nos. 22J15656 and JPH00213).

Biography

Professor Hiroshi Amano received Doctor of Engineering from Nagoya University. Currently he is a Director, Center for Integrated Research of Future Electronics, and a Professor, Institute of Materials and Systems for Sustainability, Nagoya University.

He shared the 2014 Nobel Prize in Physics with Prof. Isamu Akasaki and Prof. Shuji Nakamura "for the invention of efficient blue light-emitting diodes which has enabled bright and energy-saving white light sources". He is currently developing technologies for the fabrication of high-efficiency power semiconductor development and new energy-saving devices at Nagoya University.

Plenary Talk 2

Yeongju Hall A, 1F

July 13 (Mon.) 10:05–10:55

Session Chair Prof. Jun Seok Ha (Chonnam National University, Korea)



Advances in MOCVD for Epitaxial Growth of Wafer-Scale 2D Transition Metal Dichalcogenides

Prof. Joan Redwing

The Pennsylvania State University, USA

Abstract

Two-dimensional (2D) semiconducting transition metal dichalcogenides (TMDs), exemplified by materials like MoS₂ and WSe₂, have garnered increasing interest for next generation electronics such as gate-all-around nanosheet transistors, neuromorphic devices and sensors/imagers heterogeneously integrated with silicon CMOS technology. The interest in semiconducting TMDs arises from their atomically thin nature and passivated van der Waals surfaces, however, realization of high-performance devices requires advances in TMD synthesis to provide wafer-scale films that can be readily integrated into devices via either direct growth or layer transfer methods.

Our work has focused on the development of metalorganic chemical vapor deposition (MOCVD) as a manufacturing-compatible approach for wafer-scale semiconducting TMDs. The TMDs are grown epitaxially on 2" diameter c-plane sapphire by MOCVD at elevated temperatures (>800 °C) to obtain high crystal quality. Nucleation of TMDs on sapphire is intimately tied to the surface structure and the growth chemistry which can be controlled to achieve unidirectional TMD domains with a significant reduction in mirror twin domains in coalesced films. In situ spectroscopic ellipsometry is demonstrated to be an effective real time monitor of TMD growth even at the sub-monolayer level which can be exploited to track surface coverage as a function of time under varying growth conditions. The ability to precisely control and modulate precursor flux during growth is used to synthesize in-plane heterostructures that enable localized exciton confinement and emission. Applications for wafer-scale TMD monolayers in nanoelectronics, sensing and photonics will be discussed.



Biography

Joan Redwing is a Distinguished Professor of Materials Science and Engineering and Electrical Engineering at Penn State University. She currently serves as Director of the 2D Crystal Consortium (2DCC), an NSF Materials Innovation Platform national user facility in the U.S. that is focused on advancing the synthesis and characterization of 2D materials for next generation devices. Her research focuses on crystal growth and epitaxy of electronic materials, with an emphasis on thin film and nanomaterial synthesis by metalorganic chemical vapor deposition. She is a fellow of the Materials Research Society, the American Physical Society, and the American Association for the Advancement of Science. She is an author on over 350 publications in refereed journals and holds 8 U.S. patents.

Plenary Talk 3

Yeongju Hall A, 1F

July 15 (Wed.) 08:30~09:20

Session Chair Prof. Young-Joon Hong (Sungkyunkwan University, Korea)



Status and Future Trends of Metalorganic Chemical Vapor Phase Deposition

Prof. Michael Heuken

AIXTRON & RWTH Aachen University, Germany

Abstract

Compound semiconductor devices – such as those made from materials like Gallium Arsenide (GaAs), Indium Phosphide (InP), and Gallium Nitride (GaN) play a crucial role in advancing technologies that align with several United Nations Sustainable Development Goals. To enable LED for solid state lighting applications, advanced multi junction solar cells or power saving transistor technologies we developed the Metalorganic Chemical Vapor Phase Deposition (MOCVD or MOVPE) technology for III-As/P/N based structures in MOCVD-systems ranging from small scale to large production scale reactors. This technology enables the industrial introduction of high-volume device families which require dedicated layer sequences with exactly specified properties uniformly distributed across wafer diameter up to 300 mm.

The requirements for the process equipment are manifold, demanding utmost control of purity, composition and interfaces, dopant and layer thickness uniformity and low defect density of the epitaxial quantum structures. Besides layer quality, the ability to manufacture the device layer stacks reproducibly and economically is crucial to support the growing demand.

The focus of epitaxy production technology developments based on scientific understanding has been put on material properties close to the physical limit, improved process control, productivity enhancement concepts like wafer level automation, in-situ metrology to acquire process data for smart system control and predictive maintenance concepts. A comprehensive summary and recent progress in cost-down strategies and improved technical specifications will be reported here. The application of the underlying physical, technical and chemical fundamentals supports the engineering approaches to achieve economic, technical, and scientific objectives.



The upcoming new 2D materials classes such as transition metal dichalcogenides (TMDC) or graphene will find their application in electronic and optoelectronic devices such as memristive devices for energy efficient neuromorphic computing and quantum sensors or in sub 2 nm CMOS like AI chips.

The application of the detailed understanding of the fundamentals of MOCVD, consequently designing and optimizing epitaxial equipment and processes and managing their transfer to industry will be explained by using several examples such as these novel 2D materials.

Biography

Prof. Dr. Michael Heuken was born in Germany on November 17, 1961. He received the Graduate Engineer degree and the Doctor of Engineering degree in Electrical Engineering from Duisburg University in 1985 and 1989, respectively. He joined the Institute of Semiconductor Electronics at RWTH Aachen University and has been working in the field of metalorganic vapor phase epitaxy for electronic and optoelectronic devices. He has been lecturer for semiconductor technology and devices as well as circuits for communication systems at RWTH. In 1997 he joined AIXTRON in Aachen/Germany where he is now Vice President Advanced Technologies. In 1999 he was honored as Professor at RWTH Aachen University. His experience is in the field of semiconductor growth by MOVPE. Prof. Heuken is co-author of more than 750 publications in international journals and several invited papers at international conferences. He was President of German Crystal Growth Association, he served as elected Executive Committee Member of the IOCG, he is member of VDE/ITG. Currently he serves as Board Member of NMWP e.V. and Advanced UV for Life e.V. He acts as referee for international journals and supports several organizations as an expert. Prof Heuken has been granted several patents in the field of semiconductor technology. The scientific contributions to compound semiconductor technology especially MOCVD were recognized by the Laudise-Price of the IOCG in 2025.

Plenary Talk 4

Yeongju Hall A, 1F

July 15 (Wed.) 09:20–10:10

Session Chair Prof. Yong-Ho Ra (Jeonbuk National University, Korea)



Near-Perfect Quantum Efficiency InGaN LEDs through Growth Engineering

Prof. Nicolas Grandjean
EPFL, Switzerland

Abstract

Blue light-emitting diodes (LEDs) based on III-V nitride semiconductors have enabled the creation of semiconductor light sources with a luminous efficiency ten times greater than that of incandescent light bulbs [1]. Nowadays, these LEDs are ubiquitous in lighting applications. They have sparked a technological revolution that has significantly reduced global electricity consumption.

A remarkable feature of blue LEDs is their exceptionally high internal quantum efficiency, close to 100% at room temperature, despite an enormous dislocation density, on the order of 10^8 cm^{-2} , inherited from the epitaxial growth of GaN on foreign substrates such as sapphire [2]. To understand this apparent paradox, we need to look at the properties of InGaN/GaN quantum wells (QWs), which form the core of these devices. It was first explained that carriers are localized in random alloy potential fluctuation minima and thereby cannot diffuse toward dislocations [3]. Then it was proposed that the formation of V-shaped pits around the dislocations creates an energy barrier for carriers that hinders their recombination onto the dislocations [4]. In addition to extended defects, impurities and/or native point defects could potentially be non-radiative recombination centers (NRCs) and impair the efficiency of III-nitride LEDs [5,6].

In this presentation, we will begin by discussing the actual epitaxial structure of state-of-the-art blue LEDs. It is interesting to note that they all feature an InGaN layer (or an InGaN/GaN superlattice) beneath the active QW region. We will show that this InGaN underlayer is a prerequisite for obtaining InGaN/GaN QWs with high quantum efficiency. Its role is to trap surface defects generated during the high-temperature growth of GaN by metal-organic vapor phase epitaxy [7,8]. We will demonstrate that these surface defects depend on the growth temperature and react with indium atoms to create NRCs when



incorporated into InGaN/GaN QWs. The nature of these defects will be revealed by growth experiments. We will then propose a growth mechanism that explains the surface segregation of these surface defects and their incorporation as an NRC center in the InGaN layers. Finally, we will show that high-efficiency blue LEDs require careful growth optimization: i) screening of threading dislocations by forming topological defects (V-shaped pits) and ii) trapping of surface defects generated during high-temperature growth of the GaN buffer. The prospects for extreme wavelength III-nitride-based LEDs, i.e., the UV-C and red wavelength ranges, will also be discussed.

Biography

Nicolas Grandjean received his PhD in physics from the University of Nice–Sophia Antipolis in 1994 and subsequently joined the French National Centre for Scientific Research (CNRS) as a staff scientist. In 2004, he was appointed tenure-track assistant professor at the École polytechnique fédérale de Lausanne (EPFL), where he founded the Laboratory for Advanced Semiconductors for Photonics and Electronics. He was promoted to full professor in 2009. From 2012 to 2016, he served as Director of the Institute of Condensed Matter Physics at EPFL and was a visiting professor at the University of California, Santa Barbara, in 2016. Between 2018 and 2022, he headed the EPFL School of Physics. In 2025, he was appointed Associate Vice-President for Education. Professor Grandjean has received numerous distinctions, including the Sandoz Family Foundation Grant for Academic Promotion, the Nakamura Lecturer Award (2010), the Quantum Devices Award at the 2017 Compound Semiconductor Week, and the EPFL Best Teacher Award in 2022. He has authored more than 600 peer-reviewed publications and has delivered plenary talks at major international conferences. His research focuses on the physics and technology of III-V nitride wide-bandgap semiconductors.

Plenary Talk 5

Yeongju Hall A, 1F

July 17 (Fri.) 09:00–09:50

Session Chair Prof. Si-Young Bae (Pukyong National University, Korea)



Heteroepitaxial Strategies for Wide- and Ultrawide-Bandgap Semiconductors: From III-Nitrides to Diamond

Prof. Okhyun Nam
Tech University of Korea, Korea

Abstract

Wide-bandgap (WBG) and ultrawide-bandgap (UWBG) semiconductors are emerging as foundational materials for next-generation high-power, high-frequency, high-temperature, and extreme-environment electronics. However, their development has been fundamentally constrained by the lack of large-area native substrates and by severe lattice and thermal mismatches that generate defects, strain, cracking, and wafer bow during heteroepitaxial growth. As a result, heteroepitaxy has evolved beyond a growth technique into a central strategy for semiconductor platform engineering.

This plenary talk presents heteroepitaxial strategies as a unified framework for defect reduction, strain and interface engineering, and hybrid material integration across WBG and UWBG semiconductor systems. In III-nitrides, epitaxial lateral overgrowth (ELO) and pendeo epitaxy enabled substantial reductions in threading dislocation densities, providing critical pathways toward high-efficiency LEDs and blue-violet laser diodes. Advanced AlN-based buffer and interface engineering further enabled deep-UV AlGaN optoelectronics and AlGaN heterostructure transistors designed for extreme-environment operation.

The talk will also discuss (100)- and (111)-oriented diamond heteroepitaxy on sapphire and the development of large-area single-crystal diamond as a potential ultimate UWBG semiconductor platform. Finally, initial feasibility studies of nitride epitaxy on diamond substrates will be presented, together with future perspectives for monolithic hybrid electronics.

These studies suggest that advanced heteroepitaxial technologies may provide a future pathway toward the integration of III-nitrides and diamond for next-generation extreme-environment semiconductor platforms.



Biography

Okhyun Nam is the professor in the department of Semiconductor Engineering at the TU-Korea (Tech University of Korea) and the R&D director of Alchemist Project, South Korea.

His teaching and research interests are in the areas of the ultra-wide bandgap semiconductors such as AlGa_N and Diamond, and their device growth and fabrications for the electronic and optoelectronic applications.

After obtaining a Ph.D. from Yonsei University in South Korea in 1994, Professor Nam has studied the III-nitride semiconductors at the KIST between 1994–1995 and North Carolina State University between 1995–1998, as a post-doctoral researcher. At this time, he invented the SAE and ELO technology of GaN on a foreign substrate that made it possible to dramatically improve the performance of LDs and LEDs.

After that, he joined SAIT (Samsung Advance Institute of Technology). As a project leader, he has investigated and developed III-Nitride blue laser diodes between 1998–2007 at the SAIT. In 2004, He achieved high power blue-violet laser diode development based on III-Nitride semiconductors and took the SAMSUNG Technology Award. Also, he continued to develop the blue and green laser diode based on InGa_N semiconductors.

In 2007, He moved to the department of semiconductor engineering at Tech University of Korea and continued to work nitride semiconductor studies such as LEDs and LDs.

From 2015, He started Nitride power device growth and fabrication research, and 2018, Diamond semiconductor heteroepitaxy for large-size wafer and power devices/quantum devices.

So far, has published over 205 international journal papers and has over 65 patents in the wide bandgap and ultra-wide bandgap semiconductors.

Now, he has been working as the R&D director of the Korean National Research Projects (Alchemist Project) of “Diamond-based Ultimate Semiconductors for Space & Extreme Environmental Applications” during 2024–2030.



IV.

Rump Session





IV. Rump Session

July 15 (Wed.), 2026 / 19:00–20:30

Room A (Baekrok Hall A, 1F)

Rump Session 1

Topic Materials and Epitaxy Challenges in III-V Nitride Semiconductors for LEDs and Power Devices/HEMTs

Short Description This rump session will provide an open forum for discussing recent advances, key technical challenges, and future perspectives in III-nitride semiconductors and their epitaxial growth technologies. Particular emphasis will be placed on epitaxy-related issues and enabling technologies required for the realization of high-performance LEDs, power devices, and RF electronics. The session aims to stimulate active discussion on materials growth, device integration, and emerging directions for next-generation III-nitride-based technologies.

Moderator Prof. Nicolas Grandjean (EPFL, Switzerland)

Panelists

- Prof. Tim Wernicke (Technische Universität Berlin, Institute of Physics and Astronomy, Germany)
- Dr. Isabel Streicher (Cornell University, United States)
- Prof. Motoaki Iwaya (Meijo University, Japan)
- Dr. Byeongchan So (Fraunhofer Institute for Applied Solid State Physics IAF, Freiburg, Germany)
- Prof. Qian Sun (Suzhou Institute of Nano-Tech and Nano-Bionics, Chinese Academy of Sciences, China)
- Prof. Narihito Okada (Yamaguchi University, Japan)

Sub-Topic

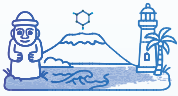
- Defect Engineering in III-Nitride Epitaxy for Advanced Device Applications
- Epitaxy-Driven Performance Limits in III-Nitride LEDs and Light-Emitting Devices
- Micro-LED Technologies for Displays and Optical Interconnects
- Current Challenges in GaN/AlGaN RF and Power Electronics

July 15 (Wed.), 2026 / 19:00–20:30

Room B (Baekrok Hall B, 1F)

Rump Session 2

Topic	Next big thing in MOCVD – 2D, ML/AI and MOCVD itself
Short Description	Next big thing in MOCVD – 2D, ML/AI and MOCVD itself. This session explores the dual frontiers of MOCVD: achieving wafer-scale 2D material epitaxy and the technological evolution of MOCVD systems and processes themselves. The discussion aims to provide a strategic roadmap for integrating emerging materials, machine learning/AI and industrial-scale manufacturing over the next decade.
Moderator	Prof. Joan Redwing (The Pennsylvania State University, USA)
Panelists	• Prof. Ryota Akaike (Mie University, Japan) • Prof. Michael Heuken (AIXTRON & RWTH Aachen University, Germany) • Prof. Vanya Darakchieva (Lund University, Sweden) • Dr. Benjamin Groven (IMEC, Belgium) • Dr. Emanuele Pelucchi (Tyndall National Institute–University College Cork, Ireland) • Prof. Suresh Sundaram (Georgia Tech Europe, France)
Sub-Topic	1. Breaking the Barriers in 2D Epitaxy: Strategies for defect control and grain size enhancement in wafer-scale 2D material growth via MOCVD. 2. The Rise of Autonomous MOCVD (Engineering AI): The role of Machine Learning and real-time feedback loops in accelerating process optimization and achieving "zero-defect" growth. 3. Industrial Scalability & Sustainability: Bridging the gap between lab-scale breakthroughs and high-volume manufacturing (HVM) while addressing precursor efficiency and environmental impacts. 4. Cultivating Future 'Growers': How to evolve MOCVD education and training to attract the next generation of researchers in an increasingly digitalized semiconductor era.



ICMOVPE XXII

July 12(Sun.)-17(Fri.), 2026

ICC JEJU, Jeju Island, Korea

V. Technical Program



1. Information on the Technical Program

1) Oral Presentation Guidelines

- ① The authors of abstracts accepted for oral presentation are asked to bring Powerpoint (or PDF) slides and present their research in a podium presentation.

[Presentation Time]

Presentation Type	Presentation Time
Plenary Talk	50 min. including Q&A
Invited Talk	30 min. including Q&A
Oral Talk	15 min. including Q&A

- ※ Session rooms will be ready with laptop computers installed with MS PowerPoint, which the speakers are encouraged to use for their presentations in order to avoid delays in schedule. (It is not recommended to bring your own laptop computer (especially MacBook) unless your presentation requires any special software and/or hardware)
 - ※ The speakers are advised to bring their PowerPoint presentation files on USB memory sticks and be also ready with a backup version of their presentations.
 - ※ Please transfer the file to the laptop computer in the session room during the break before the sessions
- ② Speakers are expected to arrive at the session room 15 minutes before the start of their sessions to report to the session chair.

2) Poster Presentation Guidelines

① Presentation Location & Time

Title	Session	Venue	Topics	Date	Set-up	Presentation	Removal
Poster Session 1	TuP	Room C (Event Hall A, 1F)	Topic 2, 3	Jul. 14 (Tue.)	13:00-16:00	16:00-17:40	17:40-18:10
Poster Session 2	WeP	Room C (Event Hall A, 1F)	Topic 1, 4	Jul. 15(Wed.)	13:00-17:00	17:10-18:40	18:40-19:00

② Presentation Guidelines

- ※ Please note that the venue does not provide printing facilities for posters.
- ※ The materials for displaying such as scissors, scotch tapes, and thumb tacks will be provided in the hall.
- ※ Please post your posters on the board that matches your abstract number.
Q&A for Posters will be conducted on-site.
- ※ Please remove your poster at the designated removal time. Any posters left behind will be discarded without notice.

V. Technical Program

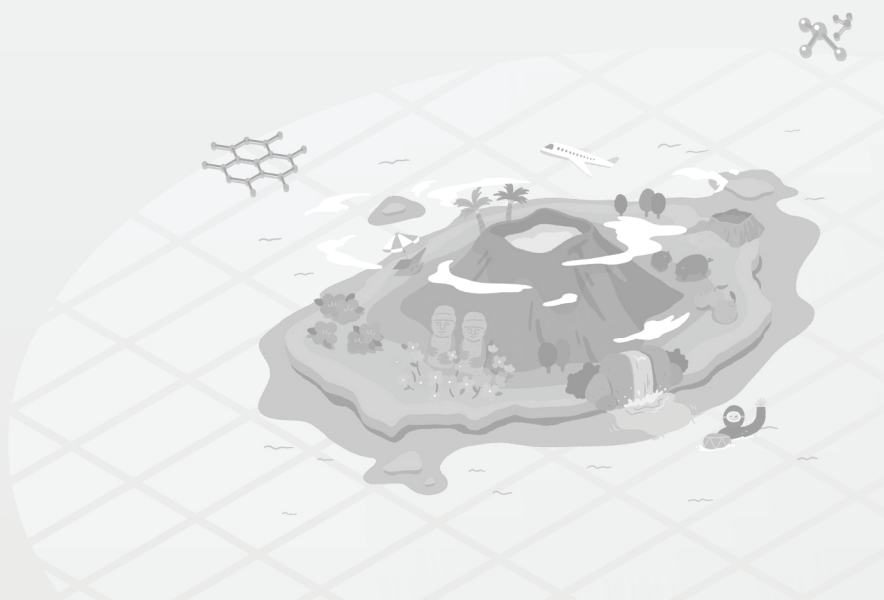
2. Technical Sessions

ICMOVPE-XXII

The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

July 13, 2026
[Monday]

Oral Session



[MoA1] 2D Materials - I

Session Date	July 13 (Mon.), 2026
Session Time	11:15–12:30
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Dr. Benjamin Groven (IMEC, Belgium), Prof. Kerstin Volz (Philipps–University Marburg, Germany)

[MoA1–1] [Invited]

11:15–11:45

From MOCVD to AI-Driven Metrology: Enabling Scalable Production and Quality Control of Wafer-Scale 2D Semiconductors

Xiaotian Zhang, Suzhou Laboratory, China

[MoA1–2] [Invited]

11:45–12:15

Scalable MOVPE van der Waals Epitaxy of hBN for III–Nitride Devices: From Mixed 2D/3D Heterostructures to RGB Micro–LEDs and Deep–UV LEDs

Suresh Sundaram^{1,2}, Phuong Vuong^{1,2,3}, May Tran Thi², Ashuthosh Srivastava^{1,2}, Tarik Moudakir⁴, Simon Gautier⁴, Paul L. Voss^{1,2}, Jean Paul Salvestrini^{1,2}, and Abdallah Ougazzaden^{1,2}, ¹Georgia Tech–Europe, France, ²Georgia Tech–CNRS IRL 2958, France, ³Georgia Institute of Technology, USA, ⁴Institut Lafayette, France

[MoA1–3]

12:15–12:30

MOCVD Growth of Suspended hBN on GaN Nano–Needles for Analog Memristive Switching via Geometric Filament Confinement

Seokho Moon¹, Jaesub Song², Odongo Francis Ngome Okello¹, Adrien Rousseau³, Semi Im², Jawon Kim², Inyong Hwang², Changuk Ji², Jinho Byun², Jiye Kim², Junyoung Choi², Hyunjeong Kwak², Seyoung Kim², Bernard Gil³, Guillaume Cassabois³, Si-Young Choi², and Jong Kyu Kim², ¹Ajou University, Korea, ²Pohang University of Science and Technology, Korea, ³Universite de Montpellier, France

**[MoB1] Nitrides for Electronics - I**

Session Date	July 13 (Mon.), 2026
Session Time	11:15–12:30
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Xiaohang Li (King Abdullah University of Science and Technology, Saudi Arabia), Prof. Markus Pristovsek (Nagoya University, Japan)

[MoB1–1] [Invited]

11:15–11:45

Recent Progress and Device Advantages of N-Polar GaN/AlN HEMTs

N. Okada¹, F. Yamanaka¹, A. H. Zazuli¹, M. Feng¹, T. Kimoto¹, R. Ninoki¹, N. Hirata¹, H. Danbata¹, A. Hayashiuchi¹, K. Sunai¹, H. Tokumoto¹, Y. Kitamura¹, S. Kurai¹, M. Hiroki², K. Hirama², Y. Taniyasu², and Y. Yamada¹, ¹Yamaguchi University, Japan, ²NTT, Inc., Japan

[MoB1–2] [Invited]

11:45–12:15

MOCVD Growth of III-Nitride Using New Precursors for HEMT: Challenges and Progress

Byeongchan So, Teresa Duarte, Hanspeter Menner, Jannik Richter, Lutz Kirste, Mario Prescher, Patrik Straňák, Sven Maegdefessel, Felix Hoffmann, Fouad Benkhelifa, Stefano Leone, and Rüdiger Quay, Fraunhofer Institute for Applied Solid State Physics IAF, Germany

[MoB1–3]

12:15–12:30

Tunable High-Temperature MOCVD Growth for Strain-Controlled AlN-Based RF GaN HEMT Epitaxy

JongJin Jang, SeongCheol Choi, and DongSik Seo, TES Co., Ltd., Korea

[MoA2] Advanced Growth Techniques - I	
Session Date	July 13 (Mon.), 2026
Session Time	14:00–15:45
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Zhe Zhuang (Nanjing University, China), Prof. Michael Heuken (AIXTRON, RWTH Aachen University, Germany)

[MoA2–1] [Invited]

14:00–14:30

Remote Epitaxy of Deformable and Stacktronic Devices

Young Joon Hong, Sungkyunkwan University, Korea

[MoA2–2]

14:30–14:45

Fabrication of Wafer-Scale Freestanding GaN Membrane Utilizing Transfer-Free Thin Amorphous Carbon Layer via MOCVD-Based Remote Epitaxy

Joonghoon Choi, Wonkwang Yang, Chang Soo Kim, Junhyun Bae, and Young Joon Hong, Sungkyunkwan University, Korea

[MoA2–3]

14:45–15:00

Remote Epitaxy of α -Ga₂O₃ via Polycrystalline MoS₂

Gyeong Ryul Lee and Roy. B. Chung, Kyungpook National University, Korea

[MoA2–4]

15:00–15:15

MOCVD of GaN and AlGaIn/GaN Heterostructures on Si(001) by Wafer-Scale MoS₂ Templates

Seung Hoon Lee¹, Chen Chen¹, Brian M. Bersch², and Joan M. Redwing¹, ¹Pennsylvania State University, USA, ²Northrop Grumman Mission Systems, USA

[MoA2–5]

15:15–15:30

InGaIn Quantum Wells Grown on Spatially Patterned Substrates – Towards the 3D Laser Emitters

Grzanka Ewa, Grzanka Szymon, Robert Czernecki, Mikołaj Grabowski, Roman Hrytsak, Artur Lachowski, Julita Smalc-Koziorowska, and Michał Leszczynski, Institute of High Pressure Physics, Poland



[MoA2-6]

15:30-15:45

Room-Temperature Continuous-Wave III-V/Si PhC Lasers on SOI Using Selective Lateral Heteroepitaxy

Xingyu Yang, Yao Chen, Jinglong Chen, Siyuan Yu, and Yu Han, Sun Yat-sen University, China

[MoB2] Micro-LEDs	
Session Date	July 13 (Mon.), 2026
Session Time	14:00–15:45
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Xinqiang Wang (Peking University, China), Dr. Armin Dadgar (Otto-von-Guericke-Universität Magdeburg, Germany)

[MoB2-1] [Invited]

14:00–14:30

In Incorporation and Strain Relaxation for Efficient Red InGaN Micro-LEDs: Towards a RGB Monolithic Approach

A. Dussaigne, J. Bosch, F. Barbier, G. Veux, F. Fedeli, B. Aventurier, D. Cooper, F. Rol, and F. Lévy, CEA-Leti, France

[MoB2-2] [Invited]

14:30–15:00

Enhancing Luminous Efficiency: The Breakthrough of PlayNitride's Tantium® MicroLED

Ching-Liang Lin¹, Yi-Ru Huang², Chia-Yun Kao², and Yun-Li Li¹, ¹Playnitride Inc., Taiwan, ²Playnitride display Co. Ltd., Taiwan

[MoB2-3]

15:00–15:15

GaN-on-Si Single-Chip Full-Color Micro-LED Display

Qian Sun^{1,2}, ¹Suzhou Legin Semiconductor Co., Ltd., China, ²Chinese Academy of Sciences, China

[MoB2-4]

15:15–15:30

Wafer Scale Fabrication of Three-Dimensional InGaN/GaN Nanostructured Quantum Wells for Enhanced Color Controllability of Micro-LEDs

Mandar Kulkarni and Sang-Wan Ryu, Chonnam National University, Korea



[MoB2-5]

15:30-15:45

Ideal Relaxed InGaN Templates Enabling Ultra-Bright RGB-Emitting MicroLEDs

Zhaoxia Bi^{1,2,3,4}, Magnus Heurlin³, Martin Berg³, Hira Usman¹, Nathanael Löfström^{1,2,3}, Jiawei Sun¹, Anders Gustafsson^{1,2}, Mikael Björk³, and Lars Samuelson^{1,2,3}, ¹Southern University of Science and Technology, China, ²Lund University, Sweden, ³Hexagem AB, Sweden, ⁴Future Display Institute of Xiamen, China

[MoA3] Arsenides

Session Date	July 13 (Mon.), 2026
Session Time	16:05–18:05
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Dr. Jean Decobert (III–V Lab, France), Dr. David Lackner (Fraunhofer Institut für Solare Energiesysteme ISE, Germany)

[MoA3–1] [Invited]

16:05–16:35

An Old Technology Which Still Surprises. III–Vs MOVPE, Precursors, Surface Processes and a Lot of Zinc and Oxygen

Emanuele Pelucchi¹, Camille Barbier¹, Agnieszka Gocalinska¹, Pawel P. Michalowski², John O'Hara¹, Luca Colavecchi¹, Gediminas Juska¹, Adrianna Rejmer², and Ayse Ozcan-Atar¹, ¹Tyndall National Institute, University College Cork, Ireland, ²Lukasiewicz Research Network, Poland

[MoA3–2]

16:35–16:50

Accurate Prediction of Intersubband Transitions in MOVPE–Grown III–V Asymmetric Coupled Quantum Wells

K. Pantzas¹, V. Trinité², A. Vasanelli³, C. Sirtori³, G. Beaudoin¹, J. L. Reverchon², G. Patriarche¹, and I. Sagnes¹, ¹Université Paris–Saclay, France, ²III–V Lab, France, ³Laboratoire de physique de L'École normale supérieure de Paris, France

[MoA3–3]

16:50–17:05

MOVPE–Grown C–Band Emitting InAs Quantum Dots on a Ge–Buffered Si (001) Substrate

P. Vijayan, M. Jetter, and P. Michler, Universität Stuttgart, Germany

[MoA3–4]

17:05–17:20

Development of AlAsP/GaAs Microcavities with Narrow Linewidth InGaAs QWs

N. J. Bailey, P. M. Walker, S. Lovett, L. Eaton, D. N. Krizhanovskii, and J. Heffernan, University of Sheffield, United Kingdom



[MoA3-5]

17:20-17:35

III-V/Germanium Photovoltaic Cells via MOVPE: Applications in Thermophotovoltaics and Laser Power Converters

Rey-Stolle, Pablo Martín, Aitana Cano, Rubén Fortín, Romain Foucher, Lidia Escanciano, and Iván García, Universidad Politécnica de Madrid, Spain

[MoA3-6]

17:35-17:50

MOVPE Growth and Characterization of GaAs-Based PIN Diodes for RF Applications

Simeon N. Vladimirov, Lidia Escanciano, Iván García, and Ignacio Rey-Stolle, Universidad Politécnica de Madrid, Spain

[MoA3-7]

17:50-18:05

Sculpturing Potential of Bound State in the Continuum Exciton-Polariton Condensates based on MOCVD-Grown Multi Quantum Well

Jaewon Kim¹, Daegwang Choi², Hyungyu Song¹, and Yong-Hoon Cho¹, ¹Korea Advanced Institute of Science and Technology, Korea, ²Gachon University, Korea

[MoB3] Optical Characterization	
Session Date	July 13 (Mon.), 2026
Session Time	16:05–17:50
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Tetsuya Takeuchi (Meijo University, Japan), Dr. Frank Brunner (Ferdinand-Braun-Institute, Germany)

[MoB3–1] [Invited]

16:05–16:35

Optical In-Situ Metrology and MOVPE: Versatile Toolbox for Laser Device Growth

A. Maaßdorf, M. Brendel, S. Breuer, and M. Weyers, Ferdinand-Braun-Institut, Germany

[MoB3–2]

16:35–16:50

Composition-Dependent Raman Anisotropy in MOVPE-Grown Non-Polar (11-20) $\text{Al}_x\text{Ga}_{1-x}\text{N}$

A Azizur Rahman¹, Eeshika Suresh^{1,2}, Maheshwar Gokhale¹, Amit P Shah¹, Kailash Rustagi¹, and Arnab Bhattacharya¹, ¹Tata Institute of Fundamental Research, India, ²Amrita Vishwa Vidyapeetham, India

[MoB3–3]

16:50–17:05

Optical Response and Anisotropy in MOVPE-Grown Non-Polar $\text{Al}_x\text{Ga}_{1-x}\text{N}$: Insights from Mueller Matrix Ellipsometry

A Azizur Rahman¹, Sanchali Datta^{1,2}, Maheshwar Gokhale¹, Amit P Shah¹, and Arnab Bhattacharya¹, ¹Tata Institute of Fundamental Research, India, ²Tripura University, India

[MoB3–4]

17:05–17:20

WITHDRAWN

[MoB3–5]

17:20–17:35

Temperature- and Wavelength-Dependent Photoluminescence Lifetimes in InGaN Quantum Wells with Varying Indium Compositions

Ririka Yamagata¹, Soma Hatanaka¹, Soya Yamagishi¹, Itsuki Shimbo¹, Atsushi A. Yamaguchi¹, Kazunori Iwamitsu², and Shigetaka Tomiya², ¹Kanazawa Institute of Technology, Japan, ²Nara Institute of Science and Technology, Japan

**[MoB3-6]**

17:35-17:50

Functional-Form Analysis of Photoluminescence Decay in InGaN Quantum Wells

Arata Suzaki¹, Ririka Yamagata¹, Itsuki Shimbo¹, Atsushi A. Yamaguchi¹, Daisuke Iida², and Kazuhiro Ohkawa², ¹Kanazawa Institute of Technology, Japan, ²King Abdullah University of Science and Technology, Saudi Arabia

V. Technical Program

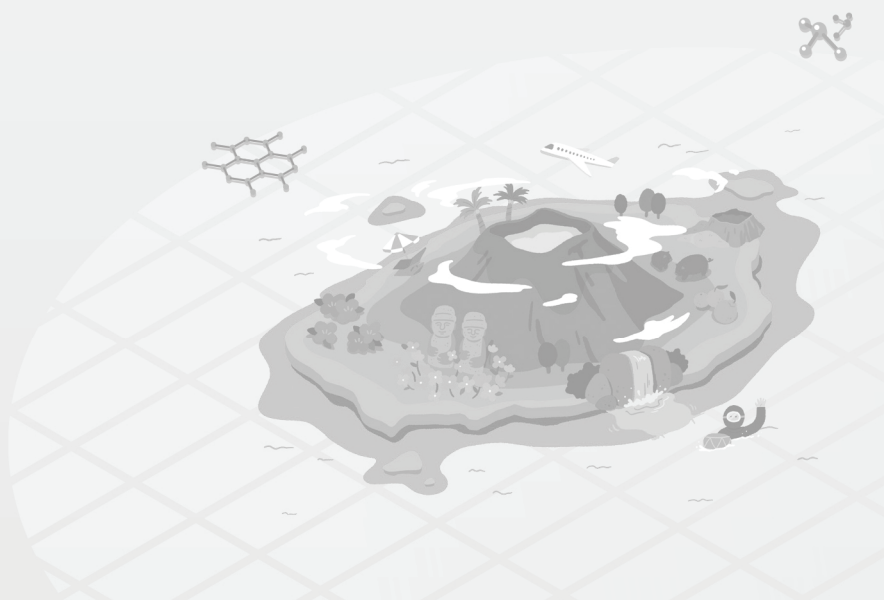
2. Technical Sessions

ICMOVPE-XXII

The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

July 14, 2026
[Tuesday]

Oral Session





[TuA1] Phosphides

Session Date	July 14 (Tue.), 2026
Session Time	08:30–10:15
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Dr. Emanuele Pelucchi (Tyndall National Institute, Ireland) Dr. Ameer Abdullah (KAIST, Korea)

[TuA1–1] [Invited]

08:30–09:00

Growth Management of InP-Based Optoelectronic and Microelectronic Devices on InP-on-Silicon (InPoSi) Wafers

C. Besancon¹, D. Néel¹, N. Vaissière¹, E. Izquierdo¹, A. Elias¹, G. Daccord¹, J.L. Reverchon¹, O. Delorme¹, A. Wilk¹, N. Davy¹, V. Nodjiadjim¹, C. Mismar¹, F. Fortunato², J. Bergsten³, H. Rodilla², B. Ghyselen⁴, L. Sanchez⁵, T. Bria⁵, F. Fournel⁵, and J. Decobert¹, ¹III–V Lab, France, ²Chalmers University of Technology, Sweden, ³Low Noise Factory, Sweden, ⁴SOITEC, France, ⁵CEA–Leti, France

[TuA1–2]

09:00–09:15

Impact of Growth Parameters on High Quality InP Microridges Grown Directly on On-Axis Si Substrates

T. Meyer¹, A. Baechele¹, M. Prescher¹, L. Kirste¹, R. Keil¹, M. Haertelt¹, P. Merkert¹, S. Messaoudène², L. Andreutti², M. Doron², B. Ben Bakir², A. Trampert³, and R. Aidam¹, ¹Fraunhofer Institute for Applied Solid State Physics IAF, Germany, ²CEA–Leti, France, ³Paul–Drude–Institut für Festkörperelektronik, Germany

[TuA1–3]

09:15–09:30

Orientation Patterned Gallium Phosphide for Integrated Nonlinear Photonics

B. Le Corre^{1,2}, S. Combré³, M. Millotte¹, G. Beaudoin¹, A. Harouri¹, L. Le Gratiot¹, I. Sagnes¹, B. Gérard⁴, A. De Rossi³, A. Grisard³, G. Patriarche¹, Y. Léger², and K. Pantzas¹, ¹Université Paris–Saclay, France, ²Université de Rennes, France, ³Thales Research and Technology, France, ⁴III–V Lab, France

[TuA1-4]

09:30-09:45

WITHDRAWN

[TuA1-5]

09:45-10:00

Resistive Ru-Doped InP Layers for Improved Semi-Insulating Buried Heterostructures

Gustavo Afonso, Nicolas Vaissiere, Antoine Elias, Cosimo Calo, Vladyslav Vakarin, Giancarlo Cerulo, Mokhtar Korti, Olivier Parillaud, Frederic Pommereau, and Jean Decobert, III-V Lab, France

[TuA1-6]

10:00-10:15

In-Situ Reflectometry and Curvature Monitoring for Process Control of InP-Based Laser Heterostructures Grown by MOVPE

K. Haberland¹, J. Decobert², N. Vaissiere², V. Bot², C. Besancon², and F. Weigert¹, ¹LayTec AG, Germany, ²III-V Lab, France



[TuB1] Lasers

Session Date	July 14 (Tue.), 2026
Session Time	08:30–10:15
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Dr. Andre Maaßdorf (Ferdinand-Braun-Institute, Germany) Dr. Nick Bailey (University of Sheffield, United Kingdom)

[TuB1-1] [Invited]

08:30–09:00

High Efficiency GaN-Based VCSELs with AlInN/GaN DBRs Grown by MOVPE

Tetsuya Takeuchi, Satoshi Kamiyama, and Motoaki Iwaya, Meijo University, Japan

[TuB1-2]

09:00–09:15

3.2-W InGaN-Based Photonic Crystal Surface Emitting Laser

Qian Sun, Chinese Academy of Sciences, China

[TuB1-3]

09:15–09:30

WITHDRAWN

[TuB1-4]

09:30–09:45

Extending the Concept of Quantum Mechanics to Bottom-Up Semiconductor Lasers

Wei Wen Wong, Xiaoying Huang, Jihua Zhang, Gaurang Garg, Olivier Lee Cheong Lem, Chennupati Jagadish, and Hoe Tan, The Australian National University, Australia

[TuB1-5]

09:45–10:00

A Novel Monolithic High-Contrast Grating VCSEL Grown by MOVPE for Near-Infrared Emission

Mikołaj Badura¹, Justyna Olejnik¹, Wojciech Dawidowski¹, Jan M. Śmigiel¹, Damian Radziejewicz¹, Adriana Łozińska¹, Marcin Gębski², Magdalena Marciniak², Tomasz Czystanowski², Weronika Głowadzka³, Marek Ekielski³, Iwona Sankowska³, Anna Szerling³, and Beata Ściana¹, ¹Wrocław University of Science and Technology, Poland, ²Lodz University of Technology, Poland, ³Łukasiewicz Research Network, Poland



[TuB1-6]

10:00-10:15

Design and Development of InGaN-Based VECSEL Structures for High-Power Single-Mode Green Emission

Lucja Marona, Szymon Grzanka, Agata Bojarska, and Piotr Perlin, Institute of High-Pressure Physics PAS, Poland

**[TuA2] Low-Dimensional Materials**

Session Date	July 14 (Tue.), 2026
Session Time	10:35–12:20
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Zaichun Sun (Wuhan University of Technology, China), Prof. Lars Samuelson (Southern University of Science and Technology, China)

[TuA2–1] [Invited]

10:35–11:05

Telecom C-Band InAs Quantum Dots on GaAs for Quantum Technological Application

Michael Jetter, Ponraj Vijayan, Stephanie Bauer, Robert Sittig, Raphael Joos, Nam Tran, Cornelius Nawrath, Sascha Kolatschek, Simone Luca Portalupi, and Peter Michler, University of Stuttgart, Germany

[TuA2–2]

11:05–11:20

Interlayer-Free Self-Assembled Growth of GaN Nanorods on Si Substrate for White Light-Emitting Diode

Ameer Abdullah¹, Jeong Ho¹, Sang-Wan Ryu², and Yong Hoon Cho¹, ¹Korea Advanced Institute of Science and Technology, Korea, ²Chonnam National University, Korea

[TuA2–3]

11:20–11:35

Exploring the MOVPE Growth of Droplet Epitaxy InAs/InP Quantum Dots for Quantum Photonic Applications

Elisa M. Sala¹, Young In Na¹, Raja S.R. Gajjala², Edoardo G. Banfi², Guoliang Zhou¹, Paul M. Koenraad², and Jon Heffernan¹, ¹The University of Sheffield, United Kingdom, ²Eindhoven University of Technology, Netherlands

[TuA2–4]

11:35–11:50

Growth of InGaAs Quantum Dots on GaAs with Emission at C-Band Wavelengths

Juwana Jose, David Nguyen, Christoph Berger, Jürgen Bläsing, Armin Dadgar, and André Strittmatter, Otto von Guericke University, Germany

[TuA2-5]

11:50-12:05

Robust GaAs/SiO₂/Si Wafer-Bonded Templates for Monolithic Telecom C-Band InAs Quantum Dot Single-Photon Sources on Silicon

P. Vijayan, M. Seidel, M. Jetter, and P. Michler, Universität Stuttgart, Germany

[TuA2-6]

12:05-12:20

MOVPE of Ga(Sb,Bi)/GaSb Heterostructures on GaSb Nano-Ridges

Marcel Kröner¹, Michiel de Maeyer^{2,3}, Johannes Haust¹, Andreas Beyer¹, Bernardette Kunert², and Kerstin Volz¹, ¹Philipps-Universität Marburg, Germany, ²imec, Belgium, ³Ghent University, Belgium

**[TuB2] Nitrides for Electronics - II**

Session Date	July 14 (Tue.), 2026
Session Time	10:35–12:20
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Narihito Okada (Yamaguchi University, Japan), Dr. Byeongchan So (Fraunhofer Institute for Applied Solid State Physics IAF, Germany)

[TuB2-1] [Invited]

10:35–11:05

AlN-Based Heteroepitaxy and Devices by MOCVD

Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[TuB2-2]

11:05–11:20

Record-High 2DEG Mobility in GaN HEMTs on an Improved AlN Buffer with a 50-nm GaN Channel

M. Hino, S. Yoshida, I. Makabe, K. Makiyama, J. Kotani, and K. Nakata, Sumitomo Electric Industries, Ltd., Japan

[TuB2-3]

11:20–11:35

Prospects and Challenges for N-Polar AlN-Based GaN Channel HEMTsMarkus Pristovsek¹, Yoann Robin¹, Itsuki Furuhashi¹, Chengzhi Zhang², Martin Kuball², Matthew D. Smith², Sheng Zhang³, Xinhua Wang³, and Xu Yang^{1,3}, ¹Nagoya University, Japan, ²University of Bristol, United Kingdom, ³Chinese Academy of Sciences, China**[TuB2-4]**

11:35–11:50

Suppress the Parasitic Leakage Current of Homoepitaxial GaN HEMT Using Self-Organizing Nucleated AlN Isolation Layer

JunShuai Xue, WenBo Sun, GuanLin Wu, Cheng Zhao, ChenKai Zhang, JinCheng Zhang, and Yue Hao, Xidian University, China

[TuB2-5]

11:50-12:05

Homoepitaxial Growth of AlGa_N Drift Layers on Bulk Ammonothermal GaN and AlGa_N Substrates

Pawel Prystawko, Tomasz Sochacki, Robert Kucharski, Piotr Kruszewski, and Marcin Krysko, Institute of High Pressure Physics PAS, Poland

[TuB2-6]

12:05-12:20

GaN-on-GaN Regrowth Interface Optimization in MOVPE for Electronic Device Structures

F. Brunner, A. Bassal, K. Tetzner, O. Hilt, S. Breuer, and M. Weyers, Ferdinand-Braun-Institut, Germany

**[TuA3] 2D Materials - II**

Session Date	July 14 (Tue.), 2026
Session Time	14:00–16:00
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Xiaotian Zhang (Suzhou Laboratory, China), Prof. Suresh Sundaram (Georgia Institute of Technology, France)

[TuA3–1] [Invited]

14:00–14:30

Opportunities of Halogen–Based Gas–Phase Reactants during Chemical Vapor Deposition of Transition Metal Dichalcogenides

Benjamin Groven, IMEC, Belgium

[TuA3–2]

14:30–14:45

Electrically Driven Ultraviolet Emission from Carbon–Incorporated h–BN Films Grown by MOCVD

Semi Im, Seokho Moon, Jawon Kim, Jaesub Song, Changuk Ji, Seonghyeon Pak, and Jong Kyu Kim, Pohang University of Science and Technology, Korea

[TuA3–3]

14:45–15:00

Role of h–BN Thickness in MOVPE–Grown III–Nitride Heterostructures: Enabling Detachment and Preserving Material Quality

T. M. Tran, P. Vuong, V. Ottapilakkal, M. Bourras, P.L. Voss, S. Sundaram, J.P. Salvestrini, and A. Ougazzaden, Georgia Institute of Technology, France

[TuA3–4]

15:00–15:15

Hexagonal Boron Nitride/Aluminium Gallium Nitride Heterojunction for High–Performance Deep Ultraviolet PhotodetectionJawon Kim¹, Seokho Moon², Semi Im¹, Jaesub Song¹, Changuk Ji¹, Seonghyeon Pak¹, and Jong Kyu Kim¹,
¹Pohang University of Science and Technology, Korea, ²Ajou University, Korea

[TuA3-5]

15:15-15:30

MOCVD Growth of 2D Post-Transition Metal Chalcogenides

Robin Gönkel, Nils Langlotz, Samane Badrosadat Ojaghi, Max Bergmann, Jürgen Belz, and Kerstin Volz, Philipps-Universität Marburg, Germany

[TuA3-6]

15:30-15:45

Scalable Hexagonal Boron Nitride-Based Memristors with Reliable Analog Switching Behavior

Jaesub Song¹, Jungho Lee², Seokho Moon³, Seonghyeon Pak¹, Semi Im¹, Jawon Kim¹, Changuk Ji¹, Jiye Kim¹, Hyeonwoo Lee², Beomjin Park², Dong-Seok Kim⁴, Changwook Jeong², and Jong Kyu Kim¹,
¹Pohang University of Science and Technology, Korea, ²Ulsan National Institute of Science and Technology, Korea, ³Ajou University, Korea, ⁴Korea Atomic Energy Research Institute, Korea

[TuA3-7]

15:45-16:00

Influence of Pre-Growth Treatment on the Homoepitaxial Growth of MOVPE BN on ¹⁰BN Flakes

A. K. Dąbrowska¹, I. Nowik¹, R. Bożek¹, M. Tokarczyk¹, K. Ludwiczak¹, B. Furtak¹, P. Tatarczak¹, P. Maksymiuk¹, J. Iwański¹, G. Cassaboïs², B. Gil², T. Poirier³, J. Li³, J.H. Edgar³, J. Binder¹, and A. Wysmołek¹,
¹University of Warsaw, Poland, ²Université de Montpellier, France, ³Kansas State University, USA

**[TuB3] Optical Devices**

Session Date	July 14 (Tue.), 2026
Session Time	14:00–16:00
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Dr. Amélie Dussaigne (CEA-Leti, France), Dr. Michael Jetter (University of Stuttgart, Germany)

[TuB3–1] [Invited]

14:00–14:30

Polarization Manipulation in III-Nitride Light Emitting Devices

Fang Liu¹, Yucheng Guo¹, Zexing Yuan¹, Xin Gao², Zhaoying Chen¹, Ping Wang¹, Hailin Peng², Bo Shen¹, Zhongfan Liu², and Xinqiang Wang¹, ¹Peking University, China, ²Great Bay University, China

[TuB3–2]

14:30–14:45

Impact of Thermal Budget and Carrier Gas Switching on the Performance of Multi-Color Cascaded LEDs

Christoph Berger, Armin Dadgar, Florian Hörich, and André Strittmatter, Otto-von-Guericke-University Magdeburg, Germany

[TuB3–3]

14:45–15:00

MOVPE Growth of Monolithic Multi-Band SWIR–MWIR InAsSb/InAsPSb MQW Heterostructures on InP Enabled by Strain Engineering

Dongwan Kim¹, Thuy Thi Nguyen¹, Minkyong Kim², Jungwon Yoon², Thu Trang Thi Bui^{1,3}, Dayoung Kim^{1,3}, Changsug Lee², Byong Sun Chun^{1,3}, and Sang Jun Lee^{1,2,3}, ¹Korea Research Institute of Standards and Science, Korea, ²IRSpectra co., LTD., Korea, ³Korea Research Institute of Standards and Science, Korea

[TuB3–4]

15:00–15:15

Investigating Surface Treatments on GaN p–i–n Avalanche Photodiodes with Shallow Beveled Edge Termination

Alexandra Dolgashev¹, Davide Balzerani¹, A. Nepomuk Otte¹, Theeradetch Detchprohm¹, Dhrubab Biswas², Subhra Chowdhury², and Russell D. Dupuis¹, ¹Georgia Institute of Technology, USA, ²Magnolia Optical Technologies, USA

[TuB3-5]

15:15-15:30

Efficiency Optimization of 222 nm AlGaIn-Based Far-UVC LEDs

Kexin Ren, Zhiyuan Liu, Haicheng Cao, Tingang Liu, Zixian Jiang, and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[TuB3-6]

15:30-15:45

Fast MOVPE Growth of AlGaAs/GaAs Dual-Junction Solar Cells

D. Lackner¹, C. Klein¹, M. Klitzke¹, J. Schön^{1,2}, J. Ohlmann¹, and F. Dimroth¹, ¹Fraunhofer Institute for Solar Energy Systems ISE, Germany, ²University of Freiburg, Germany

[TuB3-7]

15:45-16:00

Composition Pulling Effect of Indium and Origin of High-Energy Peak in InGaIn-Based Red Micro-LEDs

Chunyu Liu¹, Panpan Li^{1,2}, Hira Usman³, Anders Gustafsson³, Yang Su¹, Zihan Xia¹, Weifang Lu^{1,2}, Xu Yang^{1,2}, JinChai Li^{1,2}, Hongjian Li^{1,2}, Kai Huang^{1,2}, Zhaoxia Bi², Lars Samuelson³, and Rong Zhang^{1,2}, ¹Xiamen University, China, ²Future Display Institute of Xiamen, China, ³Southern University of Science and Technology, China

V. Technical Program

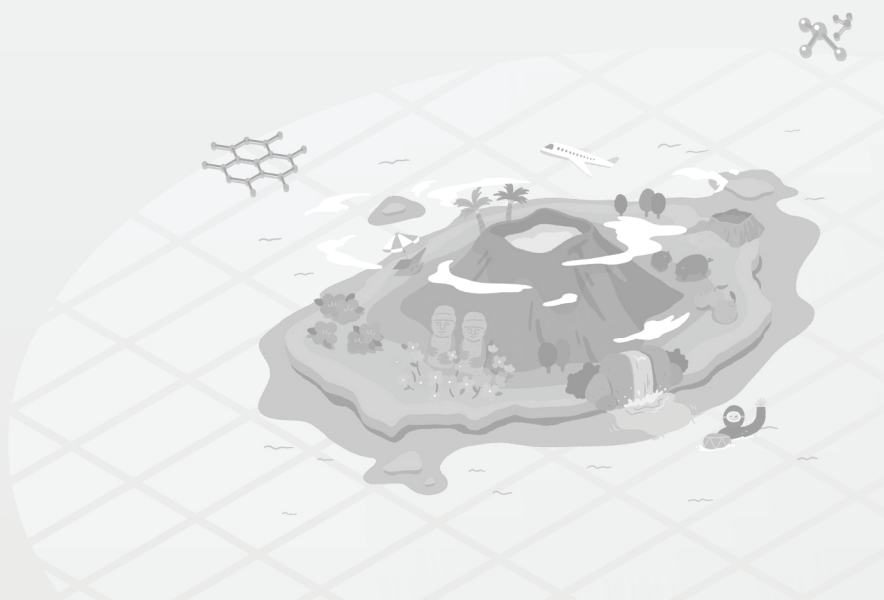
2. Technical Sessions

ICMOVPE-XXII

The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

July 15, 2026
[Wednesday]

Oral Session



[WeA1] Gallium Oxides	
Session Date	July 15 (Wed.), 2026
Session Time	10:25–12:10
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Dr. Dongwan Kim (Korea Research Institute of Standards and Science, Korea), Prof. Seokho Moon (Ajou University, Korea)

[WeA1–1] [Invited]

10:25–10:55

Atomic-Scale Interface and Polarity Engineering in III-Nitride and β -Ga₂O₃ Heterostructures by Hot-Wall MOVPE

Minho Kim¹, Alexis Papamichail², Ingmar Persson³, Hengfang Zhang¹, Dat Q. Tran¹, Ken Goto², Andri Dhora², Daniela Gogova¹, Per O. Å. Persson¹, Plamen P. Paskov¹ and Vanya Darakchieva^{1,2},
¹Linköping University, Sweden, ²Lund University, Sweden

[WeA1–2]

10:55–11:10

Effects and Applications of Nuclear Radiation in Ga₂O₃

Yoonho Choi, Jaeheon Jung, Hae Seong Hwang, and Roy B.Chung, Kyungpook National University, Korea

[WeA1–3]

11:10–11:25

AlN Mesa Sidewall Passivation Enables Thermally Stable Reverse Blocking in Vertical β -Ga₂O₃ Power Diodes

Ganesh Mainali, Nuzhat Yousf, Dhanu Chettri, Haicheng Cao, Leo Raj Solay, and Xiaohang Li, King, Abdullah University of Science and Technology, Kingdom of Saudi Arabia

[WeA1–4]

11:25–11:40

High Efficiency Growth of (001) β -Ga₂O₃ Films by Cold-Wall MOCVD

Shun Ukita and Hironori Okumura, University of Tsukuba, Japan



[WeA1-5]

11:40-11:55

Heteroepitaxial Growth of β -Ga₂O₃ on High-Angle Off-Cut Sapphire via MOCVD

Ji-Hyeon Park, Hyeong-Yun Kim, JungHun Choi, and Dae-Woo Jeon, Korea Institute of Ceramic Engineering and Technology, Korea

[WeA1-6]

11:55-12:10

Influence of Substrate Atomic Symmetry on the Epitaxy and Rotational Domain Formation of κ -Ga₂O₃

Ha Young Kang, Jaeheon Jung, Young Soo Hwang, and Roy B. Chung, Kyungpook National University, Korea

[WeB1] UV Devices

Session Date	July 15 (Wed.), 2026
Session Time	10:25–12:10
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Young Joon Hong (Sungkyunkwan University, Korea) Prof. JunShuai Xue (Xidian University, China)

[WeB1–1] [Invited]

10:25–10:55

The Role of Point Defects in AlGaIn-Based Far-UVC LEDs

T. Wernicke¹, J. Höpfner¹, M. Schilling¹, I. Prozeev², K. Loeto³, J. Ruschel⁴, D. Cameron^{5,6}, T. Kolbe⁴, J. Pacuk⁷, M. Guttman⁴, J. Rass⁴, G. Kusch⁷, Z.S. Pehlivan⁷, H.K. Cho⁴, S. Hagedorn⁴, N. Roccato⁷, N. Susilo¹, P. Edwards⁵, A. Muhin¹, F. Piva⁷, G. Cardinali¹, C. De Santi⁷, M. Buffolo⁷, N. Trivellin⁷, Marco Pilati⁷, M.R. Wagner³, M. Weyers⁴, S. Einfeldt⁴, G. Meneghesso⁷, E. Zanoni⁷, R.W. Martin⁵, R.A. Oliver⁸, J. Lähnemann³, F. Tuomisto², M. Meneghini⁷, M. Kneissl^{1,4}, ¹Technische Universität Berlin, Germany, ²University of Helsinki, Helsinki, Finland, ³Paul-Drude-Institut, Berlin, Germany, ⁴Ferdinand-Braun-Institut, Germany, ⁵University of Strathclyde, United Kingdom, ⁶Gatan, Inc., Pleasanton, United States, ⁷University of Padua, Italy, ⁸University of Cambridge, United Kingdom

[WeB1–2] [Invited]

10:55–11:25

MOVPE Growth of UV-B Laser Diodes on Sapphire Substrate and Realization of Room-Temperature Continuous-Wave Operation

Motoaki Iwaya, Takumu Saito, Rintaro Miyake, Sho Iwayama, Tetsuya Takeuchi, Satoshi Kamiyama, and Hideto Miyake, Meijo University, Japan

[WeB1–3]

11:25–11:40

Low-Leakage Shallow-Beveled Mesa GaN Ultraviolet Avalanche Photodiodes with AlGaIn Windows for Improved Responsivity

Davide Balzerani¹, Alexandra V. Dolgashev¹, A. Nepomuk Otte¹, Theeradetch Detchprohm¹, Subhra Chowdhury², Dhruves Biswas², and Russell D. Dupuis¹, ¹Georgia Institute of Technology, USA, ²Magnolia Optical Technologies, USA



[WeB1-4]

11:40-11:55

MOVPE-Grown p-AlGaIn with Coupled Polarization and Impurity Doping Achieving 12% EQE in Deep-Ultraviolet LEDs

Hongyu Liu¹, Li Chen², Jichun Ye¹, and Wei Guo¹, ¹Ningbo Institute of Materials Technology and Engineering, Chinese Academy of Sciences, ²Yongjiang Laboratory, China

[WeB1-5]

11:55-12:10

Nanoscale Characterization of Carrier Capture into the Active Region of Far-UVC LEDs

Frank Bertram¹, Gordon Schmidt¹, Niklas Dreyer¹, Peter Veit¹, Jürgen Christen¹, M. Ajmal Khan², Kohei Fujimoto^{2,3}, M. Nawaz Sharif^{2,3}, Hiroyuki Yaguchi³, and Hideki Hirayama², ¹Otto-von-Guericke University Magdeburg, Germany, ²RIKEN Cluster for Pioneering Research, Japan, ³Saitama University, Japan

[WeA2] Polarity-Engineered Epitaxy

Session Date	July 15 (Wed.), 2026
Session Time	13:30–15:15
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Ryota Akaike (Mie University, Japan) Prof. Arnab Bhattacharya (Tata Institute of Fundamental Research, India)

[WeA2-1] [Invited]

13:30–14:00

AlN-based Field-Effect Transistors Enabled by Polarization-Engineered Structures

Masanobu Hiroki, NTT Inc., Japan

[WeA2-2]

14:00–14:15

Suppression of Mn Segregation in N-Polar GaN on Mn-Doped GaN Substrates

Shigeki Yoshida, Maui Hino, Isao Makabe, Kozo Makiyama, Junji Kotani, and Ken Nakata, Sumitomo Electric Industries, Ltd., Japan

[WeA2-3]

14:15–14:30

Metalorganic Vapor Phase Epitaxy of N-Polar GaN on Ga-Polar GaN

Kazuhisa Ikeda¹, Masahiro Uemukai², Tomoyuki Tanikawa³, Ryuji Katayama², and Atsushi Kobayashi¹,
¹Tokyo University of Science, Japan, ²The University of Osaka, Japan, ³Meijo University, Japan

[WeA2-4]

14:30–14:45

Polarity-Guided Epitaxy of h-BN on AlN Using MOVPE for 2D–3D Integration

Yuning Wang¹, Ryota Akaike¹, Kosuke Takagi¹, Tomohiro Tamano¹, Hiroki Yasunaga¹, Wentao Zhang^{2,3}, Ke Xu^{2,4,5}, and Hideto Miyake¹, ¹Mie University, Japan, ²Chinese Academy of Sciences, China, ³University of Science and Technology of China, ⁴Suzhou Nanowin Science and Technology Co., Ltd., China, ⁵Jiangsu Institute of Advanced Semiconductors, China



[WeA2-5]

14:45–15:00

Fabrication of Polarity-Inverted AlN Structure Using Oxidation Processes

Tomohiro Tamano¹, Ryota Akaike¹, Hiroki Yasunaga¹, Zentaro Akase², Shigetaka Tomiya², and Hideto Miyake¹, ¹Mie University, Japan, ²Nara Institute of Science and Technology, Japan

[WeA2-6]

15:00–15:15

High-Quality N-Polar GaN Growth on Silicon for Fully-Vertical GaN-on-Si Power Devices

Pineda Padilla, A., Veux, G., Barbier, F., Guy, K., Plaza Argüello, D., Vergnaud, C., Dussaigne, A., Dupont, F., and Charles, M., CEA-Leti, France

[WeB2] Visible LEDs	
Session Date	July 15 (Wed.), 2026
Session Time	13:30–15:15
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Christophe Durand (University Grenoble Alpes, CEA, France), Prof. Qian Sun (Chinese Academy of Sciences, China)

[WeB2-1] [Invited]	13:30–14:00
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3D MOVPE Enabling Lateral Integration of InGaN-Based RGB Micro-LEDs

Mitsuru Funato and Yoshinobu Matsuda, Kyoto University, Japan

[WeB2-2]	14:00–14:15
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Vertical GaN-on-Si LEDs on Conducting TiAlN/TiN Buffer Layers

Armin Dadgar, Fabian Grossmann, Emine Kaynar, Christoph Berger, Jürgen Bläsing, and André Strittmatter, Otto-von-Guericke-Universität Magdeburg, Germany

[WeB2-3]	14:15–14:30
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From Relaxed InGaN Pseudo-Substrate to Red Emitting Quantum Wells (QWs)

H. Damen¹, D. P. Fowan³, M. Nemoz³, S. Vézian³, B. Damilano³, A. Trassoudaine², and A. Dussaigne¹,
¹Université Grenoble Alpes, France, ²Université Clermont Auvergne, France, ³Université Côte d'Azur, France

[WeB2-4]	14:30–14:45
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Enhanced Light Output in Nanorod Micro-LEDs through Optical Feedback and Structural Engineering

Min-Seok Lee¹, Sung-Un Kim¹, Jeong-Kyun Oh¹, Geon-Yeong Kim¹, Dae-Young Um², Cheul-Ro Lee¹, and Yong-Ho Ra¹, ¹Jeonbuk National University, Korea, ²Kumoh National Institute of Technology, Korea



[WeB2-5]

14:45-15:00

Modeling of Efficient Dual-Wavelength Blue-Green InGaN LEDs

Hao Lee¹, You-Jia Chen², Huai-Chin Huang¹, Li-Sheng Hu², Hsing-Ting Hung³, Chuang-Yu Hsieh³, Tien-Chang Lu², Chia-Yen Huang², and Yuh-Renn Wu¹, ¹National Taiwan University, Taiwan, ²National Yang Ming Chiao Tung University, Taiwan, ³Advanced Optoelectronic Technology Inc., Taiwan

[WeB2-6]

15:00-15:15

Impact of V-Defect Geometry and Random Alloy Fluctuations in Cylindrical Simulations of Low-Bias Leakage in Red InGaN LEDs

Pei-Shan Hsieh and Yuh-Renn Wu, National Taiwan University, Taiwan

[WeA3] Advanced Growth Techniques - II

Session Date	July 15 (Wed.), 2026
Session Time	15:35–17:05
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Yong-Ho Ra (Jeonbuk National University, Korea), Prof. Si-Young Bae (Pukyong National University, Korea)

[WeA3–1] [Invited]

15:35–16:05

Epitaxial Growth of III–Nitride Semiconductors and Their LED Structures

Zhe Zhuang, Yimeng Sang, and Bin Liu, Nanjing University, China

[WeA3–2]

16:05–16:20

Applications of Mist Chemical Vapor Deposition in the Deposition of Inorganic Functional Thin Films

Zaichun Sun and Bingchu Mei, Wuhan University of Technology, China

[WeA3–3]

16:20–16:35

Hybrid 3D/2D Growth Mode for High–Quality AlN on Si(111) by MOCVD

Mingtao Nong¹, Haicheng Cao¹, Tingang Liu¹, Patsy A Miranda Cortez¹, Glen Isaac Maciel García¹, Xiao Tang², Che–Hao Liao³, Kexin Ren¹, Zixian Jiang¹, and Xiaohang Li¹, ¹King Abdullah University of Science and Technology, Saudi Arabia, ²University of Bristol, United Kingdom, ³National Yunlin University of Science and Technology, Taiwan

[WeA3–4]

16:35–16:50

Novel MOCVD Selective Area Growth of InGaAs/GaAs/AlGaAs Using SOI Shadow Mask and Its Application to COMD Free 980nm Laser

Akihiko Kasukawa¹, I. Novitasari¹, Z–J. Sun¹, A. Albert¹, S. L. Lee¹, and M. Arai², ¹National Taiwan University of Science and Technology, Taiwan, ²University of Miyazaki, Japan



[WeA3-5]

16:50-17:05

Formation Mechanisms of Cubic GaN Grown in Si Inverted Pyramids by Selective Area OMVPE

David A. Lister, Cyan Kim, Melissa Radford, Sarah Fortin, Karen L. Kavanagh, and Simon Watkins,
Simon Fraser University, Canada

[WeB3] Nitrides for Electronics - III	
Session Date	July 15 (Wed.), 2026
Session Time	15:35–17:05
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Prof. Okhyun Nam (Tech University of Korea, Korea), Dr. Isabel Streicher (Cornell University, USA)

[WeB3–1]

15:35–15:50

In-Depth Study of Localised Growth of GaN on Silicon Leading to 1 kV, 5 mOhm.cm² Vertical Diodes

M. Charles¹, D. Plaza-Arguello¹, M. El Amrani¹, T. Kaltsounis¹, H. El Rammouz¹, Z. M'Qaddem¹, T. Guillemin², S. Torrenco¹, M. Lafossas¹, N. Rochat¹, Y. Cordier², and J. Buckley¹, ¹CEA Leti, France, ²Univ. Côte d'Azur, France

[WeB3–2]

15:50–16:05

Investigating the Impact of High-Temperature Ohmic Contact Annealing on AlN Schottky Barrier Diodes

Haicheng Cao¹, Mingtao Nong¹, Tingang Liu¹, Zixian Jiang¹, Zhiyuan Liu¹, Saravanan Yuvaraja¹, Xiao Tang², Biplab Sarkar³, Ying Wu¹, and Xiaohang Li¹, ¹King Abdullah University of Science and Technology, Saudi Arabia, ²University of Bristol, United Kingdom, ³Indian Institute of Technology, India

[WeB3–3]

16:05–16:20

Submicron Ultrafast Raman Thermography System for Power Semiconductor Devices and Next Generation Semiconductors.

Jung-Hoon Song^{1,2}, Youngboo Moon^{1,3}, Seungyoung Lim¹, Gye Eun Choi¹, and Jaesun Kim¹, ¹AccuOptotec Co., Korea, ²Kongju National University, Korea, ³UJL Co., Korea

[WeB3–4]

16:20–16:35

Understanding the Impact of n-Type GaN Drift Layer Growth Conditions on 300 mm Wafer Bow for GaN-on-Si Vertical Devices

G. Bouhet, F. Barbier, C. Vergnaud, H. El Rammouz, A. Chaumont, M. Lafossas, P. Valentin, V. Balan, A. Olivier, J. Buckley, C. Masante, M. Charles, and S. Torrenco, CEA-Leti, France



[WeB3-5]

16:35-16:50

SiO_x Interlayer for Reverse Current Suppression in p-GaN Diodes

Zixian Jiang and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[WeB3-6]

16:50-17:05

Crack-Free Si-Doped AlN on Si(111) for Fully Vertical AlN Schottky Barrier Diodes

Haicheng Cao¹, Mingtao Nong¹, Xiao Tang², Biplab Sarkar³, Ying Wu¹, and Xiaohang Li¹, ¹King Abdullah University of Science and Technology, Saudi Arabia, ²University of Bristol, United Kingdom, ³Indian Institute of Technology, India

V. Technical Program

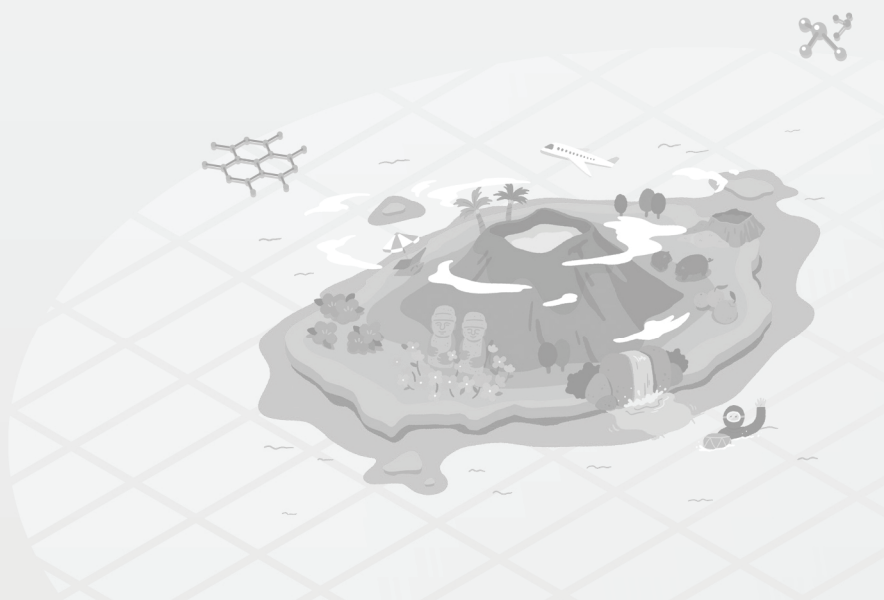
2. Technical Sessions

ICMOVPE-XXII

The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

July 16, 2026
[Thursday]

Oral Session



**[ThA1] Al-rich AlGaN**

Session Date	July 16 (Thu.), 2026
Session Time	08:30–09:45
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Hoe Tan (The Australian National University, Australia), Prof. Sang Wan Ryu (Chonnam National University, Korea)

[ThA1–1]

08:30–08:45

Interface Engineering on Enhancement-Mode Al-Rich $\text{Al}_{0.8}\text{Ga}_{0.2}\text{N}$ MOSFET Enabled by Atomic Layer Etching

Tingang Liu, Haicheng Cao, Mingtao Nong, and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[ThA1–2]

08:45–09:00

Impact of AlN/AlGaN Superlattice Structure on Proton-Induced Transport in Al-Rich AlGaN Channel HEMTs

Shyam Mohan, Joocheol Jeong, Jaejin Heo, Hyogeun Cho, Mingoo Jo, Minyeong Kim, and Okhyun Nam, Tech University of Korea, Korea

[ThA1–3]

09:00–09:15

Formation of Low-Resistance Ohmic Contacts to Al-Rich AlGaN Using Compositionally Graded n-AlGaN

Riku Ando, Ryota Akaike, Shozabro Tanaka, Hiroki Yasunaga, Takao Nakamura, and Hideto Miyake, Mie University, Japan

[ThA1–4]

09:15–09:30

Investigation of Low-Resistivity Au-Free Metal Contact on n-Type $\text{Al}_x\text{Ga}_{1-x}\text{N}$ ($x \geq 0.8$)

Tingang Liu, Haicheng Cao, Mingtao Nong, and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[ThA1-5]

09:30-09:45

High-Temperature and Radiation Responses of Al-Rich AlGaN Channel HEMTs Employing Various Gate Metals

Mingoo Jo¹, Joocheol Jeong¹, Shyam Mohan¹, Jaejin Heo¹, Hyogeun Cho¹, Minyeong Kim¹, Dongseok Kim², Jiun Oh³, Minji Kim³, and Okhyun Nam¹, ¹Tech University of Korea, Korea, ²Korea Atomic Energy Research Institute, Korea, ³Korea Institute of Energy Technology, Korea

**[ThB1] Structural Analysis**

Session Date	July 16 (Thu.), 2026
Session Time	08:30–10:15
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Dr. Masanobu Hiroki (NTT Inc., Japan), Prof. Soon-Ku Hong (Chungnam University, Korea)

[ThB1–1] [Invited]

08:30–09:00

MOVPE Growth of AlGa_N with Step-and-Terrace Structures on AlN Templates

Ryota Akaike, Hiroki Yasunaga, Takao Nakamura, and Hideto Miyake, Mie University, Japan

[ThB1–2]

09:00–09:15

Atomic Structure of Antiphase Domain Boundaries in III–V Semiconductor Layers Epitaxially Grown on Silicon (100) or Obtained by Direct Wafer Bonding

Gilles Patriarche¹, Konstantinos Pantzas¹, Alexandre Beck², Laurent Pedesseau², Rozenn Gautheron–Bernard², Nathaniel Findling¹, Ludovic Largeau¹, Grégoire Beaudoin¹, Jean–Baptiste Rodriguez³, Eric Tournié³, Isabelle Sagnes¹, and Charles Cornet², ¹Centre national de la recherche scientifique, France, ²Institut National des Sciences Appliquées de Rennes, France, ³Université de Montpellier, France

[ThB1–3]

09:15–09:30

Interplay of Carrier Recombination and Separation in an InGa_N MQW LED Investigated by Nano–STEM–EBIC and –STEM–CL

Niklas Dreyer, Frank Bertram, Gordon Schmidt, Luca Greczmiel, Christoph Berger, Armin Dadgar, André Strittmatter, and Jürgen Christen, Otto–von–Guericke–University Magdeburg, Germany

[ThB1-4]

09:30-09:45

Vacancy Properties and Their Clustering in GaN MOVPE Epitaxial Layers and Heterostructures

Alice Hospodková¹, Jakub Čížek², František Hájek¹, Karla Kuldová¹, Tomáš Hubáček¹, Jiří Pangrác¹, Maciej Oskar Liedke³, Eric Hirschmann³, Maik Butterling³, and Andreas Wagner³, ¹Institute of Physics of the Czech Academy of Sciences, Czech Republic, ²Charles University, Czech Republic, ³Helmholtz-Zentrum Dresden-Rossendorf, Germany

[ThB1-5]

09:45-10:00

Revisiting the Stacking Faults in 4H-SiC

Soon-Ku Hong¹, Moonkyong Na², Hyundon Jung³, and Wook Bahng², ¹Chungnam National University, Korea, ²Korea Electrotechnology Research Institute, Korea, ³Horiba STEC Korea, Korea

[ThB1-6]

10:00-10:15

Analytical X-Ray Solutions for Thin Film and Wafer Analysis

Andrey Zameshin¹, Alexey Pustovarenko¹, Amardeep Bharti¹, Choong Ki (Daniel) Lee², and Shuji Kusano³, ¹Malvern Panalytical, Netherlands, ²Spectris Korea Ltd, Korea, ³Spectris Co. Ltd, Japan

V. Technical Program

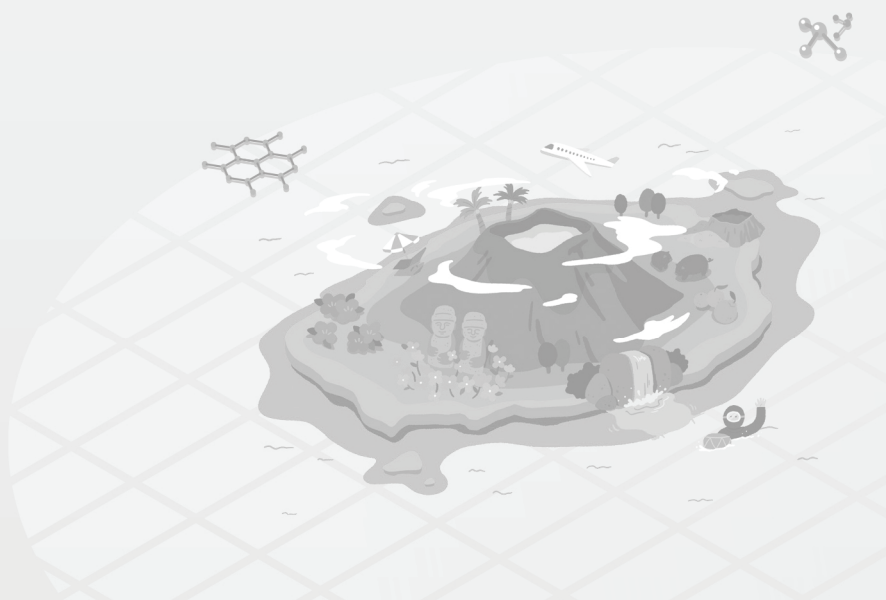
2. Technical Sessions

ICMOVPE-XXII

The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

July 17, 2026
[Friday]

Oral Session



[FrA1] Nanowires	
Session Date	July 17 (Fri.), 2026
Session Time	10:20–12:05
Session Room	Room A (Baekrok Hall A, 1F)
Session Chairs	Prof. Yong-Ho Ra (Jeonbuk National University, Korea), Dr. Elisa Maddalena Sala (The University of Sheffield, United Kingdom)

[FrA1–1] [Invited]

10:20–10:50

Growth of Core–Shell Microwire UV Emitters: From UV–A Toward UV–C

Houssein Mohaidly, Lucie Valéra, Vincent Grenier, Lucas Jaloustre, Saron R.S. De Mello, C. Petit-Etienne, E. Pargon, Gwénolé Jacopin, and Christophe Durand, Université Grenoble Alpes, France

[FrA1–2]

10:50–11:05

Facile Electrochemically Driven Defect Passivation of MOCVD–Grown GaN Nanowires Toward Durable and High–Performance Photoelectrodes

Fawad Tariq and Sang–Wan Ryu, Chonnam National University, Korea

[FrA1–3]

11:05–11:20

Interface Engineering of MOVPE–Grown GaN Nanowire Photoanodes with FeOOH/NiO Layers for Durable Alkaline Water Oxidation

Khaled Abdelkarem and Sang–Wan Ryu, Chonnam National University, Korea

[FrA1–4]

11:20–11:35

Tailoring Cu–Pd Nanoclusters on GaN Nanowires for Efficient CO₂–to–C₂H₄ Photoelectrochemical Conversion

Sneha S Lavate, In–Seo Na, Jeong–Kyun Oh, Sung–Un Kim, Min–Seok Lee, and Yong–Ho Ra, Jeonbuk National University, Korea



[FrA1-5]

11:35-11:50

Interfacial Engineering of $\text{Ni}(\text{OH})_2$ Decorated GaN Nanorods for Enhanced Photoelectrochemical Formate Production.

Shivraj Mahadik, Jeong-Kyun Oh, Sung-Un Kim, Min-Seok Lee, Hussain Musharrof, and Yong-Ho Ra, Jeonbuk National University, Korea

[FrA1-6]

11:50-12:05

Selective-Area Growth of Vertical InP Nanowires on Si(111) Substrate

Yuki Azuma¹, Keita Taniyama¹, Wei Wen Wong², Junichi Motohisa¹, Hark Hoe Tan², and Katsuhiro Tomioka¹, ¹Hokkaido University, Japan, ²The Australian National University, Australia

[FrB1] Emerging Nitrides	
Session Date	July 17 (Fri.), 2026
Session Time	10:20–12:05
Session Room	Room B (Baekrok Hall B, 1F)
Session Chairs	Dr. Ji-Hyeon Park (Korea Institute of Ceramic Engineering and Technology, Korea), Dr. An-Na Cha (Chonnam National University, Korea)

[FrB1–1] [Invited]

10:20–10:50

MOCVD of Novel Nitrides for Sustainable Electronics – AlScN and AlYN

Isabel Streicher¹, Stefano Leone², Huili Grace Xing¹, Debdeep Jena¹, and Hari Nair¹, ¹Cornell University, USA, ²Fraunhofer Institute of Applied Solid State Physics IAF, Germany

[FrB1–2]

10:50–11:05

Growth and Structural Characterization of AlYN/GaN/Sapphire by Metalorganic Chemical-Vapor Deposition

Shun Narita, Yudai Shimizu, Daisuke Iida, Keitaro Ikejiri, and Kazutada Ikenaga, Nippon Sanso Corporation, Japan

[FrB1–3]

11:05–11:20

Evaluation of Vertical B GaN Neutron Detectors Using Free-Standing GaN Substrate for Neutron Imaging

S. Takenaka¹, R. Kudo¹, K. Ando¹, Y. Maeda¹, E. Kokubo², K. Takagi¹, T. Oda³, M. Hino⁴, Y. Honda², H. Amano², Y. Inoue¹, T. Aoki¹, and T. Nakano¹, ¹Shizuoka University, Japan, ²Nagoya University, Japan, ³The University of Tokyo, Japan, ⁴Kyoto University, Japan

[FrB1–4]

11:20–11:35

Thickness Dependence of Structural and Radiation Detection Characteristics of B GaN Neutron Detectors for In-Core Nuclear Instrumentation

R. Kudo¹, E. Kokubo², K. Takagi¹, Y. Sakurai³, H. Yashima³, T. Makino⁴, T. Ohshima⁴, Y. Honda², H. Amano², Y. Inoue¹, T. Aoki^{1,3}, and T. Nakano^{1,3}, ¹Shizuoka University, Japan, ²Nagoya University, Japan, ³Kyoto University, Japan, ⁴National Institutes for Quantum Science and Technology, Japan



[FrB1-5]

No-show

11:35-11:50

Fabrication and Evaluation of BAIGaN Neutron Detector Designed for Operation in Harsh Environments

Ryusuke Suzuki¹, Ryohei Kudo¹, Toru Oikawa¹, Hinata Nakanishi¹, Eito Kokubo², Genichiro Wakabayashi³, Yoshio Honda², Hiroshi Amano², Yoku Inoue¹, Toru Aoki¹, and Takayuki Nakano¹,
¹Shizuoka University, Japan, ²Nagoya University, Japan, ³Kindai University, Japan

[FrB1-6]

11:50-12:05

Thickness-Dependent Compensation in Polarization-Doped Graded AlGaIn Grown by MOVPE

Abhishek Chatterjee¹, Z. S. Pehlivan¹, M. Frentrop¹, B. Harding¹, G. Kusch¹, M. J. Kappers¹, D. J. Wallis^{1,2}, and R. A. Oliver¹, ¹University of Cambridge, United Kingdom, ²Cardiff University, United Kingdom

V. Technical Program

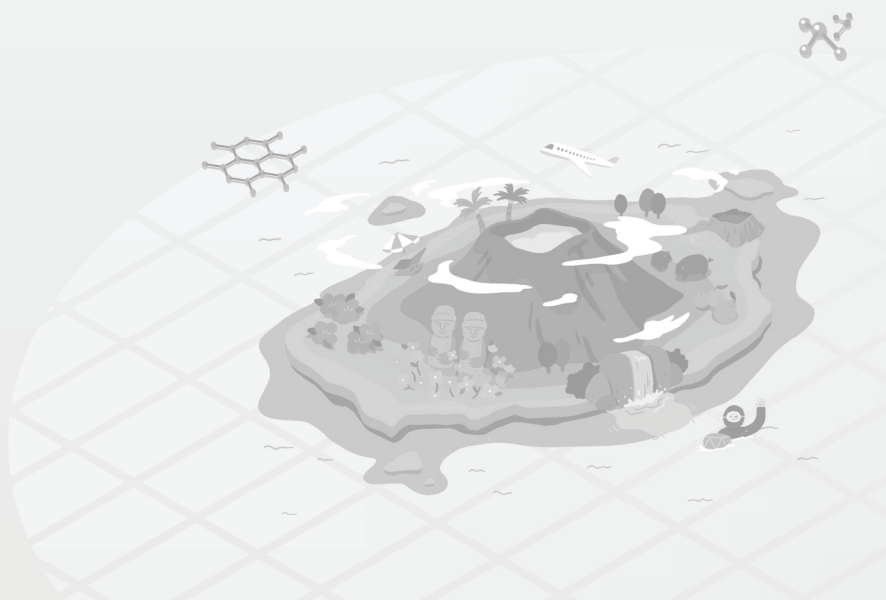
2. Technical Sessions

ICMOVPE-XXII

The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

July 14, 2026
[Tuesday]

Poster Session 1





[TuP] Poster 1

Session Date	July 14 (Tue.), 2026
Session Time	16:00–17:40
Session Room	Room C (Event Hall A, 1F)

[TuP-1]

16:00–17:40

Evolution of Surface Morphology of AlN on Low Dimensional Carbon Material Grown by HVPE

Hae-Gon Oh, Young-Jun Choi, and Hae-Yong Lee, LumiGNtech Co., Ltd., Korea

[TuP-2]

16:00–17:40

Enhanced Responsivity of β -Ga₂O₃-Based Solar-Blind UV Photodetectors via Inductively Coupled CF₄ Plasma Treatment

An-Na Cha¹, Gieop Lee¹, Sunjae Kim^{2,3}, Dae-Woo Jeon³, Ji-Hyeon Park³, Wan-Sik Hwang², and Jun-Seok Ha¹, ¹Chonnam National University, Korea, ²Korea Aerospace University, Korea, ³Korea Institute of Ceramic Engineering and Technology, Korea

[TuP-3]

16:00–17:40

Epitaxial Alignment and Substitutional Defect Control in Large-Area WS₂ Monolayers

Yunjung Cho, Wonchan Lee, Seohee Park, and Seunguk Song, Sungkyunkwan University, Korea

[TuP-4]

16:00–17:40

Two-Step Growth of Spatially Controlled WS₂-MoSe₂ Heterostructure

Chaehui Lim, Wonchan Lee, Yunjung Cho, Seohee Park, Taeyoung Jeon, and Seunguk Song, Sungkyunkwan University, Korea

[TuP-5]

16:00–17:40

The Growth of Hexagonal Boron Nitride on Graphene by Metal-Organic Chemical Vapor Deposition

Changuk Ji¹, Seokho Moon², Semi Im¹, Jawon Kim¹, Jaesub Song¹, Seonghyeon Pak¹, and Jong Kyu Kim¹, ¹Pohang University of Science and Technology, Korea, ²Ajou University, Korea

[TuP-6]

16:00-17:40

Effect of Sn Doping Concentration on the Structural Properties of β -Ga₂O₃ Thin Films Grown on Off-Axis Sapphire by Mist-CVD

Jae-Hyeok LIM¹, Tae-Yong PARK¹, Yun-Ji SHIN¹, Seong-Min JEONG¹, Chang-Mo KANG², and Si-Young BAE³, ¹Korea Institute of Ceramic Engineering and Technology, Korea, ²Pusan National University, Korea, ³Pukyong National University, Korea

[TuP-7]

16:00-17:40

Improved Crystalline Quality and Surface Morphology of β -Ga₂O₃ Epilayer on Sapphire Enabled by Nucleation Layer

Sang Hyeon Ahn, Gieop Lee, An-Na Cha, Sung Jin Son, Young-Boo Moon, Myung Sik Kim, and Jun-Seok Ha, Chonnam National University, Korea

[TuP-8]

16:00-17:40

Low-Temperature Transfer-Free Graphene Formation via Catalytic Metal-Assisted Graphitization for Remote Epitaxy

Soohyun Kim, Joonghoon Choi, Won Kwang Yang, and Young Joon Hong, Sungkyunkwan University, Korea

[TuP-9]

16:00-17:40

Control of α -Ga₂O₃ Growth Mode via Surface Energy Modulation for Enhanced UV Photodetection

Hee Won Shin, Jang Hyeok Park, and You Seung Rim, Sejong University, Korea

[TuP-10]

16:00-17:40

Localized Strain Control of MoS₂ Using GaN Pyramidal Structures for Single Photon Emission

Jun Woo Lee¹, Su Jin Kim², Joonghoon Choi¹, Dong Hyun Cho², Jeongwon Park³, Kibum Kang^{3,4}, Hyun Seok Lee², and Young Joon Hong¹, ¹Sungkyunkwan University, Korea, ²Chungbuk National University, Korea, ³Korea Advanced Institute of Science and Technology, Korea, ⁴TDS Innovation Inc., Korea

[TuP-11]

16:00-17:40

Fabrication of Quasi-Vertical α -Ga₂O₃ Schottky Barrier Diodes on Sapphire

Jang Hyeok Park, Kanghee Shin, and You Seung Rim, Sejong University, Korea

**[TuP-12]**

16:00–17:40

Complete Removal of Subsurface Damage in (010) β -Ga₂O₃ Single Crystals via a Two-Step Chemical Mechanical Polishing Process

Eun-Jeong An¹, Eun-Seo Lee¹, Sang-Jin Bae¹, Ho-Gyun Yun¹, Kwang-Hee Jung¹, Jung-Gon Kim¹, Mi-Seon Park¹, Dong-Jin Lee², Jin-Ki Kang², and Won-Jae Lee¹, ¹Dong-Eui University, Korea, ²Axel, Korea

[TuP-13]

16:00–17:40

Metalorganic Vapor Phase Epitaxy of Van Der Waals Indium Selenides

Jihwan Jeon, Yerin So, Kyungwu Kwon, and Seunguk Song, Sungkyunkwan University, Korea

[TuP-14]

16:00–17:40

Ga Pre-Deposition Assisted Heteroepitaxial Growth of Gallium Oxide Thin Films on Sapphire Substrates by MOCVD

Mi-Rim Lim¹, Tae-Hun Gu¹, A-Ran Shin¹, Jae-Hyuk Lim^{2,3}, and Si-Young Bae¹, ¹Pukyong National University, Korea, ²Korea Institute of Ceramic Engineering and Technology, Korea, ³Pusan National University, Korea

[TuP-15]

16:00–17:40

Low-Temperature MOCVD Growth of Hexagonal Boron Nitride for High-Performance Memristors with CMOS Compatibility

Seonghyeon Pak¹, Seokho Moon², Jaesub Song¹, Semi Im¹, Jawon Kim¹, Changuk Ji¹, and Jong Kyu Kim¹, ¹Pohang University of Science and Technology, Korea, ²Ajou University, Korea

[TuP-16]

16:00–17:40

Enhancement of Breakdown Voltage in β -Ga₂O₃/NiO Heterojunction Diodes by Modulating p-NiO/p+NiO Widths

SangHun Kim, TaiYoung Kang, YuSup Jung, TaeJun Park, JoonHui Park, and SinSu Kyoung, Powercubesemi Inc., Korea

[TuP-17]

16:00–17:40

Improved Homoepitaxial Growth of β -Ga₂O₃ (001) by MOCVD Using Plasma-Treated Substrates

Gieop Lee¹, An-Na Cha¹, Sang Hyeon Ahn¹, Sung Jin Son², Young-Boo Moon², Myung Sik Kim², and Jun-Seok Ha¹, ¹Chonnam National University, Korea, ²UJL Inc., Korea

[TuP-18]

16:00-17:40

Improving Heat Dissipation of the GaN HEMTs Using a Nanocrystalline Diamond Capping Layer

Han-Hsin Shih, Yi-An Chen, and WenCheng Ke, National Taiwan University of Science and Technology, Taiwan

[TuP-19]

16:00-17:40

Nanoporous Aluminum Anodic Oxide Chip-Based Optical Immunosensor

Sehyuk Yeom, ByoungHo Kang, Sanghoon Jung, Jaesung Lee, Sae-Wan Kim, and Wang-Hoon Lee, Gumi Electronics and Information Technology Research Institute, Korea

[TuP-20]

16:00-17:40

Highly Sensitive UV Photodetectors based on PVK/ZnO Hybrid Layers via Doping-Controlled Charge Dynamics

Sanghoon Jung, ByoungHo Kang, Jaesung Lee, Saewan Kim, Sehyuk Yeom, and Wanghoon Lee, Gumi Electronics and Information Technology Research Institute, Korea

[TuP-21]

16:00-17:40

TGV-to-PCB Interconnect for Flip-Chip Micro-LED FSA Transfer with Transparent Backside Polarity Inspection

Yoonmo Koo, Jae Min Jung, and Daewon Lee, Hanyang University, Korea

[TuP-22]

16:00-17:40

PDMS-Based Thermal Control Platform for Improving Reliability of 3D Integrated Si Photonics Packages

Hyunjun Kim, SeungSu Kim, Kyeongmin Ryu, and Daewon Lee, Hanyang University, Korea

[TuP-23]

16:00-17:40

Photoresist-Assisted Sequential Fluidic Self-Assembly for Heterogeneous Particles

Jaesung Park, Jubin Lee, and Daewon Lee, Hanyang University, Korea

[TuP-24]

16:00-17:40

Photoresist-Defined Selective Heterogeneous MicroLED Assembly via Sequential Fluidic Self-Assembly

Jimin Park, Chaewon Kim, and Daewon Lee, Hanyang University, Korea



[TuP-25]

16:00–17:40

Two-Step Dip-Soldering Strategy for Reliable Fluidic Self-Assembly of Micro-LED Displays

Yongjae Song, Hyunjun Kim, Siyun Song, and Daewon Lee, Hanyang University, Korea

[TuP-26]

16:00–17:40

Selective Area Epitaxy of Ge Nanowires for Active Photonics Applications

Ludovica Lunghi, Nuño Amador-Mendez, Santhanu Panikar Ramanandan, Thomas Vincent Bour, Kamil Artur Wodzislawski, Alok Rudra, and Anna Fontcuberta i Morral, École polytechnique fédérale de Lausanne, Switzerland

[TuP-27]

16:00–17:40

Fundamental Study of Gallium Nitride Epitaxial Growth Behavior on Non-Circular Substrates toward Advanced Epitaxial Processes

Samseok Jang, Da-Young Kim, and Tae-Hoon Chung, Korea Photonics Technology Institute, Korea

[TuP-28]

16:00–17:40

Site-Selective InAs/InP Quantum Dots Epitaxy with Engineered Low Fine Structure Splitting

Christian C. Ruiz Madera^{1,2}, Paweł Holewa^{1,2}, Paweł Wyborski¹, Meng Xiong^{1,2}, Battulga Munkhbat¹, and Elizaveta Semenova^{1,2}, ¹Technical University of Denmark, Denmark, ²Technical University of Denmark, Denmark

[TuP-29]

16:00–17:40

Fabrication of InGaN/GaN Core-Shell Nanorod LEDs through Hybrid Etch/Regrowth Method

Junhyun Bae¹, Joonghoon Choi¹, Chang Soo Kim¹, Hak-Jong Choi², Hyungjun Lim², Youngyoon Lim², Jongwoo Kim², and Young Joon Hong¹, ¹Sungkyunkwan University, Korea, ²Korea Institute of Machinery & Materials, Korea

[TuP-30]

16:00–17:40

Selective Area Growth of S to Green Pixels on a Single Substrate

Jong-Su Kim¹, Min-Seok Lee¹, Sain Musharraf¹, Ji-Min Kang², Dae-Young Um², and Yong-Ho Ra¹, ¹Jeonbuk National University, Korea, ²Kumoh National Institute of Technology, Korea

Withdrawn

[TuP-31]

16:00-17:40

8-Inch Wafer-Scale Uniform Growth of GaN-on-Silicon Epilayers for Near-Eye Micro-Displays

Shenyu Xu, Chenxue Li, Zhe Zhuang, and Bin Liu, Nanjing University, China

[TuP-32]

16:00-17:40

Safety Protocols and Environmental Sustainability in Emerging Low-Cost MOVPE Systems: A Systematic Review of Best Practices

Dhanashri Burungale¹, Chaewon Seong², Hyojung Bae³, Jin-woo Ju³, and Jun-Seok Ha¹, ¹Chonnam National University, Korea, ²Korea Institute of Industrial Technology, Korea, ³Korea Photonics Technology Institute, Korea

[TuP-33]

16:00-17:40

Lithography-Free Metal Droplet Patterning for Multi-Color Core-Shell InGaN/GaN Nanorod LEDs

In-Seo Na, Jae-Hong Ju, Jeong-Kyun Oh, Sung-Un Kim, Min-Seok Lee, Seo-Gyeong Eun, Woo-Hyuk Choi, and Yong-Ho Ra, Jeonbuk National University, Korea

[TuP-34]

16:00-17:40

Preparation of Graphene Transparent Conductive Layers on Nanohole-Patterned UVC-LEDs

Han-Hsin Shih, Zih-Siang Chien, and WenCheng Ke, National Taiwan University of Science and Technology, Taiwan

[TuP-35]

16:00-17:40

Layer-Controlled Epitaxial 2D InSe Thin Films via Kinetically Controlled MOCVD

Jung Hoon Kang¹, Bong Gi Lim¹, Do Hyoung Koo², Imhwan Kim¹, Da-gyeom Yoo³, Seong-gwang Lee³, Ji Hoon Jang¹, Jin Seok Kim¹, Ki Jae Jang¹, Dong Hyun Lee¹, Gyu-Chul Yi¹, Jongsun Lim³, and Chang Gyoung Kim^{1,3}, ¹Seoul National University, Korea, ²Korea University, Korea, ³Korea Research Institute of Chemical Technology, Korea, ⁴University of Science and Technology, Korea

[TuP-36]

16:00-17:40

Pattern-Engineered Selective Lateral Growth of Low-Defect High-Ge-Content Epitaxial Layers on Si(111) for Silicon Photonics

Ching-Hsueh Chiu¹, Ting-Chuan Li¹, Wu-Yih Uen¹, Chiashain Chuang¹, Chih-Chang Hung³, Lung-Hsing Hsu², and Hao-Chung Kuo^{1,4}, ¹Chung Yuan Christian University, Taiwan, ²Taiwan Semiconductor Research Institute, National Institutes of Applied Research, Taiwan, ³Bolite Co., Ltd., Taiwan, ⁴National Yang Ming Chiao Tung University, Taiwan



[TuP-37]

16:00-17:40

MOVPE Growth of InAs/InP Quantum Dots via Droplet Epitaxy for Telecom-Wavelength Applications

Justyna Kurek^{1,2}, Walery Kołkowski², and Włodzimierz Strupiński¹, ¹Warsaw University of Technology, Poland, ²Vigo Photonics SA, Poland

V. Technical Program

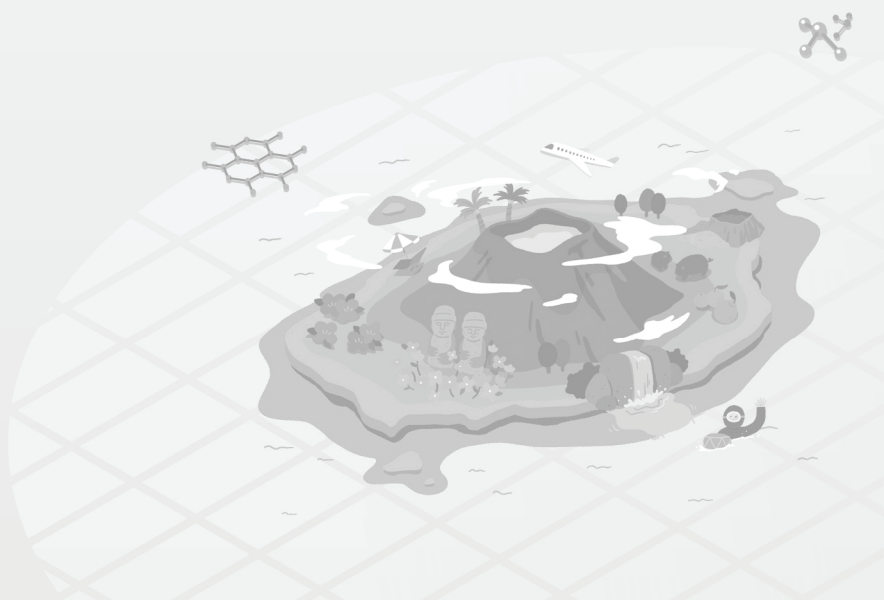
2. Technical Sessions

ICMOVPE-XXII

The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

July 15, 2026
[Wednesday]

Poster Session 2





[WeP] Poster 2

Session Date	July 15 (Wed.), 2026
Session Time	17:10–18:40
Session Room	Room C (Event Hall A, 1F)

[WeP-1]

17:10–18:40

Selective–Area Growth of InGaAs Nanowires on SOI Using a SiON/W/SiO₂ Composite Mask

Keita Taniyama, Yuki Azuma, Kai Fujimoto, Doma Hachimiya, and Katsuhiro Tomioka, Hokkaido University, Japan

[WeP-2]

17:10–18:40

Characterization of Thermal Annealing Process in Selective–Area Growth of InGaAs Nanowires

Ryuta Nakamura, Keita Taniyama, Yuki Azuma, Doma Hachimiya, and Katsuhiro Tomioka, Hokkaido University, Japan

[WeP-3]

17:10–18:40

Reduced Subthreshold Swing and Improved Uniformity in p–GaN MOSFETs Enabled by Atomic Layer Etching

Zixian Jiang and Xiaohang Li, King Abdullah University of Science and Technology, Saudi Arabia

[WeP-4]

17:10–18:40

Room Temperature Exciton–Polariton in GaN Triangular Structure Grown by Metal Organic Chemical Vapor Deposition

Chan Young Sung¹, Hyun Gyu Song², and Yong–Hoon Cho¹, ¹Korea Advanced Institute of Science and Technology, Korea, ²Korea Institute of Science and Technology, Korea

[WeP-5]

17:10–18:40

First Demonstration of 200 mm AlGaIn/GaN HEMT Epitaxy on Semi–Insulating 4H–SiC by MOCVD for Power and RF Applications

Young–Hun Han^{1,2}, Yu–Hyeon Bak², Hyun–Chul Lim², Moon–Uk Cho¹, Min–Ki Hong¹, Hyung–Sun Yun¹, Sung–Nam Lee², Yoon–Seok Kim², and June–O Song¹, ¹Wavelord Inc., Korea, ²Tech University of Korea, Korea

[WeP-6]

No-show

17:10-18:40

Strain-Balanced InGaAs/InGaP Multiple Quantum Wells for the Intermediate Junction of Triple Junction Solar Cells

Jéssica de O. Lorenzi¹, Rudy M. S. Kawabata¹, Daniel N. Micha², Luciana D. Pinto¹, Mauricio P. Pires³, Patricia L. Souza³, and Guilherme M. Torelly¹, ¹Pontifícia Universidade Católica do Rio de Janeiro, Brazil, ²Centro Federal de Educação Tecnológica Celso Suckow da Fonseca, Brazil, ³Universidade Federal do Rio de Janeiro, Brazil

[WeP-7]

17:10-18:40

MOCVD Regrowth of Step-Graded n+-AlGaN Contact Layers for Low-Resistance Ohmic Contacts in Al-Rich AlGaN Channel HEMTs

Hyogeun Cho, Joocheol Jeong, Shyam Mohan, Jaejin Heo, Minyeong Kim, Mingoo Jo, and Okhyun Nam, Tech University of Korea, Korea

[WeP-8]

17:10-18:40

Investigation of Two-Dimensional Hole Gas (2DHG) Transport in p-(Al)GaN/AlGaN/AlN Heterostructures Grown by MOCVD

Minyeong Kim, Joocheol Jeong, Shyam Mohan, Jaejin Heo, Hyogeun Cho, Mingoo Jo, and Okhyun Nam, Tech University of Korea, Korea

[WeP-9]

17:10-18:40

InGaN Micro-LEDs Integrated with CsPbBr₃ Perovskite Nanocrystals for Dual- Wavelength Visible Light Communication

Tae-Yong Park^{1,3}, Yue Wang¹, Omar Alkhazragi¹, Jung-Hong Min², Tien Khee Ng¹, and Boon S. Ooi¹, ¹King Abdullah University of Science and Technology, Saudi Arabia, ²Korea Photonics Technology Institute, Korea, ³Korea Institute of Ceramic Engineering and Technology, Korea

[WeP-10]

17:10-18:40

Strain-Induced Band Structure Engineering in MOVPE-Grown NearInfrared VCSEL Structures

Justyna Olejnik¹, Mikołaj Badura¹, Wojciech Dawidowski¹, Jan M. Śmigiel¹, Damian Radziejewicz¹, Adriana Łozińska¹, Wojciech Kijaszek¹, Iwona Sankowska², Marcin Gębski³, Magdalena Marciniak³, Marta Więckowska³, Zofia Foryś³, Michał Wasiak³, Tomasz Czystanowski³, and Beata Ściana¹, ¹Wrocław University of Science and Technology, Poland, ²Łukasiewicz Research Network, Poland, ³Łódź University of Technology, Poland

**[WeP-11]**

17:10-18:40

Control of Areal Density and Emission Wavelength of MOVPE-Grown InAs/InP Quantum Dots

J. M. Śmigiel, M. Badura, A. Szyszka, D. Radziejewicz, B. Ściana, P. Mrowiński, and M. Syperek, Wrocław University of Science and Technology, Poland

[WeP-12]

17:10-18:40

MOCVD Growth of Apex-Localized InGaN Quantum Dots on GaN Pyramid Structures for Directional Photon Emission

Jeongho Kim and Yong-Hoon Cho, Korea Advanced Institute of Science and Technology, Korea

[WeP-13]

17:10-18:40

InGaN Quantum Dots Red LED based on Post-Annealing of the Quantum Barrier

Anda Cheng, Haoxuan Yang, Lujing Wang, Changzheng Sun, Zhibiao Hao, Bing Xiong, Yanjun Han, Jian Wang, Hongtao Li, Lin Gan, Yi Luo, and Lai Wang, Tsinghua University, China

[WeP-14]

17:10-18:40

Efficiency Enhancement of InGaN/GaN Nanowire Emitters through Localized Laser Recrystallization

Ha-Neul Eom¹, Sung-Un Kim¹, Chandran Bagavath¹, Geon-Yeong Kim¹, Si-Won Park¹, Ui-Seong Hong¹, Dae-Young Um², and Yong-Ho Ra¹, ¹Jeonbuk National University, Korea, ²Kumoh National Institute of Technology, Korea

[WeP-15]

17:10-18:40

Enhancement of Color-Conversion Efficiency via Double-Sided Epitaxial Structure with Quantum Dots-Embedded Porous GaN

Jaeyoung Baik¹, Je-Sung Lee¹, Jeongwoon Kim¹, Hoe-Min Kwak², Jin-Soo Kim¹, Yu-Jin Park¹, Jaeyoung Kwon¹, Woo-Lim Jeong¹, Hyeondong Lee³, JoonSeop Kwak³, Chang-Mo Kang⁴, and Dong-Seon Lee¹, ¹Gwangju Institute of Science and Technology, Korea, ²Electronics and Telecommunications Research Institute, Korea, ³Korea Institute of Energy Technology, Korea, ⁴Pusan National University, Korea

[WeP-16]

17:10-18:40

In-Situ SiNx Interlayer for Improved Ohmic Contacts in Al-Rich AlGaN Channel HEMTs

Joocheol Jeong, Shyam Mohan, Hyogeun Cho, Minyeong Kim, Mingoo Jo, and Okhyun Nam, Tech University of Korea, Korea

[WeP-17]

17:10-18:40

Toward High Threshold Voltage, High Carrier Density p-GaN/AlGaN/GaN HEMTs

Moon Uk Cho¹, Min-Ki Hong¹, Yuhyeon Bak^{1,2}, Hyunchul Lim¹, Young-Hun Han^{1,2}, and June-O Song¹,
¹Wavelord Inc., Korea, ²Tech University of Korea, Korea

[WeP-18]

17:10-18:40

Bright Room-Temperature Telecom-Band GaN Single-Photon Emitters on Patterned Sapphire Substrates

Hyemin Kim^{1,2}, Dong Seok Shin¹, Yong-Ho Song¹, Young-Ho Ko², and Yong-Hoon Cho¹, ¹Korea Advanced Institute of Science and Technology, Korea, ²Electronics and Telecommunications Research Institute, Korea

[WeP-19]

17:10-18:40

Nano Voids Formed through Nano-Silica for Mechanical Lift-Off of III-Nitrides

Da-Young Kim, Tae-Hoon Chung, Sam-Seok Jang, and Jung-Hong Min, Korea Photonics Technology Institute, Korea

[WeP-20]

17:10-18:40

InGaN-Based Red LEDs for All-Nitride R/G/B Micro-LEDs

Won Kwang Yang, Joonghoon Choi, Joohan Bae, and Young Joon Hong, Sungkyunkwan University, Korea

[WeP-21]

17:10-18:40

Fabrication of High-Brightness GaN Nanorod LEDs for AR Display Applications

Chang Soo Kim¹, Joonghoon Choi¹, Joohan Bae², Inseok Ju², Hak-Jong Choi³, and Young Joon Hong^{1,2}, ¹Sungkyunkwan University, Korea, ²Korea Institute of Machinery & Materials, Korea

[WeP-22]

17:10-18:40

Suppression of S-Droop in AlGaInP Micro-LEDs via Sidewall Native Oxide Substitution with Sulfide Layers

Je-Sung Lee¹, Jaeyong Kwon¹, Jaeyoung Baik¹, Seung Hyeok Lee¹, Sugyeong Cha¹, Chang-Mo Kang², and Dong-Seon Lee¹, ¹Gwangju Institute of Science and Technology, Korea, ²Pusan National University, Korea



[WeP-23]

17:10-18:40

Lg=60nm AlGaIn/GaN HEMTs on Si for 6G Applications

Ji-Seung Seo, Jin-sup Kim, and Hyeon-Bhin Jo, Korea Electronics Technology Institute, Korea

[WeP-24]

17:10-18:40

Selective Area Growth of InGaIn/GaN Quantum Dots via Focused Ion Beam Patterning

Baul Kim and Yong-Hoon Cho, Korea Advanced Institute of Science and Technology, Korea

[WeP-25]

17:10-18:40

Processing Aspects of MOVPE Grown Monolithic High Contrast Grating VCSELs for Near-Infrared Applications

Joanna Prażmowska¹, Emilia Baczeńska¹, Mikołaj Badura¹, Magdalena Marciniak², Marcin Gębski², Tomasz Czystanowski², and Regina Paszkiewicz¹, ¹Wrocław University of Science and Technology, Poland, ²Lodz University of Technology, Poland

[WeP-26]

17:10-18:40

Comparative Study of GaN-Based Planar Micro-LEDs and Nanorod LEDs Fabricated by Top-Down Etching

Joohan Bae, Chang Soo Kim, Joonghoon Choi, and Young Joon Hong, Sungkyunkwan University, Korea

[WeP-27]

17:10-18:40

Surface Protection by Temporary SiO₂ Passivation During High-Temperature Rapid Thermal Annealing Improves E-Mode AlGaIn/GaN HEMTs

Min-Ki Hong¹, Hyunchul Lim¹, Yuhyeon Bak^{1,2}, Moon Uk Cho¹, Young-Hun Han^{1,2}, and June-O Song¹, ¹Wavelord Inc., Korea, ²Tech University of Korea, Korea

[WeP-28]

17:10-18:40

DC Characteristics Depending on Device Dimension about Quasi-Vertical GaN Schottky Barrier Diodes

Seongmin Kang, Jinsup Kim, and Hyeon-bhin Jo, Korea Electronics Technology Institute, Korea

[WeP-29]

17:10-18:40

Suppression of Trap-Induced Kink Effect in RF AlGaIn/GaN HEMTs through Optimized Buffer Layer Engineering

Yuhyeon Bak^{1,2}, Moon Uk Cho¹, Min-Ki Hong¹, Hyunchul Lim¹, Young-Hun Han^{1,2}, Sung-Nam Lee², Yoon Seok Kim², and June-O Song¹, ¹Wavelord Inc., Korea, ²Tech University of Korea, Korea

[WeP-30]

17:10-18:40

Optimization of Thin Epi-Layer Structure for 200V-Class GaN-on-Si HEMTs with Enhanced Breakdown Characteristics

Hyunchul Lim¹, Young-Hun Han^{1,2}, Yuhyeon Bak^{1,2}, Moon Uk Cho¹, Min-Ki Hong¹, and June-O Song¹, ¹Wavelord Inc., Korea, ²Tech University of Korea, Korea

[WeP-31]

17:10-18:40

Growth and Characterization of In₂Te₃ Thin Films

Hoki Son¹, Wonjung Choi¹, Yeoson Sim², and Jinsung Kwak¹, ¹Changwon National University, Korea, ²Argonne National Laboratory, United States

[WeP-32]

17:10-18:40

High-Efficiency and Narrow Linewidth Green CdSe/CdZnS Quantum Dots via Steric Hindrance-Controlled Core Engineering

Byoung-ho Kang, Jaesung Lee, Saewan Kim, Sanghoon Jung, Sehyuk Yeom, and Wanghoon Lee, Gumi Electronics and Information Technology Research Institute, Korea

[WeP-33]

17:10-18:40

Al-Induced Self-Passivation for Enhanced Stability of CdSe/ZnS QD-Based QLEDs

Jaesung Lee, Byoung-ho Kang, Saewan Kim, Sanghoon Jung, Sehyuk Yeom, and Wanghoon Lee, Gumi Electronics and Information Technology Research Institute, Korea

[WeP-34]

17:10-18:40

Fabrication and Characterization of Resistive Memory Device based on Quantum Dots (QDs)/PVK Hybrid Nanocomposites

Sae-Wan Kim¹, Byoung-Ho Kang¹, Jae-Sung Lee¹, Sang-Hoon Jung¹, Se-Hyuk Yeom¹, Jin-Beom Kwon², Dong-Geon Jung³, and Wang-Hoon Lee¹, ¹Gumi Electronics and Information Technology Research Institute, Korea, ²Kyungwoon University, Korea, ³Korea Institute of Industrial Technology, Korea

**[WeP-35]**

17:10–18:40

Vibrational and Strain Properties of Semipolar (11–22) AlN Films on M-Sapphire

Bei Ma^{1,2}, Kensei Oya², Ryota Akaike², Yoshihiro Ishitani¹, and Hideto Miyake², ¹Chiba University, Japan, ²Mie University, Japan

[WeP-37]

17:10–18:40

Modeling Study of Composition and Thickness Uniformity of AlGaIn Layers in UVC LED Structures

Yury Shustrov and Aleksa Galić, Semiconductor Technology Research d.o.o. Beograd, Serbia

[WeP-38]

17:10–18:40

Structure–Property Relationship of Morphology–Controlled CuS Nanostructures on Cu–Modified Gas Diffusion Electrodes

Jiwon Heo¹, Vishal Burungale¹, Chaewon Seong², Pratik Mane³, Hyojung Bae¹, and Jun–Seok Ha¹, ¹Chonnam National University, Korea, ²Korea Institute of Industrial Technology, Korea, ³Korea Photonics Technology Institute, Korea

[WeP-39]

17:10–18:40

MOVPE–Grown InGaAs–Based Strain–Balanced Multi–Quantum–Well 0.66–eV Absorber Material for Thermophotovoltaics

D. Lackner¹, A. Darwish^{1,2}, A. W. Bett^{1,2}, and H. Helmers¹, ¹Fraunhofer Institute for Solar Energy Systems ISE, Germany, ²University of Freiburg, Germany

[WeP-41]

17:10–18:40

Etch Resistance of Nitride MOCVD Reactor Components

Tomoe Yamamoto¹, Takayuki Togawa¹, Neal Gaffin², Taohid bin nur Tuhser², Creighton Tomek², Wei Fan², Yani Sun², Bowen Dong², and Jon Leist², ¹Momentive Technologies Japan K.K., Japan, ²Momentive Technologies, Inc., USA

[WeP-42]**No-show**

17:10–18:40

Interface–Engineered Van der Waals BN/AlN Templates for High–Performance AlGaIn/GaN HEMTs

Haidi Wu^{1,2}, Jing Ning^{1,2}, Yue Hao^{1,2}, and Jincheng Zhang^{1,2}, ¹The State Key Laboratory of Wide–Bandgap Semiconductor Devices and Integrated Technology, China, ²Xidian University, China

[WeP-43]

17:10-18:40

A First Look of Arsenic Incorporation into AlN for Wurtzite AlAsN

Xu Yang¹, Xinhua Wang¹, Xinyu Liu¹, and Markus Pristovsek², ¹Institute of Microelectronics, Chinese Academy of Sciences, China, ²Institute of Materials and Systems for Sustainability, Nagoya University, Japan

[WeP-44]

17:10-18:40

**Quantum Barrier Height Optimization for Efficient Far-UVC AlGaIn MQW LEDs:
A Comparison to the Thick Single-Layer Active Region Design**

Zhekai Gu^{1,2}, Yanan Guo^{1,2}, Jianchang Yan³, Jinmin Li^{1,4}, and Junxi Wang^{1,2}, ¹Institute of Semiconductors, Chinese Academy of Sciences, China, ²University of Chinese Academy of Sciences, China, ³Beihang University, China, ⁴Advanced Ultraviolet Optoelectronics Co., Ltd., China

[WeP-45]

17:10-18:40

Visible-InGaIn-Based Long-Single Nanowire Laser for Future Photonic Applications

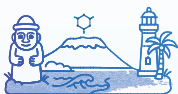
Sung-Un Kim¹, Dae-Young Um², Jeong-Kyun Oh¹, Min-Seok Lee¹, Cheul-Ro Lee¹, and Yong-Ho Ra¹, ¹Jeonbuk National University, Korea, ²Kumoh National Institute of Technology, Korea

[WeP-46]

17:10-18:40

The Origin of Efficiency in III-Nitride Micro Light-Emitting Diodes

Illi Hwang, Minji Ryu, and Dong-Pyo Han, Pukyong National University, Korea



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ICC JEJU, Jeju Island, Korea

VI.

Exhibition

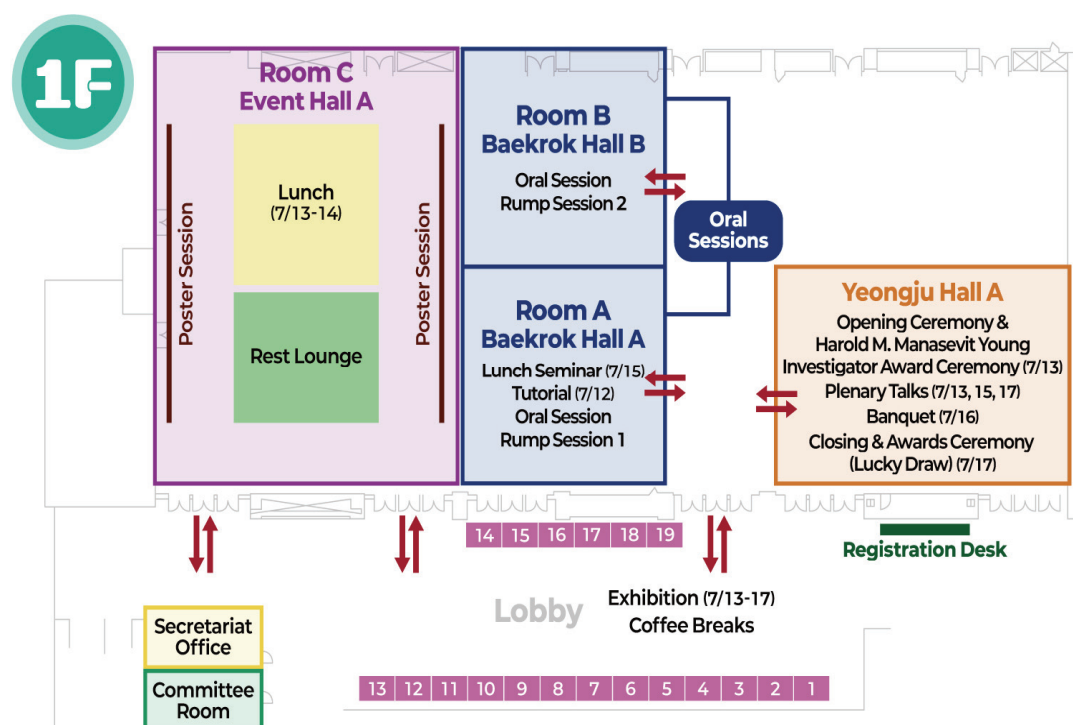


ICMOVPE XXII will be held in conjunction with the conference. All attendees may have opportunity to visit the exhibition and to communicate with representatives from the industry during the conference.

- Location: Lobby, 1F, ICC JEJU
- Operating Hours: The exhibition hall will be open during the conference as follows:

Date	July 13 (Mon.)	July 14 (Tue.)	July 15 (Wed.)	July 16 (Thu.)	July 17 (Fri.)
Time	09:00–18:00	08:30–17:40	08:30–20:30	08:30–20:30	09:20–12:00

- Layout and List of Booth





Booth No.	Company	Booth No.	Company
1	TES Co., Ltd.	11	WaveLord Inc.
2	DXG Co., Ltd.	12	Chonnam National University ECCF-NISRI
3	AccuOptotec Co., Ltd.	13	L&D Inc.
4	Suwon Special City	14	Dockweiler Chemicals GmbH
5	AIXTRON	15	Malvern Panalytical
6	Nippon Sanso Corporation	16	HI-SOLAR CO., LTD.
7	Korea Advanced Nano Fab Center	17	Semilab Korea Co., Ltd.
8	Advanced Furnace Technology Ltd	18	Semiconductor Technology Research DOO BG
9	AXT, Inc.	19	LayTec AG
10	LumiGNtech Co. Ltd		

Booth No.1			Company Logo
Company Name	TES Co., Ltd.		
Address	2374-36, Jungbu-daero, Yangji-eup, Cheoin-gu, Yongin-si, Gyeonggi-do, South Korea		
President	Jaeyoung Joo		
E-mail	oesales@hites.co.kr	Website	www.hites.co.kr/eng
Tel	+82-31-323-2552	Fax	+82-31-323-2555
Exhibitor Introduction	TES Co., Ltd. is a Korea-based semiconductor equipment company specializing in CVD and high-temperature MOCVD systems. Based on its accumulated experience in front-end semiconductor CVD equipment, TES is expanding its compound semiconductor business for wide-bandgap devices. The company focuses on Power SiC for EVs, high-voltage power grids, renewable energy, ESS, rail and AI data-center power infrastructure, and RF GaN on SiC for 5G/6G, LEO satellite communication, radar and defense applications. TES develops production-oriented epitaxy platforms that address key requirements such as high-temperature stability, high growth rate, process uniformity, low defect density and scalable system architecture. TES also supports customer-specific Ga2O3 epitaxy development.		
Exhibit Product	TES will exhibit TRION, a tunable high-temperature epitaxy platform for Power SiC and RF GaN HEMT on SiC. For Power SiC, TRION SiC targets thin re-growth epi, MOSFET drift layers and thick high-voltage epi, with high growth rate and excellent thickness and doping uniformity. For RF GaN, TRION GaN enables high-quality thick AlN buffer growth on SiC using high-temperature operation, fast gas switching and pulsed growth to improve crystallinity, insulation and thermal performance. TRION combines a special pancake-type RF T-Heater and a tunable triple-pair nozzle, allowing spatial control of temperature and gas distribution. This tunable architecture supports uniformity control, process recovery and scale-up without changing the core platform.		



Booth No.2			Company Logo
Company Name	DXG Co., Ltd.		
Address	102-8, Hoean-Daero, Opo-Eup, Gwangju-si, Gyeonggi-do, South Korea		
President	Young Joon Kim		
E-mail	ok@dxg.kr	Website	www.dxg.kr
Tel	+82-70-4673-4719	Fax	+82-2-564-0222
Exhibitor Introduction	Established in 1989, DXG Co., Ltd. is a Korea-based optical instrumentation company specializing in PL/Raman spectroscopy systems, spectrometers, monochromators, and related photonics solutions. With in house R&D and manufacturing capabilities, DXG has supplied advanced optical systems to universities, research institutes, and industrial R&D centers in Korea and overseas. DXG continues to support scientific research and technology development by providing reliable instruments, customized system integration, and technical expertise.		
Exhibit Product	• MOMO Compact Spectrometer • PL/Raman Spectroscopy Systems • Spectrometers and Monochromators • Scientific Cameras • Lasers and Optical Components • Photonics Measurement Solutions		

Booth No.3			Company Logo
Company Name	AccuOptotec Co., Ltd.		
Address	56 Gongjudaehakro, Kongju National Univ., Kongju, South Korea		
President	Jung-Hoon Song, Youngboo Moon		
E-mail	farnear9@accuopto.com	Website	www.accuopto.com
Tel	+82-41-850-8584	Fax	+82-41-850-8489
Exhibitor Introduction	AccuOptotec Co., Ltd. is a deep-tech startup founded in January 2023, specializing in ultra-fast Fourier-Transform Raman spectroscopy systems for next-generation semiconductor inspection and characterization. Based on our patented CPFT-Raman (Common-Path Fourier-Transform Raman) spectroscopy engine, we deliver measurement speeds of 0.05 ms/pixel — more than 1,000 times faster than conventional Raman systems — with sub-micron spatial resolution ($<0.5\ \mu\text{m}$).		
Exhibit Product	★ NEW — WBG Homoepitaxy Thickness Monitor In-situ / ex-situ Raman homoepitaxy thickness monitoring using confocal LOPC mode. Supports GaN, SiC, Ga_2O_3, and AlN epitaxial layers. 01 Ultra-HR Thermal Imager Sub-micron resolution ($<0.5\ \mu\text{m}$) Raman-based thermal imaging for GaN and SiC devices. Enables hot-spot mapping at over 1,000× the speed of conventional systems. 02 3D Thermal Conductivity Analyzer Layer-by-layer thermal conductivity (κ) measurement for GaN-on-Si power devices. Enables 3D depth profiling of thermal properties in heterogeneous epitaxial stacks. 03 Glass Substrate Cu Filling Inspector Non-destructive 100% in-line inspection of TGV (Through-Glass Via) void and delamination defects in glass substrates for advanced packaging. 64-channel multi-beam array enables full-panel inspection within 30 minutes.		



Booth No.4			Company Logo
Company Name	Suwon Special City		
Address	241 Hyowon-ro, Paldal-gu, Suwon-si, Gyeonggi-do, South Korea		
President	Jaejoon Lee		
E-mail	yoonsunn@korea.kr	Website	www.suwon.go.kr
Tel	+82-31-5191-2657	Fax	+82-31-369-2151
Exhibitor Introduction	Suwon City is the central hub of southern Gyeonggi Province, located just 23km from Gangnam, Seoul — a mere 30-minute drive — offering exceptional access to the capital region's core areas. With a population of 1.22 million and a Gross Regional Domestic Product (GRDP) of 41 trillion KRW in 2022, ranking 3rd among all cities in Gyeonggi Province, Suwon boasts a robust economic foundation. The city is also home to the main headquarters of Samsung Electronics, alongside leading institutions such as Sungkyunkwan University and the Korea Advanced Nano Fab Center (KANC), forming a dense cluster of advanced industry and research. Building on this foundation, Suwon City is pursuing designation as Free Economic Zones, with compound semiconductors positioned as one of its core strategic industries. Companies and institutions establishing operations within the Suwon Free Economic Zone can benefit from three key advantages: first, investment incentives such as tax benefits; second, regulatory exemptions, including relief from restrictions under the Overconcentration Control Region designation pursuant to the Seoul Metropolitan Area Readjustment Planning Act; and third, a high-quality living environment supported by world-class education, healthcare, and cultural infrastructure. Through this exhibition, Suwon City seeks to build long-term, mutually beneficial partnerships with global leaders in the field — spanning joint R&D, talent exchange, and investment opportunities within the S-FEZ.		
Exhibit Product	Introduction to Suwon Free Economic Zone (S-FEZ) Development Plan & Investment Conditions • Presentation of the grand master plan and vision for establishing a world-class science and research city. • Information on tailored incentives, administrative support, and frameworks for global enterprises and foreign-invested companies.		

Booth No.5			Company Logo
Company Name	AIXTRON		
Address	Dornkaulstr.2, 52134 Herzogenrath		
President	Dr. Felix Grawert		
E-mail	info@aixtron.com	Website	www.aixtron.com/en
Tel	+49-2407-9030-9022	Fax	
Exhibitor Introduction	AIXTRON SE is a leading provider of deposition equipment to the semiconductor industry. The Company was founded in 1983 and is headquartered in Herzogenrath (near Aachen), Germany, with subsidiaries and sales offices in Asia, United States, and in Europe. AIXTRON's technology solutions are used by a diverse range of customers worldwide to build advanced components for electronic and optoelectronic applications based on compound or organic semiconductor materials. Such components are used in a broad range of innovative applications, technologies and industries. These include Laser and LED applications, display technologies, data transmission, SiC and GaN power management and conversion, communication, signaling and lighting as well as a range of other leading-edge applications		

Booth No.6			Company Logo
Company Name	Nippon Sanso Corporation		
Address	1-3-26 Koyama, Shinagawa-ku Tokyo 142-8558, Japan		
President	Kenji Nagata		
E-mail	mocvd@jp.nipponsanso.com	Website	https://nsc.jp.nipponsanso.com/mocvd/
Tel	+81-45-872-1822	Fax	
Exhibitor Introduction	NSC was the first company to introduce its self-developed commercial MOCVD systems in 1983. NSC equipment for mass-production and R&D has received praise for its world-class performance and stability. NSC is also uniquely qualified to provide total solutions for MOCVD applications, including purification and abatement equipment, and specialty gases and gas handling equipment.		



Booth No.7			Company Logo
Company Name	Korea Advanced Nano Fab Center		 Korea Advanced Nano Fab Center
Address	109, Gwanggyo-ro, Yeongtong-gu, Suwon-si, Gyeonggi-do, South Korea		
President	Dae Seok Byeon		
E-mail	dongwhan.shin@kanc.re.kr, baeki.chung@kanc.re.kr	Website	www.kanc.re.kr
Tel	+82-31-546-6521, 6530	Fax	+82-31-546-6409
Exhibitor Introduction	Korea Advanced Nano Fab Center (KANC) is Korea's leading national nanofabrication infrastructure, dedicated to advancing nanotechnology research and the development of compound semiconductor-based nanodevices. The main goals of KANC are to establish a world-class nanofabrication facility for compound semiconductor-based nanodevices and to provide fabrication and research services to users worldwide. The center was established in 2003 through funding from the Korean government and is located in eastern Suwon, the heart of Korea's semiconductor industry. In April 2006, KANC completed the construction of a state-of-the-art nanofabrication facility. The center operates a 3,500 m² cleanroom and is equipped with approximately 165 types of fabrication and analysis equipment. The facility consists of a front-end process line, a back-end process line, and a rental area. In addition, the measurement and analysis laboratory is located in the basement. KANC provides comprehensive support for nanotechnology research and the fabrication of compound semiconductor-based nanodevices. Through its user-oriented operation, the center is committed to providing the highest level of service to both domestic and international users.		

Booth No.8			Company Logo
Company Name	Advanced Furnace Technology Ltd		
Address	18 Cheddars Lane, Cambridge, CB5 8LD, United Kingdom		
President	Paul Tolkien		
E-mail	enquire@advancedft.com	Website	https://advancedfurnacetech.com
Tel	+44-1223-461-321	Fax	
Exhibitor Introduction	Advanced Furnace Technology Ltd (AFT) is a UK-based specialist company providing high-temperature cleaning, purification and coating services for graphite and silicon carbide components used in the semiconductor and advanced technology industries. With extensive experience in supporting MOCVD and other high-temperature applications, AFT offers thermal cleaning, high purity processing and pyrolytic graphite coating solutions to extend component lifetime and improve performance. Operating from our facilities in Cambridge, United Kingdom, we work closely with leading manufacturers, research organizations and technology companies worldwide, providing reliable, high-quality processing with a strong focus on customer requirements and continuous improvement.		
Exhibit Product	• High-temperature graphite cleaning and purification services • Pyrolytic graphite (PyG) coating services • MOCVD graphite component refurbishment solutions		



Booth No.9			Company Logo
Company Name	AXT, Inc.		
Address	4281 Technology Drive Fremont CA 94538 USA		
President	Morris Young CEO		
E-mail	sales@axt.com	Website	www.axt.com
Tel	+1-510-438-4700	Fax	
Exhibitor Introduction	AXT is a material science company that develops and manufactures high-performance compound and single element semiconductor wafer substrates comprising indium phosphide (InP), gallium arsenide (GaAs) and germanium (Ge). AXT's worldwide headquarters are in Fremont, California and includes sales, administration and customer service functions. AXT's subsidiary in China ("Tongmei") has similar functions as well as manufacturing facilities to produce wafer substrates. In addition, as part of the supply chain strategy, AXT, Tongmei and Tongmei subsidiaries collectively have partial ownership in ten companies in China producing raw materials.		
Exhibit Product	Wafers		

Booth No.10			Company Logo
Company Name	LumiGNtech Co., Ltd		
Address	Room 902, E-dong, 60, Haan-Ro, Gwangmyeong-Si, Gyeonggi-do, South Korea 14322		
President	Hae-Yong, Lee		
E-mail	ohk7100@lumigntech.net	Website	www.lumigntech.net
Tel	+82-2-6112-2340	Fax	+82-2-6112-2342
Exhibitor Introduction	Welcome to LumiGNtech, a specialized manufacturer of advanced compound semiconductor substrates and templates. We provide high-quality Gallium Nitride (GaN) and Aluminum Nitride (AlN) wafers grown via our proprietary, high-throughput HVPE (Hydride Vapor Phase Epitaxy) technology. Our core products include free-standing GaN wafers, AlN templates, and AlGaN templates. These materials are essential for next-generation applications such as Ultra High Brightness (UHB) LEDs, Micro/Nano LEDs, UVC LEDs, and Power/RF electronics. LumiGNtech stands out with its cost-effective and highly efficient manufacturing process. By utilizing our innovative self-separation technology with an AWC (AlN with Carbon buffer) layer.		
Exhibit Product	GaN wafer, AlN template, Ga2O3 epi wafer, AlN with Carbon buffer template		



Booth No.11			Company Logo
Company Name	WaveLord Inc.		 WaveLord
Address	(18589) 411-31, Baran-ro, Hyangnam-eup, Manse-gu, Hwaseong-si, Gyeonggi-do, South Korea		
President	JuneO Song		
E-mail	admin@wavelord.co.kr	Website	www.wavelord.co.kr/eng/
Tel	+82-31-366-3442	Fax	+82-31-366-3470
Exhibitor Introduction	WaveLord is a GaN compound semiconductor solutions company that supplies epitaxial wafers and devices across the communications, power, and display industries. Spanning three platforms, RF GaN-on-SiC, 8-inch Power GaN-on-Si, and MicroLED, we offer a broad portfolio that extends from epitaxy to devices, addressing the diverse application needs of our customers. In the RF domain, we supply 4-inch and 6-inch GaN-on-SiC epitaxy for high-power RF amplifiers used in 5G/6G communications and defense systems, with a differentiated lineup that includes the buffer-free WLBF™ and the Fe-doped WLGB™. In the power domain, we provide 8-inch E/D-mode GaN-on-Si epitaxy for next-generation power conversion, tailored to application-specific voltage classes of 650V, 200V, and 100V. In the display domain, we go beyond epitaxy to fabricate devices in-house, supplying LEDoS with ultra-fine pixel pitches of 5μm and 2.5μm, along with MicroLED COW (Chip-on-Wafer) and COC (Chip-on-Carrier) devices, to serve the next-generation microdisplay market. Building on our differentiated proprietary technologies, WaveLord delivers a total GaN solution spanning both epitaxy and devices, enabling our customers to realize their next-generation technologies.		
Exhibit Product	8inch GaN-on-Si Epiwafer, 6inch GaN-on-Si Epiwafer, 4inch RF GaN-on-SiC Epiwafer etc		

Booth No.12		Company Logo	
Company Name	Chonnam National University ECCF-NISRI		
Address	77, Yongbong-ro, Buk-gu, Gwangju, South Korea		
President	Jun Seok HA		
E-mail	jnu.eccf@gmail.com	Website	www.zeus.go.kr/cloud/eccf
Tel	+82-62-530-1977	Fax	
Exhibitor Introduction	The Energy Convergence Core-Facility (ECCF) and Gwangju·Jeonnam National Inter-university Semiconductor Research Institute (NISRI) provide advanced research infrastructure and technical support for energy, semiconductor, and packaging technologies. Our facilities support research in photonics and energy convergence, optoelectronic devices, advanced materials, semiconductor materials and devices, and advanced semiconductor packaging. Equipped with state-of-the-art fabrication and characterization systems, cleanroom facilities, and packaging platforms, we offer comprehensive support from fundamental research to industrial applications. Through collaboration with academia, industry, and government, as well as user training, technical services, and industry partnerships, ECCF and NISRI contribute to technological innovation, workforce development, and the advancement of next-generation energy and semiconductor technologies. Together, we serve as a leading research support hub driving innovation for a sustainable and net-zero future.		



Booth No.13			Company Logo
Company Name	L&D Inc.		
Address	Room 411, Daejeon TIPS Town, 99 Daehak-ro, Yuseong-gu, Daejeon, South Korea		
President	Kwanghee Kim		
E-mail	talk@lnd35.com	Website	https://lnd35.com/
Tel	+82-42-382-3335	Fax	+82-42-480-4307
Exhibitor Introduction	L&D Inc. specializes in AlN-based epitaxial wafer solutions for next-generation RF, power, and UV device applications. Our core technology is the growth of thick, high-quality AlN layers with excellent crystalline quality, smooth surface morphology, and stable material uniformity. Based on our in-house MOCVD growth technology, L&D Inc. develops AlN templates and AlN buffer-based GaN HEMT epiwafers on SiC substrates. These epiwafer platforms are designed to support high-frequency and high-power semiconductor devices, including RF power devices, 5G/6G communications, satellite communication, radar systems, power electronics, and UV devices. L&D Inc. is committed to providing reliable AlN-based epiwafer products by continuously improving AlN growth quality, thickness control, surface uniformity, and device-oriented epitaxial structures.		
Exhibit Product	• 4-inch Customized AlN Buffer-based Epitaxial Wafers • AlN on SiC Template • GaN & AlGaN Channel HEMT Epiwafers • Doped GaN & AlN Structures • 6-inch AlN Template		

Booth No.14			Company Logo
Company Name	Dockweiler Chemicals GmbH		
Address	Emil-von-Behring-Strasse 76, 35041 Marburg		
President	Jörg Koch		
E-mail	info@dockchemicals.com	Website	http://www.dockchemicals.com/
Tel	+49-642139-6380	Fax	+49-642139-6381
Exhibitor Introduction	Dock is a trusted provider of metal-organic chemistry solutions, with a history spanning over 30 years. We specialize in serving the III/V semiconductor market, as well as addressing the demands of the CVD, ALD, and MOVPE industries. We offer a comprehensive range of precursors essential for these applications, packaging tailored to your specific needs, and a full range of bubbler services, including cleaning, maintenance, and transfilling of larger batches for our customers worldwide. In addition to product supply, we are a science-driven company offering custom synthesis, molecule scaling, and purification process development. Adhering to stringent quality standards, we utilize various methods, such as ICP-AES, ICP-MS, H-NMR, and GC, for quality control. Dock holds ISO 9001 quality management certification, demonstrating our commitment to delivering products of the highest quality. Our ISO 14001 environmental management certification reflects our dedication to sustainable business practices. In summary, Dock is your trusted partner for precursor chemistry solutions, providing the highest quality products and services to support the evolving requirements of the semiconductor industry.		
Exhibit Product	High-purity metal organics such as TEB, TMAI, TMGa, TEGa, TBP, TBAs, TMSb, TESb, TMBi dopants, liquid Scandium and Yttrium precursors and many more		



Booth No.15			Company Logo
Company Name	Malvern Panalytical		
Address	Enigma Business Park, Grovewood Road, Malvern, Worcestershire WR14 1XZ, United Kingdom		
President	Christian Sauber		
E-mail	Korea.info@malvernpanalytical.com	Website	www.malvernpanalytical.com
Tel	+82-31-786-0840	Fax	
Exhibitor Introduction	Malvern Panalytical is a leading provider of advanced analytical instrumentation and software solutions for materials characterization. Our technologies support research, development, manufacturing, and quality control across a wide range of industries, including semiconductors, advanced materials, batteries, pharmaceuticals, and academia. For the semiconductor industry, Malvern Panalytical offers comprehensive characterization and metrology solutions for thin films, epitaxial layers, crystal structures, elemental composition, and wafer analysis. Our solutions help researchers and manufacturers accelerate innovation, improve process control, and enhance product performance. With decades of scientific expertise and a global network of application specialists, Malvern Panalytical partners with customers worldwide to solve complex analytical challenges and advance semiconductor and materials research.		
Exhibit Product	Empyrean Series – Advanced X-ray diffraction (XRD) platform for thin-film characterization, epitaxial layer analysis, reciprocal space mapping (RSM), high-resolution XRD (HRXRD), X-ray reflectivity (XRR), and semiconductor materials research. 2030ZT Wafer Analyzer – Advanced semiconductor thin-film X-ray fluorescence (XRF) metrology solution for non-destructive elemental composition and thickness measurement of semiconductor wafers. Crystal Orientation Range – High-precision X-ray diffraction solutions for crystal orientation, wafer alignment, off-cut angle measurement, and quality control of semiconductor substrates including Si, SiC, GaN, sapphire, and other single-crystal materials.		

Booth No.16			Company Logo
Company Name	HI-SOLAR CO., LTD.		
Address	313, Cheomdangwagi-Ro, Buk-Gu, Gwangju-City, 61008 South Korea		
President	Choon Ho An		
E-mail	sales@hisolarled.com	Website	www.hisolarled.co.kr
Tel	+82-62-973-0490	Fax	+82-62-973-0489
Exhibitor Introduction	Hi-Solar focuses more on inner strength than external growth, and values trust more than appearance. Founded in 1999, Hi-Solar has specialized in high-precision surface preparation of sapphire wafers for blue and green LED applications. We have developed proprietary lapping and polishing processes for ultra-flat sapphire substrates. Through these advanced technologies, we are able to produce 2-, 3-, 4-, and 6 inch sapphire substrates with bow less than 5 μm and surface roughness (RMS) as low as 0.2 nm while maintaining high productivity. In addition, Hi-Solar provides a wide range of semiconductor and optoelectronic materials, including Glass, SiC, Si, GaAs, and Ga_2O_3 substrates for power electronics, RF devices, optoelectronics, and advanced semiconductor applications.		
Exhibit Product	Sapphire wafer, Si wafer, SiC wafer, Glass wafer		

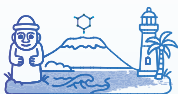


Booth No.17			Company Logo
Company Name	Semilab Korea Co., Ltd.		
Address	411,412,413,414,830 Dongtan Circulation-daero, Hwaseong-si, Gyeonggi-do, South Korea		
President	Jason Chung		
E-mail	Salesadmin.korea@semilab.com	Website	https://www.semilabkr.com/
Tel	+82-31-630-2172~4	Fax	+82-31-630-2175
Exhibitor Introduction	We are the strategic metrology supplier and innovation partner of the leading wafer manufacturers, IC device makers in the More-than-Moore market segment, solar and display industries worldwide. We provide state-of-the-art metrology solutions for semiconductor device manufacturers, for both in-line and R&D segments, and we are the world leader in non-contact electrical metrology as well as contact and optical technologies.		
Exhibit Product	Non-contact, Non-destructive Precision Metrology, Semiconductor, Wafer Inspection, Display, Solar/Photovoltaic (PV), R&D		

Booth No.18			Company Logo
Company Name	Semiconductor Technology Research DOO BG		
Address	Veljka Dugosevica 54, Building B5, Zvezdara, 11000 Belgrade, Serbia		
President	Iuliia Rakita		
E-mail	jana.stanisavljevic@str-soft.com	Website	https://str-soft.com/
Tel	+381-60-339-0849	Fax	
Exhibitor Introduction	STR develops physics-based simulation software and provides modeling services for crystal growth, epitaxial processes, and the operation of semiconductor devices. Every software product is built on comprehensive in-house research to ensure careful validation of the physical models and numerical approaches. STR's expertise in crystal growth science and device engineering is reflected in numerous publications in peer-reviewed journals. Through predictive simulation, STR helps its partners understand and optimize their crystal growth and device processes across four areas: – crystal growth from the melt and solution; – bulk crystal growth from the gas and vapor phase; – deposition and epitaxy; – optoelectronic devices.		
Exhibit Product	Software packages: Virtual Reactor and CVDSim3D – epitaxy of compound semiconductors (GaN, III-V, Si, SiC) STREEM – stress buildup and relaxation in AlGaN- and InGaN-based epitaxial stacks CGSim – Cz, VGF, Bridgman, and Kyropoulos crystal growth from the melt and solution (Si, Ge, InP, GaAs, GaN, SiC, sapphire, YAG, and more) Virtual Reactor PVT – bulk crystal growth of SiC, AlN, and GaN by PVT and HVPE IProS2D – multiscale modeling of thermal and plasma-assisted device processing steps DiaDeMo – single-crystal diamond growth by MPCVD PolySim – polysilicon deposition by the Siemens process		



Booth No.19			Company Logo
Company Name	LayTec AG		 MEMBER OF THE NYNOMIC GROUP
Address	Seesener Str. 10-13		
President	Volker Blank		
E-mail	info@laytec.de	Website	www.laytec.de
Tel	+49-30-8900550	Fax	+49-30-890055180
Exhibitor Introduction	LayTec is a major provider of in-situ and in-line optical metrology for thin-film processes. These metrology tools are used in a broad range of thin-film applications such as LED & laser production, power devices and transistors, thin-film photovoltaics, oxide and organic deposition as well as other large area deposition processes. LayTec's integrated metrology provides access to all key thin-film parameters in real-time – either in-situ, during the deposition process, or in-line. Also, in-situ metrology tools for dry etching have been added expanding LayTec's portfolio along the production chain. Beyond these integrated methods, LayTec also offers mapping solutions which ideally complement in-situ measurements by providing uniformity analysis of the deposited layers. The implementation of LayTec metrology systems in production processes significantly shortens development cycles and enables efficient quality control that helps to considerably reduce production and development costs.		
Exhibit Product	EpiX[®] Comprehensive 2D optical wafer mapping for advanced compound semiconductor manufacturing. EpiCurve[®] TT Combines wafer curvature measurements with emissivity-corrected pyrometry and growth rate/thickness measurements by three-wavelength reflectance. TRItton[®] Automated endpoint detection for plasma etching with multi-wavelength in-situ reflectometry.		



ICMOVPE XXII
July 12(Sun.)-17(Fri.), 2026
ICC JEJU, Jeju Island, Korea

VII.

Sponsorship & Support





ICMOVPE XXII



The 22nd International Conference on Metal Organic Vapor Phase Epitaxy

VII. Sponsorship & Support

Organized by

- Korea Optoelectronic Society



Supported by

- Korea Tourism Organization
- Jeju Tourism Organization



Sponsorship

Diamond



Gold



Silver



Bronze





ICMOVPE XXII
July 12(Sun.)-17(Fri.), 2026
ICC JEJU, Jeju Island, Korea

VIII.

Conference Information



VIII. Conference Information

1. Secretariat Office

- Location : Room 100, 1F
- Opening hours

Date	Time	Place
July 12 (Sun.)	13:00-17:00	Lobby, 1F
July 13 (Mon.)	08:00-18:00	
July 14 (Tue.)	07:30-17:00	
July 15 (Wed.)	07:30-17:00	
July 16 (Thu.)	07:30-18:30	
July 17 (Fri.)	08:30-12:00	

2. Registration Desk

- Location : Lobby, 1F
- Opening hours

Date	Time	Place
July 12 (Sun.)	13:00-17:00	Lobby, 1F
July 13 (Mon.)	08:00-18:00	
July 14 (Tue.)	07:30-17:00	
July 15 (Wed.)	07:30-17:00	
July 16 (Thu.)	07:30-18:30	
July 17 (Fri.)	08:30-12:00	



• On-site Registration Fee

Category	Type	On-site (July 12 – 17)	Fee Includes
Conference (July 13–17)	Regular	USD 900	Access to all Technical Sessions, Exhibition, Welcome Reception (July 12), Lunches (July 13, July 14, July 15), and Banquet (July 16)
	Student	USD 550	Access to all Technical Sessions, Exhibition, Welcome Reception (July 12), and Lunches (July 13, July 14, July 15)
Tutorial (July 12)	Regular	USD 100	Access to Tutorial Only
	Student	USD 70	
Additional Banquet Ticket (July 16)		USD 120	1 Banquet Ticket

• Name Badge

For security purpose, participants must wear their name badges during the conference. If your badge needs any correction, please visit the registration desk for a replacement.

3. Opening Ceremony & Harold M. Manasevit Young Investigator Award Ceremony

- Date & Time : July 13 (Mon), 09:00–09:15
- Location: Yeongju Hall A, 1F

4. Social Programs

We hope these programs will enrich your conference experience and provide memorable opportunities to connect with fellow participants from around the world.

• Welcome Reception

Reconnect with colleagues or network with other professionals and form new alliances at this kickoff event.

- Date & Time : July 12 (Sun.), 18:00–19:30
- Location : Yeongju Hall A, 1F

• Excursion

Free Tour + Sandwich Lunch Box

Enjoy Jeju's breathtaking coastal scenery through a self-guided visit to **Jusangjeolli Cliff** and **Jeju Olle Trail Route 8**.

- Date & Time : July 16 (Thu.), 2026, 10:15-12:00
- Tour Fee : Free
- Included : Sandwich Lunch Box
 - No tour guide will accompany participants.
 - Participants may explore the attractions freely at their own pace.
 - Comfortable walking shoes are recommended.
 - Sandwich lunch boxes will be provided to registered participants only.



Spot 1: Daepo Jusangjeolli Cliff

Spectacular hexagonal volcanic rock formations created by ancient lava flows, offering breathtaking coastal views.



Spot 2: Baret Naegongwon

A tranquil park along Jeju Olle Trail Route 8, featuring scenic walking trails, green landscapes, and relaxing coastal views.



Spot 3: Jungmun Saekdal Beach

One of Jeju's most popular beaches, renowned for its crystal-clear waters, soft sandy shoreline, and beautiful coastal scenery. It is an ideal place to relax and enjoy the refreshing ocean views.

JEJU OLLE ROUTE 8

Discover more attractions, scenic spots, and trail information along Jeju Olle Route 8

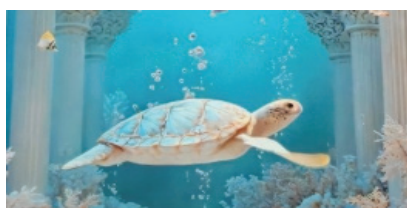




Optional Excursion: Innerlith Jeju → Seongsan Ilchulbong

Discover the beauty of eastern Jeju through a unique blend of immersive media art and breathtaking natural scenery.

- Date & Time : July 16 (Thu.), 2026, from 13:00
- Tour Fee : USD 50
- Departure from ICC (Meet-up at 12:40)



Innerlith Jeju

An immersive media art experience where come to life through cutting-edge digital technology, light, and sound.



Seongsan Ilchulbong (UNESCO World Heritage)

One of Jeju's most iconic volcanic landmarks, offering spectacular coastal scenery and panoramic views from the crater.

• Banquet

- Date & Time : July 16 (Thu.), 18:30–20:30
- Location: Yeongju Hall A, 1F

The Banquet will feature a delightful dinner and a captivating fusion performance of traditional Korean gugak and flamenco. Join us for an enjoyable evening of fine dining, cultural entertainment, and networking with fellow participants.

• Closing & Awards Ceremony (Lucky Draw)

- Date & Time : July 17 (Fri.) 12:05–12:35
- Location : Yeongju Hall A, 1F

Join us for the Closing Ceremony and don't miss the Lucky Draw!

5. Venue

"Beauty meets Brains at ICC JEJU"

Magnificent nature, abundant Tourist Assets, Convenient Access and Lodgings, Warm and Friendly People are the descriptions of Jeju, a worldly renowned resort in terms of its recreation and tourism. And on this gorgeous island, there lies a top-notch convention center: International Convention Center Jeju aka **ICC JEJU**.



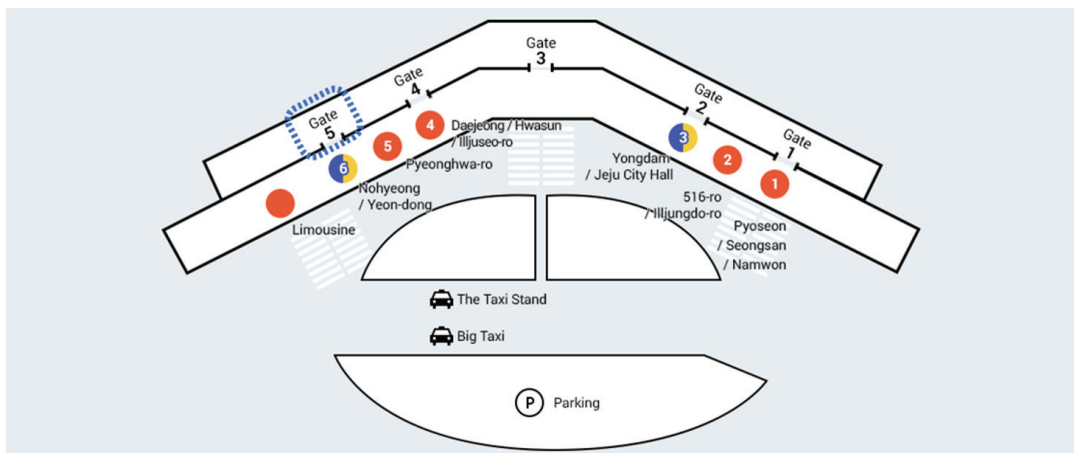
ICC JEJU is located in the Jungmun Tourist Complex with the cobalt-blue Northern Pacific stretching on the south and towering Mt. Hallasan in the north. Spreading over an area of more than 5,000m², the world-class convention center is a 7-story building. Artfully blending tourist resources and convention facility, this resort-style convention center is fully equipped for international meetings of any scale and provides professional logistic support in events hosting. For all these reasons, **ICC JEJU** is certainly an ideal site for conferences.

6. Transportation

[Jeju Airport → ICC] Option 1. Limousine bus

After arriving at Jeju International Airport, you can take the airport limousines to get to ICC Jeju. Limousine bus stop is located near Gate 5. (Samyoung Traffic No. 600, 601) Limousine bus stop.

Limousine bus stop





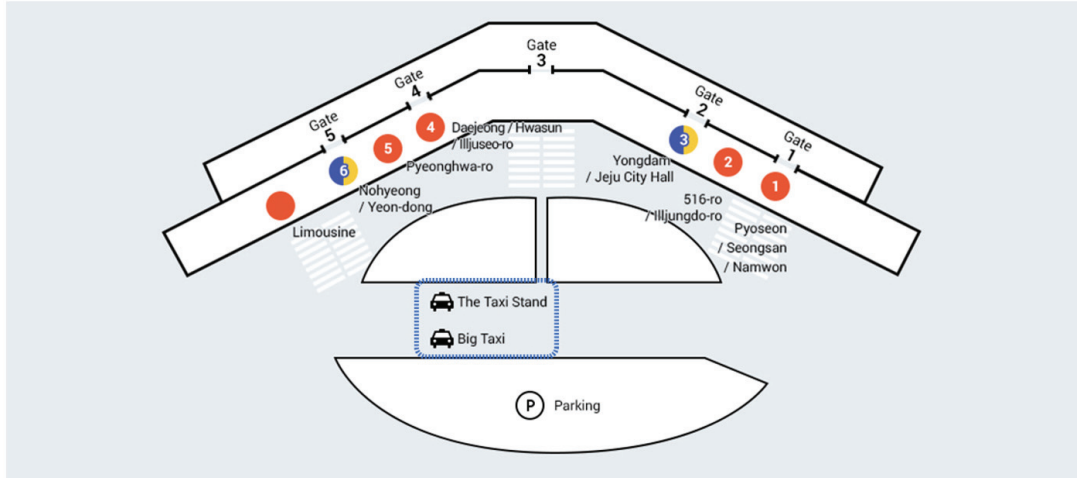
Route title	600
Get on/off here	Limousine Stop is in front of Gate 5
Fare	One-way (adult) KRW 4,500 from the airport to ICC JEJU
First/Last Bus	• Airport → Seogwipo KAL Hotel First : 06 : 30 • Last : 22 : 20
Operation Interval	50~60 min
Duration	approximately 1 hour
Route Guide	Airport – Halla Hospital – Donggwang Transfer Stop – Jungmun Tourist Complex Entrance – Hotel (Grand Josun Jeju, Parnas Hotel, Shilla Hotel, Suites Hotel, Bloom Hotel, Lotte Hotel, Kensington Resort, CS Hotel) – Jeju International Convention Center (ICC JEJU) – Jeju World Cup Stadium – Paradise Hotel – Seogwipo KAL Hotel
Transport Company ContactInformation	Samyeong Transportation 064-713-7000
Bus operator website	https://bus.jeju.go.kr/publicTrafficInformation/generalBusSchedule

Route title	601
Get on/off here	Limousine Stop is in front of Gate 5
Fare	One-way (adult) KRW 4,500 from the airport to ICC JEJU
First/Last Bus	• Airport → Jeju International Convention Center (ICC JEJU) First: 06 : 00 • Last : 21 : 02
Operation Interval	50~60 min
Duration	approximately 1 hour
Route Guide	Airport – Halla Hospital – Donggwang Transfer Stop – Jungmun Tourist Complex Entrance – Hotel (Grand Josun Jeju, Parnas Hotel, Shilla Hotel, Suites Hotel, Bloom Hotel, Lotte Hotel, Kensington Resort, CS Hotel) – Jeju International Convention Center (ICC JEJU)
Transport Company ContactInformation	Samyeong Transportation 064-713-7000
Bus operator website	https://bus.jeju.go.kr/publicTrafficInformation/generalBusSchedule

[Jeju Airport → ICC] Option 2. Taxi

After you exit Gate of Jeju Airport, there is a taxi stand between gates and parking lot. It takes approximately 40–50 minutes by taxi, and the fare will be KRW 35,000 to ride 41km. The taxi fee is charged by a taximeter and most Korean taxis are equipped with a credit card machine. Korean Currency can be taken only if you make a payment by cash. Please refer to the taxi stand location and more information below.

• Taxi Stand Location



Time	Approximately 40–50 minutes	Fare	Approximately KRW 35,000
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[Korean] 안녕하세요, 기사님. 제주ICC로 데려다 주시면 감사하겠습니다.
(주소 : 제주 서귀포시 중문관광로 224, 제주ICC)

7. General Information

Major foreign currencies can be exchanged at banks, hotels, and airports. Major international credit cards are widely accepted throughout Korea.

Bills			
			
50,000 won (oman won)	10,000 won (man won)	5,000 won (ocheon won)	1,000 won (cheon won)
Coins			
			
500 won (obaek won)	100 won (baek won)	50 won (osip won)	10 won (sip won)



ATM

Travelers who carry internationally recognized credit cards can get a cash advance in Korea Won from Automated Teller Machines (ATMs) installed at airports, major hotels, department stores, subway stations and tourist attractions. ATMs are in operation 24 hours a day. Most large stores, hotels and restaurants in Korea accept major international credit cards. However it is advisable to carry some cash, since many smaller establishments and stores are unlikely to accept credit cards.

TIME

When Indicating Korea Time: Present Time (GMT+9) / No daylight savings time 11:58:55

Cell Phone & SIM Card

You may rent a cell phone at the Incheon International Airport. Users can rent a handset and pay rental and call charges upon returning the phone. Applicants require identification, credit card, and a service contract (available at the booth).

International Calls

International dialing code in Incheon, Korea is +82-32 (Area code). Please omit (0) when dialing from overseas.

Tip & Tax

!TIP Tipping is not a regular practice in Korea. Service charges are included in your bill for rooms, meals and other services at hotels and upscale restaurants. Koreans occasionally do tip when they are especially pleased with the service they receive.

!TIP Visitors can receive a refund on a receipt for a minimum purchase of KRW 50,000 (around US\$52). To receive this refund, present refund receipts with the purchased goods at the customs desk at the Incheon International Airport when departing. These receipts can be cashed in at the Cash Refund Office in front of the Airport Duty Free Shop.

Business Hours

Government office hours are usually from 9:00 to 18:00 on weekdays. Banks are open from 9:00 to 16:00 on weekdays. Most stores are open every day from 10:30 to 20:00, including Sundays.

Electricity

The standard electricity supply is 220 volts AC/60 cycles. Most hotels may provide outlet converters for 110 and 220 volts. Participants are recommended to check with the hotel beforehand.

Emergency Numbers

1339 : Medical Emergency **119** : Emergencies for Fire, Rescue & Hospital Services
112 : Police **129** : First Aid Services



IX.

Author Index



IX. Author Index

Last Name	First Name	Presentation Code
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A

Abdelkarem	Khaled	FrA1-3
Abdullah	Ameer	TuA2-2
Afonso	Gustavo	TuA1-5
Ahn	Sang Hyeon	TuP-7
Ahn	Sang Hyeon	TuP-17
Aidam	R.	TuA1-2
Akaike	Ryota	WeA2-4
Akaike	Ryota	WeA2-5
Akaike	Ryota	WeP-35
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Badura	Mikołaj	WeP-10
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Barbier	F.	MoB2-1



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Beaudoin	Grégoire	ThB1-2
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Berger	Christoph	WeB2-2
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Biswas	Dhrubesh	WeB1-3
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Bläsing	Jürgen	TuA2-4
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Bourras	M.	TuA3-3
Božek	R.	TuA3-7
Brendel	M.	MoB3-1
Breuer	S.	MoB3-1
Breuer	S.	TuB2-6
Bria	T.	TuA1-1
Brunner	F.	TuB2-6
Buckley	J.	WeB3-1
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Cha	An-Na	TuP-7
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Charles	M.	WeB3-4
Chatterjee	Abhishek	FrB1-6
Chaumont	A.	WeB3-4
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Chen	Yao	MoA2-6
Chen	Yi-An	TuP-18
Chen	Li	WeB1-4
Chen	You-Jia	WeB2-5
Chen	Chen	MoA2-4
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Cheng	Anda	WeP-13
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Cho	Yunjung	TuP-3
Cho	Yunjung	TuP-4
Cho	Dong Hyun	TuP-10
Cho	Hyogeun	ThA1-5
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Cho	Yong-Hoon	WeP-4
Cho	Yong-Hoon	WeP-12
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Cho	Yong-Hoon	WeP-24
Cho	H.K.	WeB1-1
Choi	Joonghoon	MoA2-2

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Choi	Joonghoon	TuP-10
Choi	Joonghoon	TuP-29
Choi	Joonghoon	WeP-20
Choi	Joonghoon	WeP-21
Choi	Joonghoon	WeP-26
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Choi	SeongCheol	MoB1-3
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Choi	Daegwang	MoA3-7
Choi	Hak-Jong	TuP-29
Choi	Junyoung	MoA1-3
Choi	Si-Young	MoA1-3
Choi	Hak-Jong	WeP-21
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Chung	Roy. B.	MoA2-3
Chung	Tae-Hoon	TuP-27
Chung	Tae-Hoon	WeP-19
Čížek	Jakub	ThB1-4
Colavecchi	Luca	MoA3-1
Combré	S.	TuA1-3
Cooper	D.	MoB2-1
Cordier	Y.	WeB3-1
Cornet	Charles	ThB1-2
Cortez	Patsy A Miranda	WeA3-3
Czernecki	Robert	MoA2-5
Czyszanowski	Tomasz	TuB1-5
Czyszanowski	Tomasz	WeP-25



Last Name	First Name	Presentation Code
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Czyszanowski	Tomasz	WeP-10
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Dąbrowska	A. K.	TuA3-7
Daccord	G.	TuA1-1
Dadgar	Armin	TuA2-4
Dadgar	Armin	TuB3-2
Dadgar	Armin	WeB2-2
Dadgar	Armin	ThB1-3
Damen	H.	WeB2-3
Damilano	B.	WeB2-3
Danbata	H.	MoB1-1
Darakchieva	Vanya	WeA1-1
Darwish	A.	WeP-39
Datta	Sanchali	MoB3-3
Davy	N.	TuA1-1
Dawidowski	Wojciech	TuB1-5
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De Maeyer	Michiel	TuA2-6
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De O. Lorenzi	Jéssica	WeP-6
De Rossi	A.	TuA1-3
De Santi	C.	WeB1-1
Decobert	Jean	TuA1-5
Decobert	J.	TuA1-1
Decobert	J.	TuA1-6
Delorme	O.	TuA1-1
Detchprohm	Theeradetch	TuB3-4
Detchprohm	Theeradetch	WeB1-3
Dhora	Andri	WeA1-1
Dimroth	F.	TuB3-6
Dolgashev	Alexandra	TuB3-4
Dolgashev	Alexandra V.	WeB1-3
Doron	M.	TuA1-2
Dreyer	Niklas	WeB1-5
Dreyer	Niklas	ThB1-3
Duarte	Teresa	MoB1-2

Last Name	First Name	Presentation Code
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Dupont	F.	WeA2-6
Dupuis	Russell D.	TuB3-4
Dupuis	Russell D.	WeB1-3
Durand	Christophe	FrA1-1
Dussaigne	A.	MoB2-1
Dussaigne	A.	WeA2-6
Dussaigne	A.	WeB2-3

E

Eaton	L.	MoA3-4
Edgar	J.H.	TuA3-7
Edwards	P.	WeB1-1
Einfeldt	S.	WeB1-1
Ekielski	Marek	TuB1-5
El Amrani	M.	WeB3-1
El Rammouz	H.	WeB3-1
El Rammouz	H.	WeB3-4
Elias	Antoine	TuA1-5
Elias	A.	TuA1-1
Eom	Ha-Neul	WeP-14
Escanciano	Lidia	MoA3-5
Escanciano	Lidia	MoA3-6
Eun	Seo-Gyeong	TuP-33
Ewa	Grzanka	MoA2-5

F

Fan	Wei	WeP-41
Fedeli	F.	MoB2-1
Feng	M.	MoB1-1
Findling	Nathaniel	ThB1-2
Fortin	Sarah	WeA3-5
Fortín	Rubén	MoA3-5
Fortunato	F.	TuA1-1
Foucher	Romain	MoA3-5
Fournel	F.	TuA1-1
Fowan	D. P.	WeB2-3



Last Name	First Name	Presentation Code
Frentrup	M.	FrB1-6
Fujimoto	Kai	WeP-1
Fujimoto	Kohei	WeB1-5
Funato	Mitsuru	WeB2-1
Furtak	B.	TuA3-7
Furuhashi	Itsuki	TuB2-3

G

Gaffin	Neal	WeP-41
Gajjela	Raja S.R.	TuA2-3
Galić	Aleksa	WeP-37
Gan	Lin	WeP-13
Gao	Xin	TuB3-1
García	Iván	MoA3-5
García	Iván	MoA3-6
García	Glen Isaac Maciel	WeA3-3
Garg	Gaurang	TuB1-4
Gautheron-Bernard	Rozenn	ThB1-2
Gautier	Simon	MoA1-2
Gębski	Marcin	TuB1-5
Gębski	Marcin	WeP-10
Gębski	Marcin	WeP-25
Gérard	B.	TuA1-3
Ghyselen	B.	TuA1-1
Gil	B.	TuA3-7
Gil	Bernard	MoA1-3
Głowadzka	Weronika	TuB1-5
Gocalinska	Agnieszka	MoA3-1
Gogova	Daniela	WeA1-1
Gokhale	Maheshwar	MoB3-2
Gokhale	Maheshwar	MoB3-3
Goto	Ken	WeA1-1
Grabowski	Mikolaj	MoA2-5
Greczmiel	Luca	ThB1-3
Grenier	Vincent	FrA1-1

Last Name	First Name	Presentation Code
Grisard	A.	TuA1-3
Grossmann	Fabian	WeB2-2
Groven	Benjamin	TuA3-1
Grzanka	Szymon	TuB1-6
Gu	Tae-Hun	TuP-14
Gu	Zhekai	WeP-44
Guillemin	T.	WeB3-1
Günkel	Robin	TuA3-5
Guo	Wei	WeB1-4
Guo	Yucheng	TuB3-1
Guo	Yanan	WeP-44
Gustafsson	Anders	MoB2-5
Gustafsson	Anders	TuB3-7
Guttmann	M.	WeB1-1
Guy	K.	WeA2-6

H

Ha	Jun-Seok	TuP-2
Ha	Jun-Seok	TuP-7
Ha	Jun-Seok	TuP-17
Ha	Jun-Seok	TuP-32
Ha	Jun-Seok	WeP-38
Haberland	K.	TuA1-6
Hachimiya	Doma	WeP-1
Hachimiya	Doma	WeP-2
Haertelt	M.	TuA1-2
Hagedorn	S.	WeB1-1
Hájek	František	ThB1-4
Han	Dong-Pyo	WeP-46
Han	Yanjun	WeP-13
Han	Yu	MoA2-6
Han	Young-Hun	WeP-5
Han	Young-Hun	WeP-17
Han	Young-Hun	WeP-27
Han	Young-Hun	WeP-29
Han	Young-Hun	WeP-30
Hao	Yue	TuB2-4



Last Name	First Name	Presentation Code
Hao	Zhibiao	WeP-13
Hao	Yue	WeP-42
Harding	B.	FrB1-6
Harouri	A.	TuA1-3
Hatanaka	Soma	MoB3-5
Haust	Johannes	TuA2-6
Hayashiuchi	A.	MoB1-1
Heffernan	J.	MoA3-4
Heffernan	Jon	TuA2-3
Helmers	H.	WeP-39
Heo	Jaejin	WeP-7
Heo	Jaejin	WeP-8
Heo	Jaejin	ThA1-2
Heo	Jaejin	ThA1-5
Heo	Jiwon	WeP-38
Heurlin	Magnus	MoB2-5
Hilt	O.	TuB2-6
Hino	M.	TuB2-2
Hino	M.	FrB1-3
Hino	Maui	WeA2-2
Hirama	K.	MoB1-1
Hirata	N.	MoB1-1
Hirayama	Hideki	WeB1-5
Hiroki	Masanobu	WeA2-1
Hiroki	M.	MoB1-1
Hirschmann	Eric	ThB1-4
Ho	Jeong	TuA2-2
Hoffmann	Felix	MoB1-2
Holewa	Paweł	TuP-28
Honda	Y.	FrB1-3
Honda	Y.	FrB1-4
Honda	Yoshio	FrB1-5
Hong	Young Joon	MoA2-1
Hong	Young Joon	MoA2-2
Hong	Young Joon	TuP-8
Hong	Young Joon	TuP-10
Hong	Young Joon	TuP-29
Hong	Young Joon	WeP-20

Last Name	First Name	Presentation Code
Hong	Young Joon	WeP-21
Hong	Young Joon	WeP-26
Hong	Min-Ki	WeP-5
Hong	Min-Ki	WeP-17
Hong	Min-Ki	WeP-27
Hong	Min-Ki	WeP-29
Hong	Min-Ki	WeP-30
Hong	Soon-Ku	ThB1-5
Hong	Ui-Seong	WeP-14
Höpfner	J.	WeB1-1
Hörich	Florian	TuB3-2
Hospodková	Alice	ThB1-4
Hrytsak	Roman	MoA2-5
Hsieh	Pei-Shan	WeB2-6
Hsieh	Chuang-Yu	WeB2-5
Hsu	Lung-Hsing	TuP-36
Hu	Li-Sheng	WeB2-5
Huang	Xiaoying	TuB1-4
Huang	Chia-Yen	WeB2-5
Huang	Yi-Ru	MoB2-2
Huang	Huai-Chin	WeB2-5
Huang	Kai	TuB3-7
Hubáček	Tomáš	ThB1-4
Hung	Chih-Chang	TuP-36
Hung	Hsing-Ting	WeB2-5
Hwang	Hae Seong	WeA1-2
Hwang	Ilji	WeP-46
Hwang	Young Soo	WeA1-6
Hwang	Inyong	MoA1-3
Hwang	Wan-Sik	TuP-2
I		
Iida	Daisuke	MoB3-6
Iida	Daisuke	FrB1-2
Ikeda	Kazuhisa	WeA2-3
Ikejiri	Keitaro	FrB1-2
Ikenaga	Kazutada	FrB1-2



Last Name	First Name	Presentation Code
Im	Semi	MoA1-3
Im	Semi	TuA3-2
Im	Semi	TuA3-4
Im	Semi	TuA3-6
Im	Semi	TuP-5
Im	Semi	TuP-15
Inoue	Y.	FrB1-3
Inoue	Y.	FrB1-4
Inoue	Yoku	FrB1-5
Ishitani	Yoshihiro	WeP-35
Iwamitsu	Kazunori	MoB3-5
Iwański	J.	TuA3-7
Iwaya	Motoaki	TuB1-1
Iwaya	Motoaki	WeB1-2
Iwayama	Sho	WeB1-2
Izquierdo	E.	TuA1-1

J

Jacopin	Gwénolé	FrA1-1
Jagadish	Chennupati	TuB1-4
Jaloustre	Lucas	FrA1-1
Jang	Ji Hoon	TuP-35
Jang	JongJin	MoB1-3
Jang	Ki Jae	TuP-35
Jang	Sam-Seok	WeP-19
Jang	Samseok	TuP-27
Jena	Debdeep	FrB1-1
Jeon	Dae-Woo	TuP-2
Jeon	Dae-Woo	WeA1-5
Jeon	Jihwan	TuP-13
Jeon	Taeyoung	TuP-4
Jeong	Changwook	TuA3-6
Jeong	Joocheol	WeP-7
Jeong	Joocheol	WeP-8
Jeong	Joocheol	WeP-16
Jeong	Joocheol	ThA1-2
Jeong	Joocheol	ThA1-5

JEONG	Seong-Min	TuP-6
Jeong	Woo-Lim	WeP-15
Jetter	M.	MoA3-3
Jetter	M.	TuA2-5
Jetter	Michael	TuA2-1
Ji	Changuk	MoA1-3
Ji	Changuk	TuA3-2
Ji	Changuk	TuA3-4
Ji	Changuk	TuA3-6
Ji	Changuk	TuP-5
Ji	Changuk	TuP-15
Jiang	Zixian	TuB3-5
Jiang	Zixian	WeA3-3
Jiang	Zixian	WeB3-2
Jiang	Zixian	WeB3-5
Jiang	Zixian	WeP-3
Jo	Hyeon-Bhin	WeP-23
Jo	Hyeon-bhin	WeP-28
Jo	Mingoo	WeP-7
Jo	Mingoo	WeP-8
Jo	Mingoo	WeP-16
Jo	Mingoo	ThA1-2
Jo	Mingoo	ThA1-5
Joos	Raphael	TuA2-1
Jose	Juwana	TuA2-4
Ju	Jae-Hong	TuP-33
Ju	Inseok	WeP-21
Ju	Jin-woo	TuP-32
Jung	Jae Min	TuP-21
Jung	Jaeheon	WeA1-2
Jung	Jaeheon	WeA1-6
Jung	Sanghoon	TuP-19
Jung	Sanghoon	TuP-20
Jung	Sanghoon	WeP-32
Jung	Sanghoon	WeP-33
Jung	YuSup	TuP-16
Jung	Dong-Geon	WeP-34
Jung	Hyundon	ThB1-5



Last Name	First Name	Presentation Code
Jung	Kwang-Hee	TuP-12
Jung	Sang-Hoon	WeP-34
Juska	Gediminas	MoA3-1

K

Kaltsounis	T.	WeB3-1
Kamiyama	Satoshi	TuB1-1
Kamiyama	Satoshi	WeB1-2
Kang	Byoung-ho	TuP-19
Kang	Byoung-ho	TuP-20
Kang	Byoung-ho	WeP-32
Kang	Byoung-ho	WeP-33
Kang	Byoung-Ho	WeP-34
KANG	Chang-Mo	TuP-6
Kang	Chang-Mo	WeP-15
Kang	Chang-Mo	WeP-22
Kang	Ha Young	WeA1-6
Kang	Jin-Ki	TuP-12
Kang	Jung Hoon	TuP-35
Kang	Kibum	TuP-10
Kang	Seongmin	WeP-28
Kang	TaiYoung	TuP-16
Kao	Chia-Yun	MoB2-2
Kappers	M. J.	FrB1-6
Kasukawa	Akihiko	WeA3-4
Katayama	Ryuji	WeA2-3
Kavanagh	Karen L.	WeA3-5
Kawabata	Rudy M. S.	WeP-6
Kaynar	Emine	WeB2-2
Ke	WenCheng	TuP-18
Ke	WenCheng	TuP-34
Keil	R.	TuA1-2
Khan	M. Ajmal	WeB1-5
Kijaszek	Wojciech	WeP-10
Kim	Baul	WeP-24
Kim	Chaewon	TuP-24
Kim	Chang Gyoun	TuP-35

Last Name	First Name	Presentation Code
Kim	Chang Soo	MoA2-2
Kim	Chang Soo	TuP-29
Kim	Chang Soo	WeP-21
Kim	Chang Soo	WeP-26
Kim	Cyan	WeA3-5
Kim	Dayoung	TuB3-3
Kim	Da-Young	TuP-27
Kim	Da-Young	WeP-19
Kim	Dongseok	ThA1-5
Kim	Dong-Seok	TuA3-6
Kim	Dongwan	TuB3-3
Kim	Geon-Yeong	WeB2-4
Kim	Geon-Yeong	WeP-14
Kim	Hyemin	WeP-18
Kim	Hyeong-Yun	WeA1-5
Kim	Hyunjun	TuP-22
Kim	Hyunjun	TuP-25
Kim	Imhwan	TuP-35
Kim	Jaesun	WeB3-3
Kim	Jaewon	MoA3-7
Kim	Jawon	MoA1-3
Kim	Jawon	TuA3-2
Kim	Jawon	TuA3-4
Kim	Jawon	TuA3-6
Kim	Jawon	TuP-5
Kim	Jawon	TuP-15
Kim	Jeongho	WeP-12
Kim	Jeongwoon	WeP-15
Kim	Jin Seok	TuP-35
Kim	Jin-Soo	WeP-15
Kim	Jinsup	WeP-28
Kim	Jin-sup	WeP-23
Kim	Jiye	MoA1-3
Kim	Jiye	TuA3-6
Kim	Jong Kyu	MoA1-3
Kim	Jong Kyu	TuA3-2
Kim	Jong Kyu	TuA3-4
Kim	Jong Kyu	TuA3-6



Last Name	First Name	Presentation Code
Kim	Jong Kyu	TuP-5
Kim	Jong Kyu	TuP-15
Kim	Jongwoo	TuP-29
Kim	Jung-Gon	TuP-12
Kim	Minho	WeA1-1
Kim	Minji	ThA1-5
Kim	Minkyong	TuB3-3
Kim	Minyeong	WeP-7
Kim	Minyeong	WeP-8
Kim	Minyeong	WeP-16
Kim	Minyeong	ThA1-2
Kim	Minyeong	ThA1-5
Kim	Myung Sik	TuP-7
Kim	Myung Sik	TuP-17
Kim	Saewan	TuP-20
Kim	Saewan	WeP-32
Kim	Saewan	WeP-33
Kim	Sae-Wan	TuP-19
Kim	Sae-Wan	WeP-34
Kim	SangHun	TuP-16
Kim	SeungSu	TuP-22
Kim	Seyoung	MoA1-3
Kim	Soohyun	TuP-8
Kim	Su Jin	TuP-10
Kim	Sung-Un	WeB2-4
Kim	Sung-Un	WeP-14
Kim	Sung-Un	WeP-45
Kim	Sung-Un	TuP-33
Kim	Sung-Un	FrA1-4
Kim	Sung-Un	FrA1-5
Kim	Sunjae	TuP-2
Kim	Yoon Seok	WeP-29
Kim	Yoon-Seok	WeP-5
Kimoto	T.	MoB1-1
Kirste	L.	TuA1-2
Kirste	Lutz	MoB1-2
Kitamura	Y.	MoB1-1
Klein	C.	TuB3-6

Last Name	First Name	Presentation Code
Klitzke	M.	TuB3-6
Kneissl	M.	WeB1-1
Ko	Young-Ho	WeP-18
Kobayashi	Atsushi	WeA2-3
Koenraad	Paul M.	TuA2-3
Kokubo	E.	FrB1-3
Kokubo	E.	FrB1-4
Kokubo	Eito	FrB1-5
Kolatschek	Sascha	TuA2-1
Kolbe	T.	WeB1-1
Kořkowski	Walery	TuP-37
Koo	Do Hyoung	TuP-35
Koo	Yoonmo	TuP-21
Korti	Mokhtar	TuA1-5
Kotani	J.	TuB2-2
Kotani	Junji	WeA2-2
Krizhanovskii	D. N.	MoA3-4
Kröner	Marcel	TuA2-6
Kruszewski	Piotr	TuB2-5
Krysko	Marcin	TuB2-5
Kuball	Martin	TuB2-3
Kucharski	Robert	TuB2-5
Kudo	R.	FrB1-3
Kudo	R.	FrB1-4
Kudo	Ryohei	FrB1-5
Kuldová	Karla	ThB1-4
Kulkarni	Mandar	MoB2-4
Kunert	Bernardette	TuA2-6
Kuo	Hao-Chung	TuP-36
Kurai	S.	MoB1-1
Kurek	Justyna	TuP-37
Kusano	Shuji	ThB1-6
Kusch	G.	WeB1-1
Kusch	G.	FrB1-6
Kwak	Hoe-Min	WeP-15
Kwak	Hyunjeong	MoA1-3
Kwak	Jinsung	WeP-31
Kwak	JoonSeop	WeP-15



Last Name	First Name	Presentation Code
Kwon	Jaeyong	WeP-15
Kwon	Jaeyong	WeP-22
Kwon	Jin-Beom	WeP-34
Kwon	Kyungwu	TuP-13
Kyoung	SinSu	TuP-16

L

Lachowski	Artur	MoA2-5
Lackner	D.	TuB3-6
Lackner	D.	WeP-39
Lafossas	M.	WeB3-1
Lafossas	M.	WeB3-4
Lähnemann	J.	WeB1-1
Langlotz	Nils	TuA3-5
Largeau	Ludovic	ThB1-2
Lavate	Sneha S	FrA1-4
Le Corre	B.	TuA1-3
Le Gratiot	L.	TuA1-3
Lee	Changsug	TuB3-3
Lee	Cheul-Ro	WeB2-4
Lee	Cheul-Ro	WeP-45
Lee	Choong Ki (Daniel)	ThB1-6
Lee	Chul-Ho	TuP-35
Lee	Daewon	TuP-21
Lee	Daewon	TuP-22
Lee	Daewon	TuP-23
Lee	Daewon	TuP-24
Lee	Daewon	TuP-25
Lee	Dong Hyun	TuP-35
Lee	Dong-Jin	TuP-12
Lee	Dong-Seon	WeP-15
Lee	Dong-Seon	WeP-22
Lee	Eun-Seo	TuP-12
Lee	Gieop	TuP-2
Lee	Gieop	TuP-7
Lee	Gieop	TuP-17

Last Name	First Name	Presentation Code
Lee	Gyeong Ryul	MoA2-3
Lee	Hae-Yong	TuP-1
Lee	Hao	WeB2-5
Lee	Hyeondong	WeP-15
Lee	Hyeonwoo	TuA3-6
Lee	Hyun Seok	TuP-10
Lee	Jaesung	TuP-19
Lee	Jaesung	TuP-20
Lee	Jaesung	WeP-32
Lee	Jaesung	WeP-33
Lee	Jae-Sung	WeP-34
Lee	Je-Sung	WeP-15
Lee	Je-Sung	WeP-22
Lee	Jubin	TuP-23
Lee	Jun Woo	TuP-10
Lee	Jungho	TuA3-6
Lee	Min-Seok	TuP-33
Lee	Min-Seok	WeB2-4
Lee	Min-Seok	WeP-45
Lee	Min-Seok	FrA1-4
Lee	Min-Seok	FrA1-5
Lee	S. L.	WeA3-4
Lee	Sang Jun	TuB3-3
Lee	Seong-gwang	TuP-35
Lee	Seung Hoon	MoA2-4
Lee	Seung Hyeok	WeP-22
Lee	Sung-Nam	WeP-5
Lee	Sung-Nam	WeP-29
Lee	Wanghoon	TuP-20
Lee	Wanghoon	WeP-32
Lee	Wanghoon	WeP-33
Lee	Wang-Hoon	TuP-19
Lee	Wang-Hoon	WeP-34
Lee	Wonchan	TuP-3
Lee	Wonchan	TuP-4
Lee	Won-Jae	TuP-12
Léger	Y.	TuA1-3
Leist	Jon	WeP-41



Last Name	First Name	Presentation Code
Lem	Olivier Lee	TuB1-4
	Cheong	
Leone	Stefano	MoB1-2
Leone	Stefano	FrB1-1
Leszczynski	Michal	MoA2-5
Lévy	F.	MoB2-1
Li	Chenxue	TuP-31
Li	Hongjian	TuB3-7
Li	Hongtao	WeP-13
Li	J.	TuA3-7
Li	JinChai	TuB3-7
Li	Jinmin	WeP-44
Li	Panpan	TuB3-7
Li	Ting-Chuan	TuP-36
Li	Xiaohang	TuB2-1
Li	Xiaohang	TuB3-5
Li	Xiaohang	WeA1-3
Li	Xiaohang	WeA3-3
Li	Xiaohang	WeB3-2
Li	Xiaohang	WeB3-5
Li	Xiaohang	WeB3-6
Li	Xiaohang	WeP-3
Li	Xiaohang	ThA1-1
Li	Xiaohang	ThA1-4
Li	Yun-Li	MoB2-2
Liao	Che-Hao	WeA3-3
Liedke	Maciej Oskar	ThB1-4
Lim	Bong Gi	TuP-35
Lim	Chaehui	TuP-4
Lim	Hyunchul	WeP-17
Lim	Hyunchul	WeP-27
Lim	Hyunchul	WeP-29
Lim	Hyunchul	WeP-30
Lim	Hyun-Chul	WeP-5
Lim	Hyungjun	TuP-29
LIM	Jae-Hyeok	TuP-6
Lim	Jae-Hyuk	TuP-14
Lim	Jongsun	TuP-35

Last Name	First Name	Presentation Code
Lim	Mi-Rim	TuP-14
Lim	Seungyoung	WeB3-3
Lim	Youngyoon	TuP-29
Lin	Ching-Liang	MoB2-2
Lister	David A.	WeA3-5
Liu	Bin	TuP-31
Liu	Bin	WeA3-1
Liu	Chunyu	TuB3-7
Liu	Fang	TuB3-1
Liu	Hongyu	WeB1-4
Liu	Tingang	TuB3-5
Liu	Tingang	WeA3-3
Liu	Tingang	WeB3-2
Liu	Tingang	ThA1-1
Liu	Tingang	ThA1-4
Liu	Xinyu	WeP-43
Liu	Zhiyuan	TuB3-5
Liu	Zhiyuan	WeB3-2
Liu	Zhongfan	TuB3-1
Loeto	K.	WeB1-1
Löfström	Nathanael	MoB2-5
Lovett	S.	MoA3-4
Łozińska	Adriana	TuB1-5
Łozińska	Adriana	WeP-10
Lu	Tien-Chang	WeB2-5
Lu	Weifang	TuB3-7
Ludwiczak	K.	TuA3-7
Lunghi	Ludovica	TuP-26
Luo	Yi	WeP-13

M

M'Qaddem ¹	Z.	WeB3-1
Ma	Bei	WeP-35
Maaßdorf	A.	MoB3-1
Madera	Christian C. Ruiz	TuP-28
Maeda	Y.	FrB1-3
Maegdefessel	Sven	MoB1-2



Last Name	First Name	Presentation Code
Mahadik	Shivraj	FrA1-5
Mainali	Ganesh	WeA1-3
Makabe	I.	TuB2-2
Makabe	Isao	WeA2-2
Makino	T.	FrB1-4
Makiyama	K.	TuB2-2
Makiyama	Kozo	WeA2-2
Maksymiuk	P.	TuA3-7
Mane	Pratik	WeP-38
Marciniak	Magdalena	TuB1-5
Marciniak	Magdalena	WeP-10
Marciniak	Magdalena	WeP-25
Marona	Lucja	TuB1-6
Martin	R.W.	WeB1-1
Martín	Pablo	MoA3-5
Masante	C.	WeB3-4
Matsuda	Yoshinobu	WeB2-1
Mei	Bingchu	WeA3-2
Meneghesso	G.	WeB1-1
Meneghini	M.	WeB1-1
Menner	Hanspeter	MoB1-2
Merkert	P.	TuA1-2
Messaoudène	S.	TuA1-2
Meyer	T.	TuA1-2
Micha	Daniel N.	WeP-6
Michalowski	Pawel P.	MoA3-1
Michler	P.	MoA3-3
Michler	P.	TuA2-5
Michler	Peter	TuA2-1
Millotte	M.	TuA1-3
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Dongwan	Kim	Korea Research Institute of Standards and Science	WeA1	Gallium Oxides	July 15 (Wed.), 2026	10:25-12:10	Room A (Baekrok Hall A, 1F)



First name	Last name	Affiliation	Session Code	Session Title	Session Date	Session Time	Session Room
David	Lackner	Fraunhofer Institut für Solare Energiesysteme ISE	MoA3	Arsenides	July 13 (Mon.), 2026	16:05–18:05	Room A (Baekrok Hall A, 1F)
Xiaohang	Li	King Abdullah University of Science and Technology	MoB1	Nitrides for Electronics – I	July 13 (Mon.), 2026	11:15–12:30	Room B (Baekrok Hall B, 1F)
Andre	Maaßdorf	Ferdinand-Braun-Institute	TuB1	Lasers	July 14 (Tue.), 2026	08:30–10:15	Room B (Baekrok Hall B, 1F)
Seokho	Moon	Ajou University	WeA1	Gallium Oxides	July 15 (Wed.), 2026	10:25–12:10	Room A (Baekrok Hall A, 1F)
Okhyun	Nam	Tech University of Korea	WeB3	Nitrides for Electronics – III	July 15 (Wed.), 2026	15:35–17:05	Room B (Baekrok Hall B, 1F)
Narihito	Okada	Yamaguchi University	TuB2	Nitrides for Electronics – II	July 14 (Tue.), 2026	10:35–12:20	Room B (Baekrok Hall B, 1F)
Ji-Hyeon	Park	Korea Institute of Ceramic Engineering and Technology	FrB1	Emerging Nitrides	July 17 (Fri.), 2026	10:20–12:05	Room B (Baekrok Hall B, 1F)
Emanuele	Pelucchi	Tyndall National Institute	TuA1	Phosphides	July 14 (Tue.), 2026	08:30–10:15	Room A (Baekrok Hall A, 1F)
Markus	Pristovsek	Nagoya University	MoB1	Nitrides for Electronics – I	July 13 (Mon.), 2026	11:15–12:30	Room B (Baekrok Hall B, 1F)
Yong-Ho	Ra	Jeonbuk National University	WeA3	Advanced Growth Techniques – II	July 15 (Wed.), 2026	15:35–17:05	Room A (Baekrok Hall A, 1F)
Yong-Ho	Ra	Jeonbuk National University	FrA1	Nanowires	July 17 (Fri.), 2026	10:20–12:05	Room A (Baekrok Hall A, 1F)
Sang Wan	Ryu	Chonnam National University	ThA1	Al-rich AlGaIn	July 16 (Thu.), 2026	08:30–09:45	Room A (Baekrok Hall A, 1F)
Elisa Maddalena	Sala	The University of Sheffield	FrA1	Nanowires	July 17 (Fri.), 2026	10:20–12:05	Room A (Baekrok Hall A, 1F)
Lars	Samuelson	Southern University of Science and Technology	TuA2	Low-Dimensional Materials	July 14 (Tue.), 2026	10:35–12:20	Room A (Baekrok Hall A, 1F)
Byeongchan	So	Fraunhofer Institute for Applied Solid State Physics IAF	TuB2	Nitrides for Electronics – II	July 14 (Tue.), 2026	10:35–12:20	Room B (Baekrok Hall B, 1F)
Isabel	Streicher	Cornell University	WeB3	Nitrides for Electronics – III	July 15 (Wed.), 2026	15:35–17:05	Room B (Baekrok Hall B, 1F)
Zaichun	Sun	Wuhan University of Technology	TuA2	Low-Dimensional Materials	July 14 (Tue.), 2026	10:35–12:20	Room A (Baekrok Hall A, 1F)
Qian	Sun	Chinese Academy of Sciences	WeB2	Visible LEDs	July 15 (Wed.), 2026	13:30–15:15	Room B (Baekrok Hall B, 1F)
Suresh	Sundaram	Georgia Tech Europe	TuA3	2D Materials – II	July 14 (Tue.), 2026	14:00–16:00	Room A (Baekrok Hall A, 1F)
Tetsuya	Takeuchi	Meijo University	MoB3	Optical Characterization	July 13 (Mon.), 2026	16:05–17:50	Room B (Baekrok Hall B, 1F)



First name	Last name	Affiliation	Session Code	Session Title	Session Date	Session Time	Session Room
Hoe	Tan	The Australian National University	ThA1	Al-rich AlGaN	July 16 (Thu.), 2026	08:30-09:45	Room A (Baekrok Hall A, 1F)
Kerstin	Volz	Philipps-University Marburg	MoA1	2D Materials - I	July 13 (Mon.), 2026	11:15-12:30	Room A (Baekrok Hall A, 1F)
Xinqiang	Wang	Peking University	MoB2	Micro-LEDs	July 13 (Mon.), 2026	14:00-15:45	Room B (Baekrok Hall B,1F)
JunShuai	Xue	Xidian University	WeB1	UV Devices	July 15 (Wed.), 2026	10:25-12:10	Room B (Baekrok Hall B,1F)
Xiaotian	Zhang	Suzhou Laboratory	TuA3	2D Materials - II	July 14 (Tue.), 2026	14:00-16:00	Room A (Baekrok Hall A, 1F)
Zhe	Zhuang	Nanjing University	MoA2	Advanced Growth Techniques - I	July 13 (Mon.), 2026	14:00-15:45	Room A (Baekrok Hall A, 1F)

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30 min



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PORT
50 min

3 CORE STRENGTHS FOR YOUR R&D HUB

01

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- ✓ Home to Samsung Electronics HQ
- ✓ At the Heart of Korea's Largest Semiconductor Ecosystem
- ✓ Strong Synergy with Key Cities in Southern Gyeonggi:
 - Yongin (Foundry, Memory)
 - Pyeongtaek (Mega Fab Complex)
 - Icheon (Memory)



02

World-Class Talent & R&D Network



- ✓ 43,000 Professional Researchers
- ✓ 3,600 STEM Graduates Annually
- ✓ 5 Leading Universities in Suwon



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IR SESSION

**Building Korea's Next
Global Compound Semiconductor
R&D Hub in Suwon**

DATE 2026. 7. 15. (Wed)

TIME 12:10 - 12:40

LOCATION Baekrok Hall A

EVENT Lucky Draw



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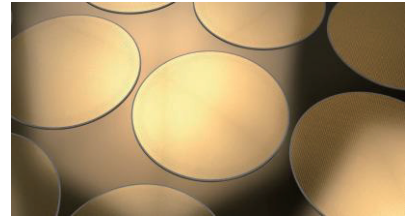
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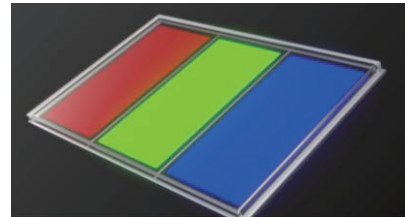
GaN Epitaxy Wafers

- RF GaN HEMT-on-SiC Epitaxy Wafer (8", 6", 4")
- Power GaN HEMT-on-Si Epitaxy Wafer (8", 6")
- LED GaN-on-Sapphire Epitaxy Wafer (6", 4")



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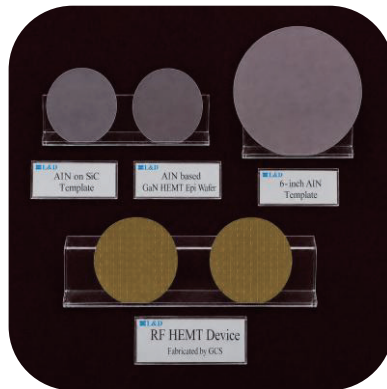
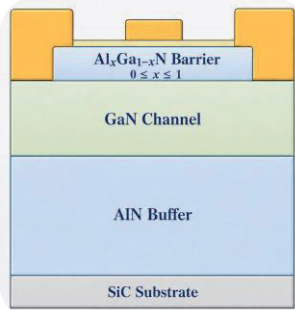
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- 4-inch GaN HEMT Epiwafers on SiC
- AlN-buffer-based HEMT Structures
- AlN and AlGaIn Barrier Epi Structures
- AlGaIn Channel HEMT Epiwafers
- 6-inch AlN Buffer Templates

⚙️ TECHNOLOGY STRENGTHS

- Proprietary MOCVD system developed in-house
- In-house AlN-buffer-based epitaxial growth
- AlN buffer and template process expertise
- Wafer-level characterization: XRD, AFM, TEM, Hall
- 4-inch production and 6-inch wafer development

💻 APPLICATIONS

- RF & Power semiconductor devices
- UVC LED and UVC sensors
- Satellite communication
- Radar and defense systems
- 5G/6G communication infrastructure

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📍 **L&D Inc. Research Institute / R&D Center**
Semiconductor Convergence Research Building, Kyungpook National University Daegu Campus, 80 Daehak-ro, Buk-gu, Daegu 41566, Republic of Korea

AIXTRON

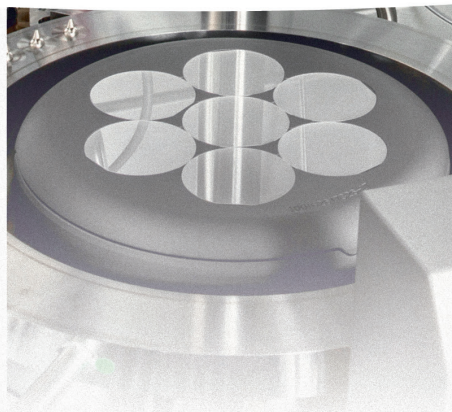
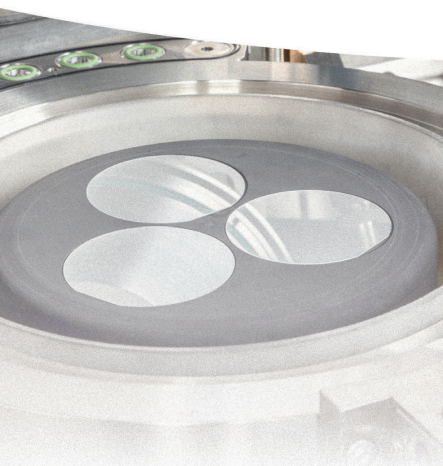
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[ICMOVPE XXII Special Session]

Compound Semiconductor Networking Reception

July 15 (Wed.)

ROOM 202(ICC JEJU, Jeju Island, Korea)

Time	Program	
15:00-16:00(60')	KANC Info Session (Individual Meeting)	
16:00-16:20(20')	Opening & Photo Time	
16:20-16:40(20')	Introduction of KANC Epi. platforms	Dr. Chuyoung Cho (KANC)
16:40-17:00(20')	MOCVD Based Next-Generation GaN Epiwafer Technologies for Power and RF Applications by WaveLord	Young-Hun Han (WaveLord)
17:00-17:20(20')	AIN-platform Technology - Present and Future	Dr. Jung-Hee Lee (L&D)
17:20-17:40(20')	8 inch GaN on Si Epiwafer and HEMT Device Manufacturing Technology and Application	Dr. Hyun-Jun Jo (A-PRO Semicon)
17:40-	Closing / Dinner	

Contact

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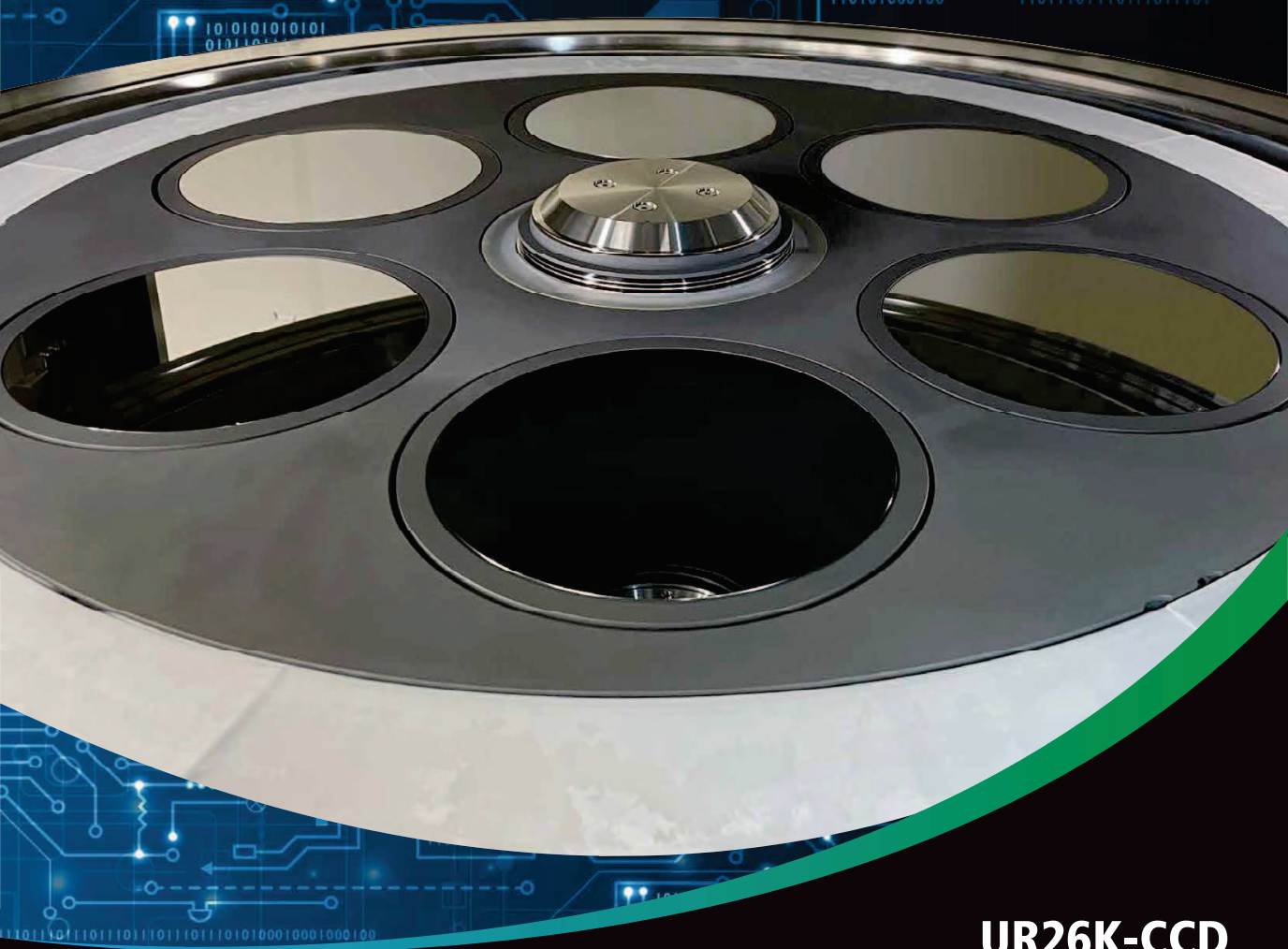
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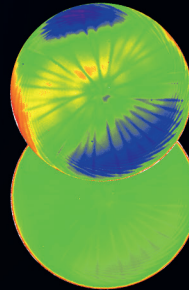
EpiX® is measuring wafers for:

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- › LEDs
- › Lasers
- › VCSELs
- ...



and anything else made of:

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- › Arsenides
- › Phosphides
- › Oxides
- › 2D-materials
- › Dielectrics
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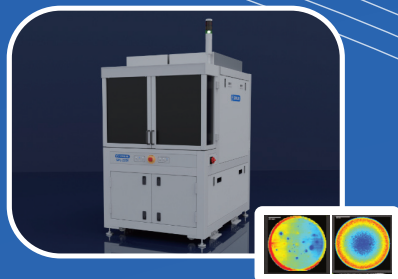
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< 0.5μm resolution · GaN/SiC
hot-spot mapping · 1,000× faster

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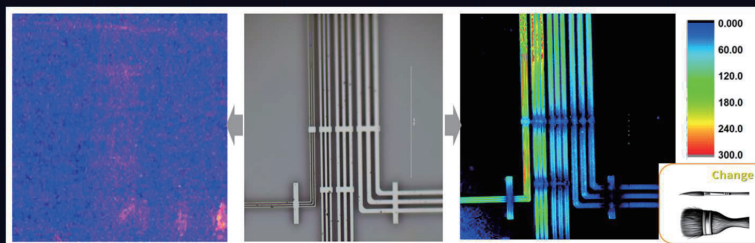
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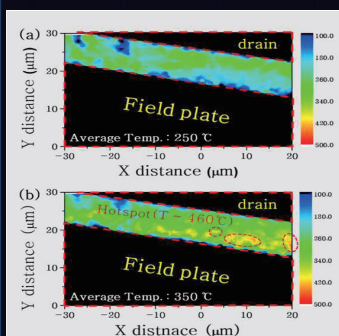
IR image

optical

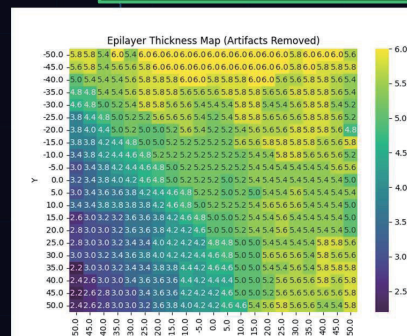
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GaN HOTSPOT THERMAL MAP · <0.5μm RES.



SiC Homoepitaxy Thickness Mapping

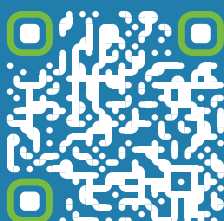


SCIENCE DRIVEN SOLUTIONS

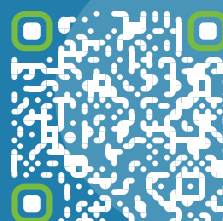
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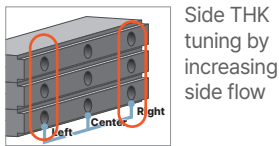
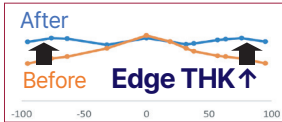
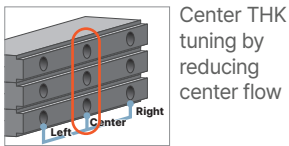
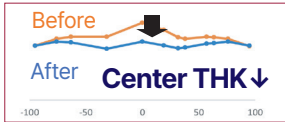


TRION Platform

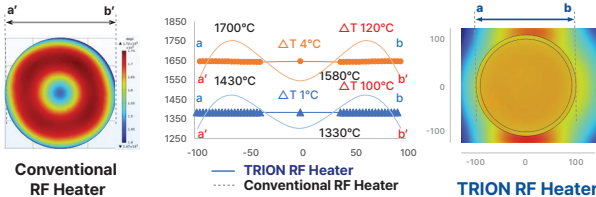


- 6/8inch single wafer
- 2-chamber cluster tool
- 1385°C RF GaN | 1650°C Power SiC
- Tunable Nozzle + T-Heater
- In-situ temperature control

Tunable Triple Pair Nozzle



T-HEATER UNIFORMITY (200mm)



RF GaN

Electrical Property & AlN Crystallinity

>2,000 cm^2/Vs
HALL MOBILITY
@ mid $\times 10^{12} \text{cm}^{-2}$

<350 Ω/sq
SHEET RESISTANCE
Rs UNIF. < 2%

<350 arcsec
XRD (102) FWHM
of AlN buffer

RF GaN Epi with AlN Buffer

AlGaN Barrier
25–30 nm

GaN Channel
250–300 nm

AlN Buffer
~2 μm , undoped
(Bow < 20 μm)

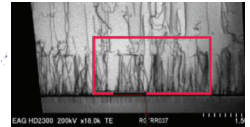
SiC substrate
on axis

CRACK-FREE AlN



OM $\times 1000$

DISLOCATION BENDING



Fast Gas-switching
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→ dislocation bending ↑
→ **low-defect**

POWER SiC

4 °C ΔT
@ 1,650 °C UNIF.

1–100 μm
EPI THICKNESS

>95 %
TUA (5 $\times$ 5)



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This research was supported by the Ministry of Education through the Basic Science Research Capacity Enhancement Project, operated by the Korea Basic Science Institute (KBSI) and the National Research Facilities & Equipment Center (NFEC)



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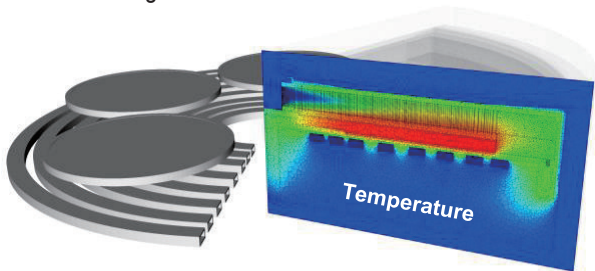
STR Simulation Software for Epitaxy and Devices

Modeling of MOVPE of Nitrides

- ▶ GaN, AlN, AlGaN and InGaN epitaxy
- ▶ Thickness and composition uniformity
- ▶ Extrinsic and intrinsic carbon doping, point defects
- ▶ Planetary, rotating disc, showerhead, and custom design reactors

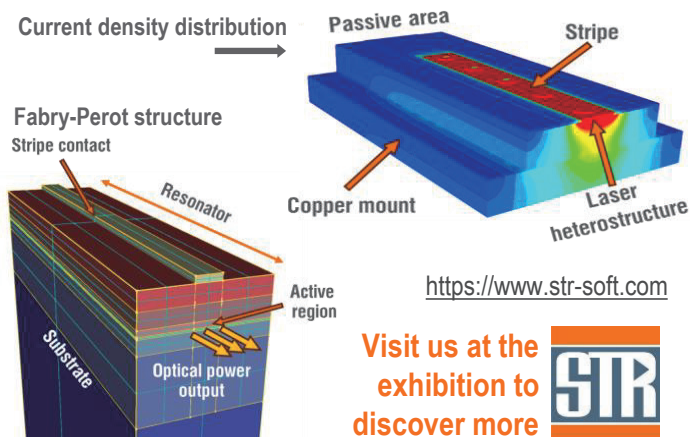
Virtual Reactor for III-Vs

- ▶ Epitaxy of GaAs - and InP-based layers
- ▶ Group III and Group V composition uniformity
- ▶ Parasitic deposition on the interior reactor parts including As and P condensation



3D modeling of LED, μ LED, and LD chips

- ▶ Current spreading and its impact on chip performance
- ▶ Self-heating (multiple mechanisms)
- ▶ Import of current-voltage characteristics from SiLENSe or parametric specification
- ▶ Lateral carrier diffusion and surface recombination
- ▶ Geometry parameterization for quick modifications



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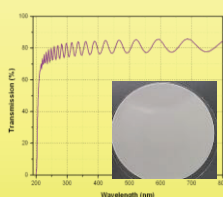


Business Roadmap

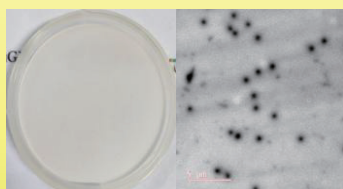
- ◆ Focus on the materials(GaN, Ga₂O₃, AlN) for Power/RF semiconductors
 - Short term: Focus on the R & BD of GaN substrate for Power/RF devices
 - Mid term: Ga₂O₃ area Epi-wafer development by Government Funding
 - Long term: R & BD of AlN substrate



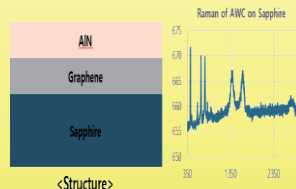
Products



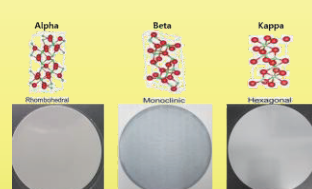
<AlN template>



<GaN wafer>



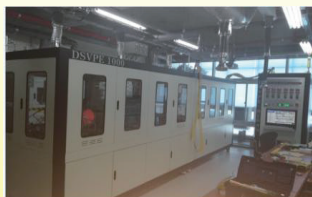
<Graphene buffer template>



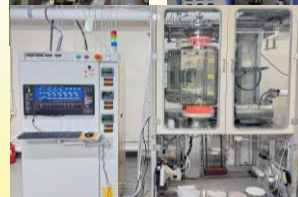
<Ga₂O₃ epi wafer>

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- ◆ Lateral and Vertical HVPE



<Lateral HVPE 2 ~ 6inch>



<Vertical HVPE 2 ~ 6inch>

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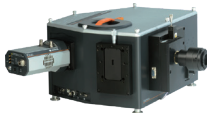
Raman/PL
Maple III



Time-resolved Confocal Microscopy
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iXon Ultra EMCCD

Korea's leading technology company Beyond the Silicon Semiconductor



POWERCUBESEMI, INC.
Potential · Convergence · Smart



Main Product Type

Si SJ MOSFET



Si Diode



SiC MOSFET



SiC Diode



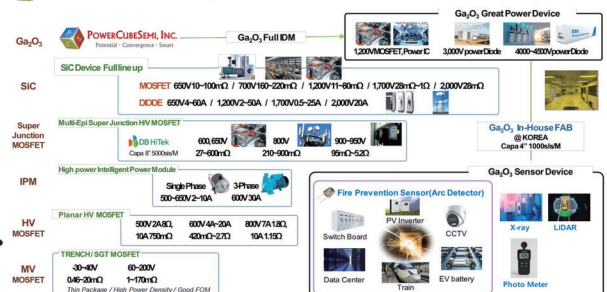
Ga₂O₃ Sensor



Ga₂O₃ Diode



Product Roadmap





The 22nd International Conference on
Metal Organic Vapor Phase Epitaxy

ICMOVPE XXII

July 12(Sun.)-17(Fri.), 2026

ICC JEJU, Jeju Island, Korea

Program Book

